

модуль IGBT SKKT SKKH SKM SEMIKRON продажа в Минске



Product Lines

Overview of Product Lines	9
----------------------------------	---

Product Classes

1	IGBT Modules	42
2	Silicon Carbide Modules, Full SiC, Hybrid SiC	74
3	MOSFET Modules	82
4	Thyristor/Diode Modules	88
5	Bridge Rectifier Modules	102
6	Intelligent Power Module – IPM	118
7	IGBT Driver	130
8	Stacks	134
9	Systems	144
10	Discretes, Chips, Discretes Diodes, Discretes Thyristors	152
11	Accessories, Heatsinks, Fans, Thermal Paste	164

Service & Contact

Application Manual	172
SemiSel Simulation	173
Applications & Technologies	174
Abbreviations	175
SEMIKRON Sample Request	176
SEMIKRON Online Shop	177
Worldwide Presence	178



Product at a Glance

MiniSKiiP	10
SEMITOP	12
SEMiX	14
SEMITRANS	16
SKiM	18
SEMIPONT	20
SEMIPACK	22
SEMiSTART	24
SKiiP	26
SKYPER	28
SEMISTACK CLASSIC	30
SEMISTACK RE	32
SEMIKUBE	34
SKiiPRACK	36
SKAI	38

Low inductance package design down to 10 nH

Benefits

The SEMITRANS package provides a low-inductive design down to 10nH which can be used for AC/DC inverters from 20kW to 1.5MW. The modules are available up to 1400A and 1700V. Availability is ensured by different IGBT sources. With a market experience of over 20 years the SEMITRANS packages offers a well proven standard design.

Applications

The proven package is designed for a broad range of applications like regenerative inverters and power supplies. The long service life fits perfectly to ambitious applications like AC drives, switched reluctance and DC motors.

Product range

The SEMITRANS family offers a broad range of topologies and power ranges. All standard voltage classes from 600V to 1700V can be chosen. The current rating extends from 50A to 1400A. And the SEMITRANS package is available as half bridge, chopper, single switch, MLI and common emitter.

Key features

- Topologies: half bridge, chopper, single switch, MLI, common emitter
- Isolated copper baseplate using DBC Technology
- With integrated gate resistor
- High isolation voltage

Further information:
www.semikron.com/semitrans

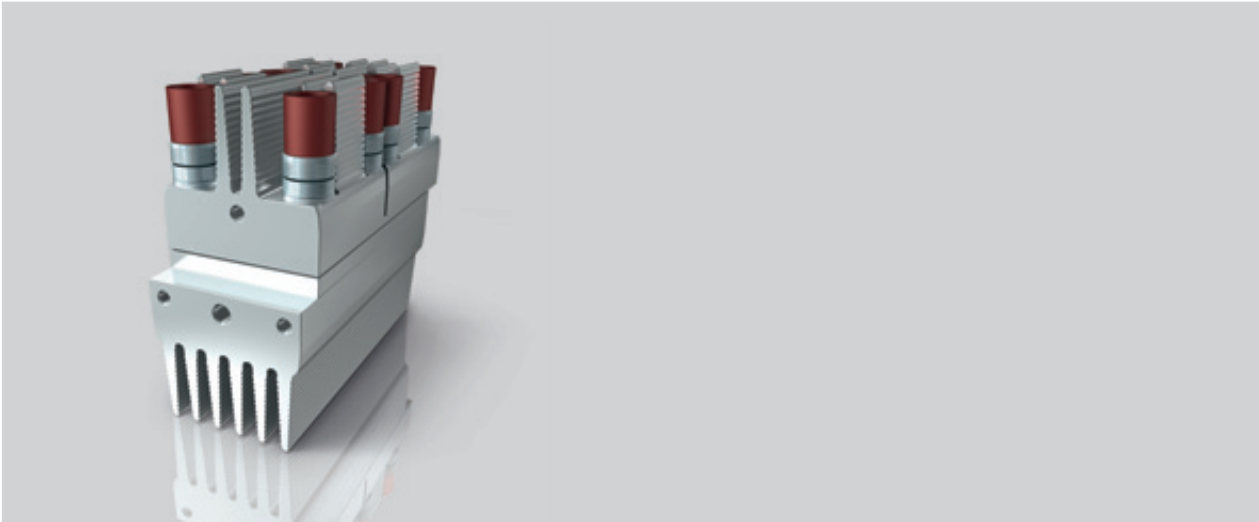
SEMiSTART®



Double-sided cooling for high load cycle capability

Robust pressure contact technology

Low thermal resistance



Motor
Drives

Robust thyristor package

Benefits

The main advantage of this power module is the high current capability in a new compact design. A 400kW soft-starter featuring SEMiSTART has just one sixth of the volume of the same device with conventional capsule thyristors.

Applications

SEMiSTART, the anti-parallel thyristor module is designed with an integrated heatsink for soft-start applications.

Product range

The SEMiSTART thyristor module is offered in five current classes, two voltages classes and three sizes.

In addition, due to pressure contact technology and double-sided chip cooling, these new thyristor modules can withstand overload currents of up to 3000A for a 20s duration of overload.

Key features

- 500A up to 3000A overload
- Double sided cooling
- Pressure contact

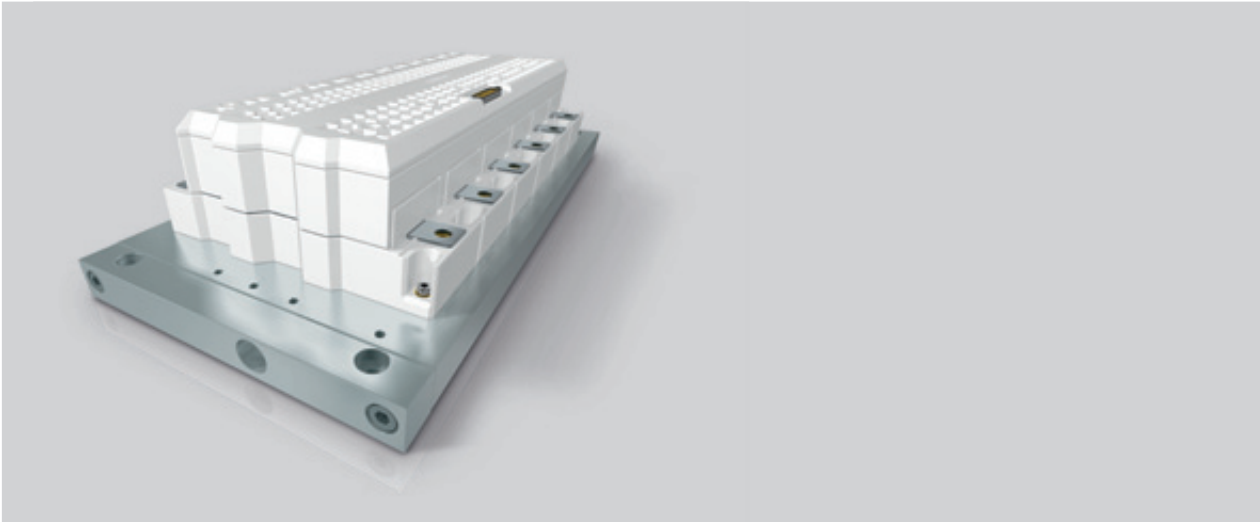
Further information:
www.semikron.com/semistart



3-in-1: Driver, semiconductors and cooling

2-3 times higher power cycling capability due to sinter technology

Completely assembled and 100% tested - including 1 hour burn-in test



Motor
Drives



Wind
Energy



Solar
Energy



Power
Quality



Utility
Vehicles



Urban Transport
Equipment

Sintered chips – for high operating temperatures

Benefits

SKiiP4 is the most powerful IPM on the market. SKiiP4 modules enable the production of converter units with outputs of up to 2.1MW. The power semiconductors used in SKiiP4 modules can be operated at a junction temperature of up to 175°C. To make sure these components can be reliably used at these temperatures, the power circuitry is 100% solder-free. Sinter technology is used to create a sintered silver layer instead of the solder layer which could limit the service life of power modules. Reliability during active and passive thermal cycling is greatly improved. A further benefit is the better load cycling capability as compared to solder-based modules.

The integrated gate driver in the SKiiP4 sets new standards in terms of reliability and functionality. The digital driver guarantees safe isolation between the primary and secondary side, both for switching signals and all measurement parameters, such as temperature and DC link voltage. This means the user no longer has to introduce complex and costly circuit components to provide safe isolation. For the first time, the SKiiP drive features a CANopen diagnosis channel for the integration of additional functions.

Applications

The success story of the SKiiP family has progressed hand in hand with the advancement of the wind power market. The 4th generation SKiiP modules are a further improvement of the powerful SKiiP series. The mainstay of SKiiP4 modules is the wind power sector, with approximately 57GW out of the 122GW of wind power installed worldwide (at the end of 2009) featuring SEMIKRON solutions, in many cases SKiiP technology. Besides wind power applications, SKiiP modules can also be found in elevators, solar power and railway applications – in fact, in any area where powerful, safe and reliable IGBT IPMs are a must.

Product range

SKiiP4 is available for 1200V and 1700V. In both of these voltage classes, SKiiP4 modules come in the topologies 3GB 1800A, 4GB 2400A and – new to the SKiiP family – 6GB 3600A. The wide range of accessories is now available for both SKiiP3 and SKiiP4. Among them the fiber optic boards, the boards for paralleling of SKiiP systems and the adapter board for connection of SKiiP4 to SKiiP3 controller.

Key features

System

- DC-Link monitoring (SKiiP3, SKiiP4)
- Current sensors (SKiiP3, SKiiP4)
- Temperature measurement (SKiiP3, SKiiP4)
- CAN diagnostic interface (SKiiP4)
- 100% solder-free (SKiiP4)
- Water, air and customized cooler

Production and Test

- 100% tested (function, isolation, protection function)
- Burn-In (SKiiP3 on request, SKiiP4 = 100%)

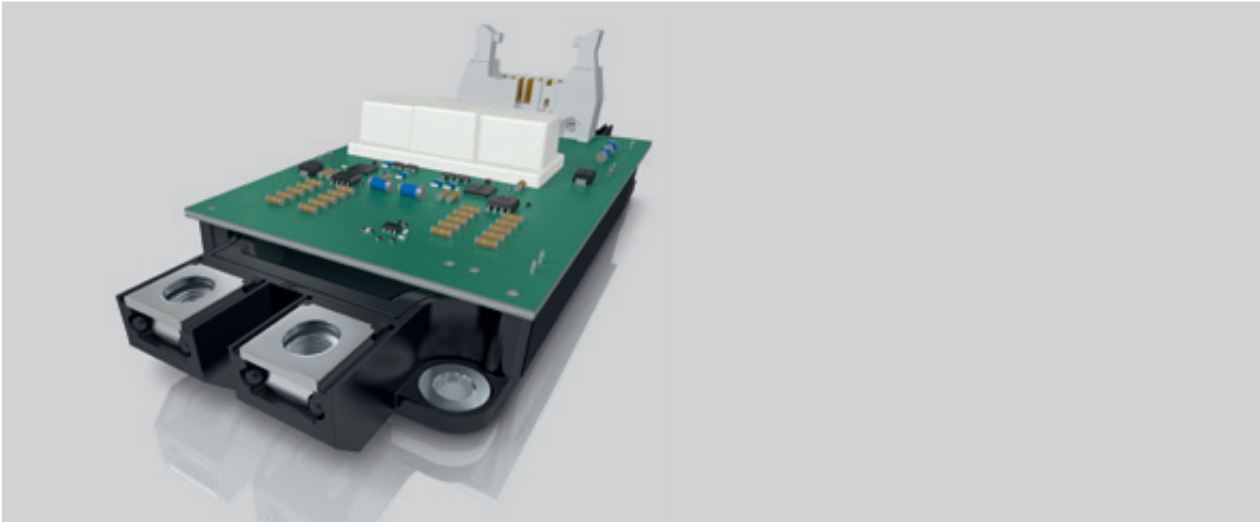
SKYPER®



MTBF rate of 5×10^6 hours (29500) with new SEMIKRON ASIC chipset

Safe gate control with separate signal transmission

7kV burst durability due to interlayer connection and metal pad ASICs




Motor
Drives


Solar
Energy


Power
Quality


Urban Transport
Equipment

SKYPER drives 3 x longer

Benefits

The high integration of SEMIKRON's new ASIC chipset provides for safe IGBT gate control over the whole lifecycle. Short circuits are managed very fast by separate error channels. SoftOff and over voltage feedback avoid dangerous overvoltages. The mixed signal ASICs guarantee lowest tolerances over the full temperature range. MLI or paralleled IGBT topologies are managed by the adjustable error handling. With an optimized interface and the adjustable filter setting the SKYPER IGBT driver survives external interferences over 100% of EN standards.

Key features

- Two driver channels for IGBT single and half bridges
- For 600V, 1200V and 1700V IGBT modules
- Driving up to 2500A
- Short pulse suppression and EMC cage
- SoftOff and separate error channels
- Adjustable filter and failure management
- Customized adapter boards on request

Applications

The new SKYPER 42 LJ offers the benefits of digital signal consistency while maintaining full performance. Ambitious applications such as medical or large drives up to 300kW are securely powered. SKYPER 32 is the perfect solution for industrial drives and process control applications. SKYPER 42 meets the requirements of induction heating/welding applications that call for high currents, durable solar inverters and motor drives between 300kW and 1.5MW. SKYPER Prime drives Primepack and SEMITRANS 10 modules up to 1700V and 1400A. The new SKYPER 12 PF is the benchmark for motor drives applications based on 17mm press fit modules.

Product range

The SKYPER drivers are available as IGBT driver cores and plug and play driver. The SKYPER platform can drive 600V, 1200V and 1700V IGBT modules. SKYPER 32 drives with a standard and a PRO version 1W per channel. The PRO version has additional protection features like external failure inputs and SoftOff. The SKYPER 42 has 4W per channel and can drive up to 2500A IGBTs. The SKYPER 42 LJ with 2W per channel closes the gap between SKYPER 32 and 42. With the new ASIC chipset, the fast failure management and the consistent signal conditioning the 42LJ is the latest driver core of SEMIKRON. The latest IGBT drivers are SKYPER Prime and SKYPER 12 PF. Both offer as fully qualified Plug & Play driver maximum performance when using SEMiX P or SEMITRANS 10 modules.

SEMISTACK® CLASSICS



Off-the-shelf product range

Air cooled power assemblies

Ready for integration



Motor Drives



Power Quality



Urban Transport Equipment

Standards for LV diode/thyristor rectifiers

Benefits

The SEMISTACK CLASSICS family range has been set up for fast integration of an industrial rectifier. Each power bridge has been sized to embed semi-conductors with suitable RC commutation circuit, proper AC fuses and cooling devices.

Applications

- Regulated/unregulated power supplies
- Alternator excitation
- Motor control
- Soft starters
- Soft charge
- Industrial heating

Product range

The SEMISTACK CLASSICS family range consists of a 125 item list, corresponding to four electrical topologies B6C, B6HK, B6U, W3C. All rectifiers include RC commutation circuit and fuses. Some are offered with a cooling system, heatsink temperature is monitored by thermo switches. Depending on the semiconductor technology, SEMISTACK CLASSICS power assemblies can be isolated (SEMIPACK) or non-isolated (capsule and stud screw).

Key features

- 4 topologies B6C, B6U, B6HK, W3C
- Maximum continuous DC current from 60A up to $4015A_{DC}$
- Rectifier AC voltage up to $500V_{AC}$
- DC bus voltage up to $670V_{DC}$
- RC, fuses, cooling fans and thermo switches included

Further information:
www.semikron.com/semistack-classics

SEMISTACK® RE

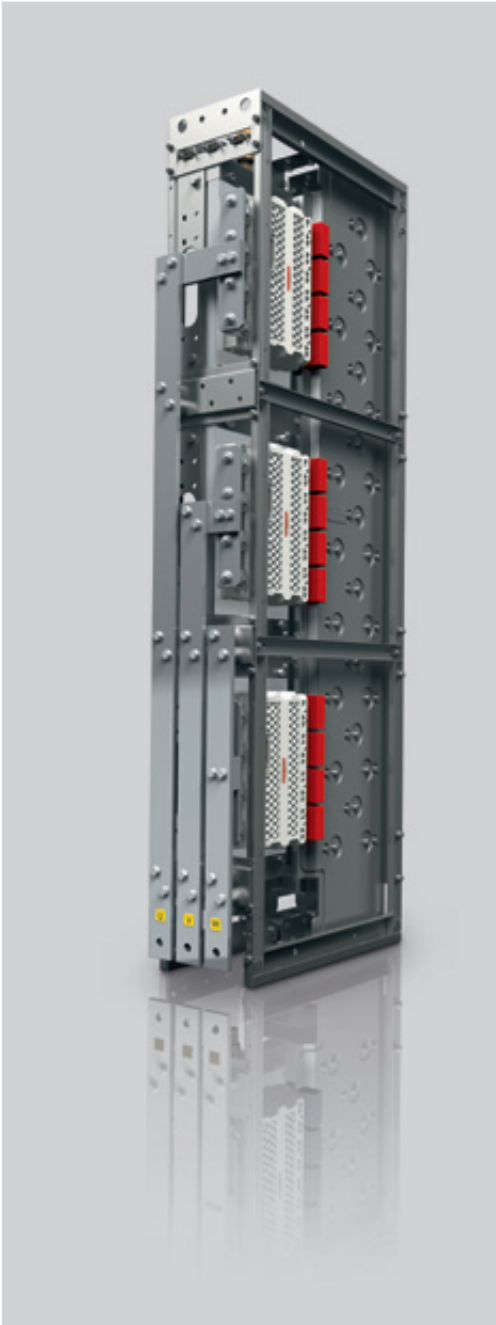


Pre-qualified water cooled IGBT power assemblies

IGBT inverter power density up to 11.4kVA/L

2- and 4-quadrant 3-phase converter

Long life expectancy



Wind Energy



Solar Energy

Low voltage optimized converter for wind and solar PV

Benefits

The SEMISTACK RE offers a pre-qualified power assembly ready for integration following rigorous SEMIKRON qualification and current environmental standards (IEC 60721-3).

The platform design has been optimized to get the best compromise cost/performance for a water-cooled power inverter in the megawatt power range.

The book format enables a compact integration in standard industrial cabinets to achieve high power up to 6MVA low voltage. Specified for wind turbine applications, the SEMISTACK RE offers a high IGBT cycling capability and a high capacitor bank lifetime, reducing maintenance.

Key features

- Maximum continuous output current from 600A up to 1400A_{RMS}
- Switching frequency up to 5kHz
- Inverter output voltage up to 690V_{AC}
- DC bus voltage up to 1250V_{DC}
- DC bus polypropylene capacitor bank lifetime rated at 100,000 hours at 40°C
- Analogue measurement T, V_{BUS}, I_{OUT}
- CAN interface (configuration and monitoring)
- Brake chopper optional

Applications

The SEMISTACK RE complies with wind turbine requirements, offering the capability to built 4-quadrant converters suitable with synchronous generator and double fed induction generators, with an optional brake chopper design. The platform flexibility allows to match requirement of solar PV central inverters with a DC bus voltage up to 900VDC continuous.

Alternatively, SEMISTACK RE can be used in low-voltage applications requiring high power and high reliability, such as 3-phase inverters in a shipyard or in a battery energy storage unit installed close to renewable energy power plants.

Product range

The SEMISTACK RE platform offers a standard inverter size HWD 1500x230x510mm to fit two power sub-assemblies into a 600x600x2000mm cabinet. The standard size has a current distribution between 1000A and 1400A.

For applications with lower current rating or with a stronger constraint on the cabinet size, a smaller inverter size HWD 1250x230x510mm offers continuous output current rated from 600A to 900A_{RMS}.

The SEMISTACK RE embeds the SKiiP IPM product family which integrates the IGBT gate driver and monitoring analogue outputs (temperature, output current and DC bus voltage). As an option, a CAN interface for supervising the SKiiP. To increase power capacity up to 6MVA, SEMISTACK RE can be put in parallel, connected together through the DC bus and controlled all-like-one with a SEMIKRON paralleling board. As an option, SEMISTACK RE platform can be offered as an integration into an industrial cabinet with suitable AC and/or DC power filters, electrical and hydraulic distribution.

SEMIKUBE®



- Air cooled IGBT power assembly
- Maximum output current from 150A up to 1500A
- Fits into 300mm cabinets
- Fully integrated safety management




Motor
Drives


Solar
Energy

AC | DC
Power
Supplies

Air cooled IGBT converter family up to 1MVA

Benefits

Extending the SEMIKUBE portfolio, the SEMIKUBE SlimLine platform is a family of pre-qualified power assemblies which follow the same rigorous SEMIKRON qualification and certifications. The platform integrates advanced technologies which maximize performance and power density. SEMIKUBE SlimLine platform has been designed to fit applications in severe environments. Suitable for outdoor cabinets, the platform can be placed in environments subject to high temperature fluctuations. Extremely slim, the platform can be mounted into 300mm deep cabinets. SEMIKUBE, by its modular design and patented DC clamp, enables the construction of various converter topologies. The platform design facilitates easy arrangement in the cabinet owing to the separation of the main cooling air flow through the heatsink and its IP54 rated mounting flange.

Applications

Following the philosophy of the SEMIKUBE, the SEMIKUBE SlimLine is optimised for solar PV central inverters. Sized for the most commonly used central inverter ratings on the market, i.e. 500kW, 670kW up to 900kW, the SEMIKUBE SlimLine 3-phase inverter operates up to 1000VDC bus voltage.

Designed in accordance with IEC 62109, the platform is poised to obtain UL 1000V recognition. SEMIKUBE SlimLine complies with most AC drives application requirements. The current measurement precision of 1% (at 25°C) allows for premium motor control required for highly dynamic applications and motion control systems.

Product range

The SEMIKUBE offers four frame sizes of continuous rated current from 150A to 1500A, using SEMITRANS 1200V IGBT Trench E4 modules. SEMIKUBE SlimLine design is optimised for 3-phase inverter topologies. Dedicated rectifier with 3-phase inverter and optional brake chopper may be added. The IGBTs are controlled by a SEMIKRON embedded driver, which provides error management, and analogue outputs of current, DC voltage and heatsink temperature. A CAN interface is available for parameter configuration and diagnostics monitoring. Air cooling for SEMIKUBE SlimLine is provided by highly efficient long life axial fans, realizing maximum power within a compact package. SEMIKUBE is a more versatile product, allowing converter construction around a common DC link, including four quadrant converters, and multiphase converters.

Key features

- Power density up to 7.5kVA/L
- Four frame sizes ranging from 75kVA up to 1300kVA
- AC output voltage up to 500VAC
- Current measurement accuracy <1%
- $T_{HEATSINK}$, V_{BUS} , I_{OUT} : analogue measurement or CAN monitoring
- Operating temperature range: -30°C to +60°C
- Integration into 300mm deep cabinet
- UL1741 1000V ready
- 100% tested in production

SKiiPRACK®

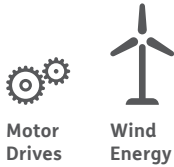


Pre-qualified water cooled IGBT power assemblies

IGBT Inverter power density at 10.4kVA/L

Flexible mounting

High reliability and long life expectancy



Versatile high power inverter platform

Benefits

The SKiiPRACK offers a pre-qualified power assembly ready for integration following rigorous SEMIKRON qualification and current environmental standards (IEC 60721-3). Based on a "Cell" construction, the SKiiPRACK platform offers high flexibility for designing numerous electrical topologies and for a convenient integration into standard industrial cabinets. The SKiiPRACK has been designed for applications requesting high reliability and a long life time up to 20 years. Totally dismountable, the cell concept eases maintenance phases, reducing the time of handling and application stops.

Key features

- Maximum continuous output current from 600A up to 1200A_{RMS}
- Switching frequency up to 5kHz
- Inverter output voltage up to 690V_{AC}
- DC bus voltage up to 1100V_{DC}
- DC bus polypropylene capacitor bank lifetime rated at 100,000 hours at 40 °C
- Analogue measurement T, V_{BUS}, I_{OUT}
- As possible options:
 - Brake chopper, additional capacitor bank, DC bus electrolytic capacitor bank, diode/thyristor rectifier cells

Applications

The SKiiPRACK complies with wind turbine requirements, offering the capability to build 4-quadrant converters suitable for synchronous generators and double fed induction generators, with an optional brake chopper design. The platform flexibility allows matching electrical topologies of AC drive applications to power AC induction motors up to 1MW, in particular for pumps or in shipyards.

Product range

The SKiiPRACK platform consists of a cell HWD 525x375x470mm to be assembled with others cells to create a functional unit in standard cabinets 600mm deep and 2,000mm high. A cell can integrate an H-bridge, a 1-phase leg + brake chopper or 12-pulse rectifier, and combination of them can create 3-phase inverter, 4-quadrant converter or 3-phase rectifier and inverter. The output current range offers scalability from 600A to 1200A continuous.

The SKiiPRACK embeds the SKiiP IPM product family which integrates the IGBT gate driver and monitoring analogue outputs (temperature, output current and DC bus voltage). As an option, a CAN interface for supervising the SKiiP. To increase power capacity up to 5MVA, SKiiPRACK can be put in parallel, connected in a very flexible way (horizontal or vertical) together through the DC bus and controlled all-like-one with a SEMIKRON paralleling board. As an option, SKiiPRACK platform can be offered with integration in an industrial cabinet with suitable AC and/or DC power filters, electrical and hydraulic distribution.

SKAI[®]2

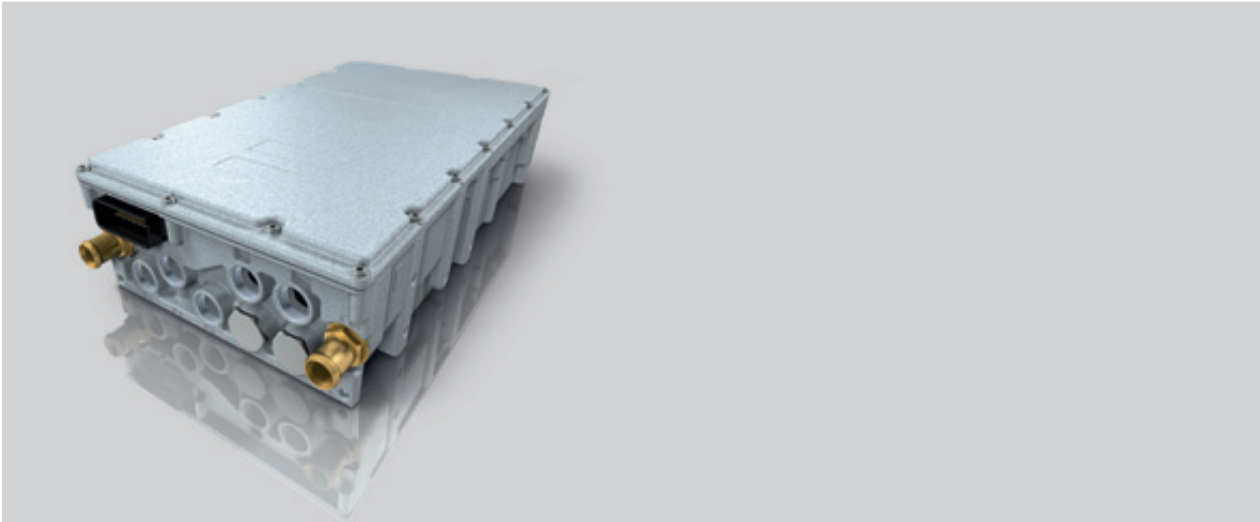


Suitable for battery voltages 24V up to 800V

Sintered power semiconductors

EMI compliant

“off-the-shelf” variants with gate driver interface, vector control software, automotive power connections



Utility
Vehicles



Urban Transport
Equipment

Most compact power electronic system „off-the-shelf“ for electro-mobility

Benefits

The SKAI power electronic platform – now in its 2nd generation – comprises highly integrated inverters which provide the ideal powertrain solution for mobile electric and hybrid applications. Power densities of up to 20kVA / liter provide a notable size reduction compared with other available standard inverter products. The systems are designed to operate with supply voltages of 24V up to 800V and with output power ratings of up to 250kVA.

The IGBT-based SKAI 2 HV inverter operates on sintered 100% solder-free 600V or 1200V power semiconductors and it features polypropylene film DC-link capacitors. The MOS-based SKAI 2 LV inverter uses the established SkiiP technology with a very low-inductive connection to the DC-link capacitors, driver electronics, latest generation DSP controller, current, voltage and temperature sensors. It is integrated in a waterproof IP67 enclosure. The compact inverters withstand high vibration amplitudes up to 10g rms. QUASAR motor control software functionally complements the system and completes this tried-and-tested package. SEMIKRON provides engineering services to support customers in the integration of the SKAI 2 inverter systems. Available services include, for instance, lifetime estimation, field application support, individual parameterization of motor control software etc.

Key features

- Compact integration in IP 67 enclosure
- Voltage, current and temperature sensors
- Gate driver with protection
- IGBT/ MOSFET power semiconductors
- Fully programmable digital signal processor
- EMI filters
- Versatile cooling system (liquid cooled, forced air cooled, base plate)
- DC link capacitors
- Motor control software

Applications

The SKAI 2 "Off-the-Shelf" power electronic building block family has been introduced to cover a broad range of vehicle electrification applications. Examples are electric drivetrains with standardized motor/generator flanges to fit or retrofit the drives easily into existing vehicle designs. These types of drivetrains have been developed for many vehicle types, i.e. buses, light trucks, agriculture and construction machinery as well as marine applications or cars.

Product range

There are versatile SKAI 2 HV "Off-the-Shelf" variants available. The SKAI 2 LV is available as single or dual inverter for supply voltages between 24V and 120V. Cooling methods are liquid, forced air cooling or base plate. There are different optional services available like end-of-line flashing of customer specific software, lifetime estimation based on application profile analysis, field application support, individual parameterization of motor control software and further services on request.

Product Classes





1	IGBT Modules	42
2	Silicon Carbide Modules, Full SiC, Hybrid SiC	74
3	MOSFET Modules	82
4	Thyristor/Diode Modules	88
5	Bridge Rectifier Modules	102
6	Intelligent Power Module – IPM	118
7	IGBT Driver	130
8	Stacks	134
9	Systems	144
10	Discretes, Chips, Discretes Diodes, Discretes Thyristors	152
11	Accessories, Heatsinks, Fans, Thermal Paste	164

IGBT Modules for Maximum Performance

1

SEMIKRON offers IGBT (insulated-gate bipolar transistor) modules in SEMITRANS, SEMiX, SKiM, MiniSKiiP and SEMITOP packages in different topologies, current and voltage ratings. Starting from 6A to 1400A in voltage classes from 600V to 1700V.

The IGBT modules are used in a variety of applications offering key technologies like sintering, spring or pressfit contacts for easy and fast assembly.

Different topologies like CIB (converter inverter brake), halfbridge, H-bridge, 6-pack and 3-level are available in order to cover almost all application fields.

The latest IGBT chip and diode technologies offer optimized switching performance up to $T_j \text{ max} = 175^\circ\text{C}$.

Product	Page
MiniSKiiP	44
SEMITOP	49
SEMiX	55
SEMITRANS	62
SKiM 4/5	70
SKiM 63/93	72

▶ For detailed information
please refer data sheets.

Further information:
www.semikron.com/igbt-modules

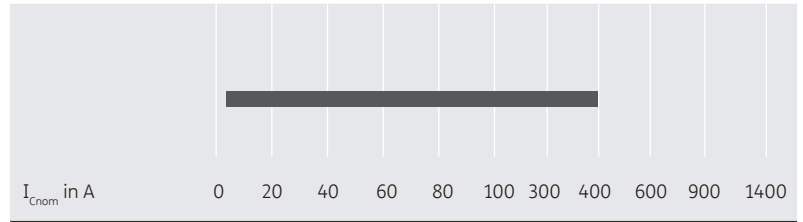
IGBT Modules

MiniSKiiP®

6-pack
3-level
H-bridge
CIB
half bridge
twin 6-pack



600V up to 1700V

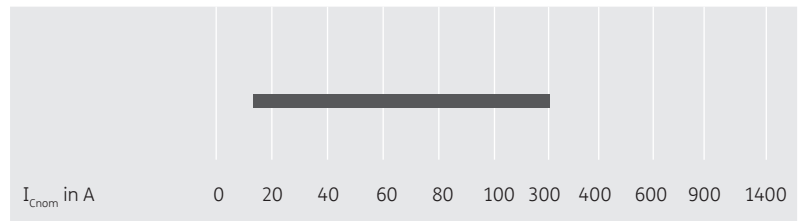


SEMITOP®

half bridge
6-pack
3-level
chopper
H-bridge
CIB



600V up to 1200V

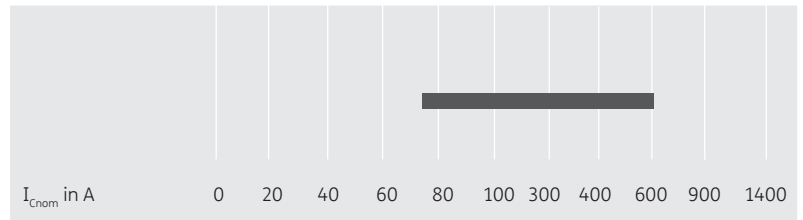


SEMiX®

half bridge
6-pack
3-level
chopper
buck-boost converter



600V up to 1700V

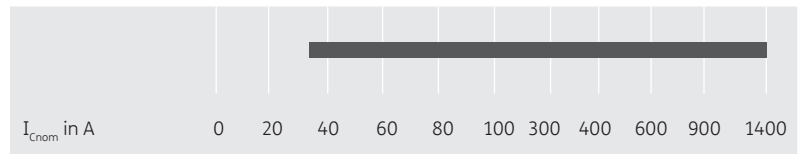


SEMITRANS®

half bridge
6-pack
chopper
single switch

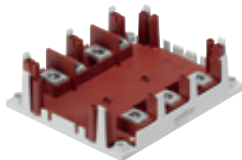


600V up to 1700V

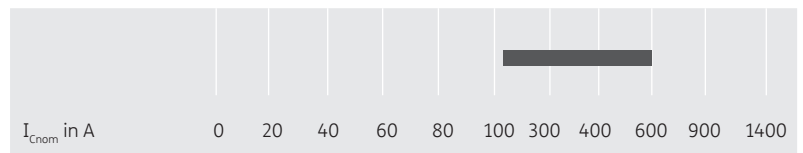


SKiM® 4/5

6-pack
3-level

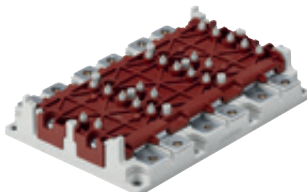


600V up to 1700V

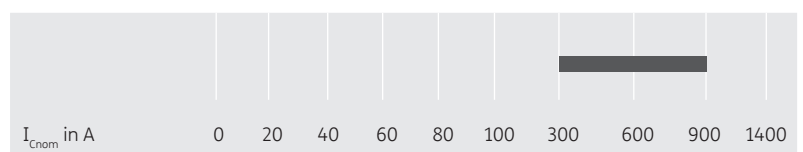


SKiM® 63/93

6-pack
chopper



600V up to 1700V



IGBT Modules / MiniSKiiP

Type	IGBT						Diode				Rectifier		Module		
	$I_c @ T_s = 25^\circ\text{C}$	I_{cnom}	$V_{CE(sat)} @ T_j = 25^\circ\text{C typ.}$	E_{on}	E_{off}	$R_{th(j-s)}$	$I_F @ T_s = 25^\circ\text{C}$	$V_F @ T_j = 25^\circ\text{C typ.}$	E_{rr}	$R_{th(j-s)}$	$I_{FSM} @ T_j = 25^\circ\text{C}$	$R_{th(j-s)}$	Case	Circuit	
	A	A	V	mJ	mJ	K/W	A	V	mJ	K/W	A	K/W			
600V - IGBT3 (Trench)															
SKiiP 16GH066V1	65	50	1.45	1.7	1.7	0.95	56	1.50	1.3	1.6	-	-	II 1		
SKiiP 27GH066V1	88	75	1.45	2.7	3	0.75	77	1.50	1.8	1.2	-	-	II 2		
SKiiP 28GH066V1	112	100	1.45	3.4	3.5	0.6	112	1.30	3.3	0.8	-	-	II 2		
SKiiP 01NAC066V3	12	6	1.45	0.3	0.2	2.4	12	1.30	0.2	3	220	1.5	II 0		
SKiiP 02NAC066V3	20	10	1.45	0.5	0.3	2	20	1.30	0.5	2.5	220	1.5	II 0		
SKiiP 01NEC066V3	12	6	1.45	0.3	0.2	2.4	12	1.30	0.2	3	220	1.5	II 0		
SKiiP 02NEC066V3	20	10	1.45	0.5	0.3	2	20	1.30	0.5	2.5	220	1.5	II 0		
SKiiP 03NEC066V3	27	15	1.45	0.6	0.5	1.8	28	1.40	0.5	2.5	220	1.5	II 0		
SKiiP 11NAB066V1	12	6	1.45	0.3	0.2	2.4	12	1.30	0.2	3	220	1.5	II 1		
SKiiP 12NAB066V1	20	10	1.45	0.5	0.3	2	20	1.30	0.5	2.5	220	1.5	II 1		
SKiiP 13NAB066V1	27	15	1.45	0.6	0.5	1.8	28	1.40	0.5	2.5	220	1.5	II 1		
SKiiP 14NAB066V1	33	20	1.45	0.75	0.7	1.6	31	1.60	0.55	2.5	220	1.5	II 1		
SKiiP 25NAB066V1	43	30	1.45	0.9	1.2	1.35	39	1.50	1.1	2.1	370	1.5	II 2		
SKiiP 26NAB066V1	65	50	1.45	1.6	1.6	0.95	56	1.50	1.3	1.6	370	1.5	II 2		
SKiiP 37NAB066V1	88	75	1.45	2.7	3	0.75	77	1.50	1.8	1.2	700	0.9	II 3		
SKiiP 38NAB066V1	112	100	1.45	3.4	3.5	0.6	112	1.30	3.3	0.8	700	0.9	II 3		
SKiiP 02NEB066V3	20	10	1.45	0.5	0.3	2	20	1.30	0.5	2.46	220	1.5	II 0		
SKiiP 03NEB066V3	27	15	1.45	0.6	0.5	1.8	28	1.40	0.5	2.5	220	1.5	II 0		
SKiiP 25NEB066V1	43	30	1.45	0.9	1.2	1.35	39	1.50	1.1	2.1	370	1.5	II 2		
600V - NPT IGBT (Standard)															
SKiiP 11NAB065V1 ²⁾	12	6	2.00	0.3	0.2	1.9	12	1.30	0.2	2.5	220	1.5	II 1		
SKiiP 12NAB065V1 ²⁾	20	10	2.00	0.3	0.3	1.5	20	1.40	0.2	2.5	220	1.5	II 1		
SKiiP 13NAB065V1 ²⁾	24	15	2.00	0.6	0.3	1.4	26	1.40	0.4	2.2	220	1.5	II 1		
SKiiP 14NAB065V1 ²⁾	29	20	2.00	0.7	0.4	1.25	26	1.60	0.4	2.2	370	1.25	II 1		
650V - IGBT3 (Trench)															
SKiiP 26MLI07E3V1 ¹⁾	98	75	1.45	2.8	2.8	0.6	75	1.5	1.4	1	-	-	II 2		
SKiiP 27MLI07E3V1 ¹⁾	110	100	1.45	4.2	4.2	0.6	107	1.4	3.5	0.8	-	-	II 2		
SKiiP 28MLI07E3V1 ¹⁾	135	150	1.45	5.5	5.6	0.55	126	1.4	5.5	0.75	-	-	II 2		
SKiiP 39MLI07E3V1 ¹⁾	159	200	1.45	3.6	8.9	0.5	163	1.4	8.3	0.6	-	-	II 3		

Footnotes: 1) New product / 2) Not for new design / 8) Target data

IGBT Modules / MiniSKiiP

Type	IGBT						Diode				Rectifier		Module	
	$I_c @ T_s = 25^\circ\text{C}$	I_{cnom}	$V_{CE(ant)} @ T_j = 25^\circ\text{C typ.}$	E_{on}	E_{off}	$R_{th(j-s)}$	$I_F @ T_s = 25^\circ\text{C}$	$V_F @ T_j = 25^\circ\text{C typ.}$	E_{rr}	$R_{th(j-s)}$	$I_{FSM} @ T_j = 25^\circ\text{C}$	$R_{th(j-s)}$	Case	Circuit
	A	A	V	mJ	mJ	K/W	A	V	mJ	K/W	A	K/W		
650V - IGBT3 (Trench)														
SKiiP 24GB07E3V1 ¹⁾	185	150	1.45	2.2	5.1	0.33	161	1.5	3.7	0.45	-	-	II 2	
SKiiP 26GB07E3V1 ¹⁾	229	200	1.45	4.4	7.4	0.28	235	1.4	4.5	0.35	-	-	II 2	
SKiiP 38GB07E3V1 ¹⁾	287	300	1.45	5.5	10.6	0.25	310	1.4	5.1	0.28	-	-	II 3	
1200V - IGBT3 (Trench)														
SKiiP 11AC126V1 ²⁾	16	8	1.70	0.9	1	1.5	14	1.90	0.9	2.5	-	-	II 1	
SKiiP 12AC126V1 ²⁾	28	15	1.70	1.7	1.9	1.15	26	1.60	1.2	1.95	-	-	II 1	
SKiiP 13AC126V1 ²⁾	41	25	1.70	4.1	3.1	0.9	30	1.80	2.2	1.7	-	-	II 1	
SKiiP 23AC126V1 ²⁾	41	25	1.70	3.7	3.1	0.9	30	1.80	2.6	1.7	-	-	II 2	
SKiiP 24AC126V1 ²⁾	52	35	1.70	4.2	4.4	0.75	38	1.80	3.5	1.5	-	-	II 2	
SKiiP 25AC126V1 ²⁾	73	50	1.70	5.8	6.5	0.55	62	1.60	5.1	1	-	-	II 2	
SKiiP 26AC126V1 ²⁾	88	70	1.70	9	7.7	0.5	91	1.50	7.5	0.7	-	-	II 2	
SKiiP 37AC126V2 ²⁾	97	75	1.70	9.6	8.7	0.45	90	1.60	9.6	0.7	-	-	II 3	
SKiiP 38AC126V2 ²⁾	118	105	1.70	13.1	13	0.4	118	1.60	11.2	0.55	-	-	II 3	
SKiiP 39AC126V2 ²⁾	157	140	1.70	19.9	17.2	0.3	167	1.50	16.2	0.4	-	-	II 3	
SKiiP 11NAB126V1 ²⁾	16	8	1.70	0.8	1	1.5	14	1.90	0.9	2.5	220	1.5	II 1	
SKiiP 12NAB126V1 ²⁾	28	15	1.70	2	1.9	1.15	26	1.60	1.3	1.95	220	1.5	II 1	
SKiiP 23NAB126V1 ²⁾	41	25	1.70	3.5	3	0.9	30	1.80	2.5	1.7	370	1.25	II 2	
SKiiP 23NAB126V10 ²⁾	41	25	1.70	3.5	3	0.9	30	1.80	2.5	1.7	635	0.9	II 2	
SKiiP 24NAB126V1 ²⁾	52	35	1.70	4.6	4	0.75	38	1.80	3.3	1.5	370	1.25	II 2	
SKiiP 24NAB126V10 ²⁾	52	35	1.70	4.6	4	0.75	38	1.80	3.3	1.5	635	0.9	II 2	
SKiiP 35NAB126V1 ²⁾	73	50	1.70	6.5	6.1	0.55	62	1.60	4.7	1	700	0.9	II 3	
SKiiP 36NAB126V1 ²⁾	88	70	1.70	9	7.7	0.5	91	1.50	7.5	0.7	700	0.9	II 3	
1200V - IGBT4 (Trench)														
SKiiP24GB12T4V1 ¹⁾	170	150	1.85	10.8	15.6	0.32	157	2.2	10.3	0.41	-	-	II 2	
SKiiP26GB12T4V1 ¹⁾	224	200	1.80	13.6	22.1	0.25	194	2.2	13.4	0.34	-	-	II 2	
SKiiP38GB12E4V1 ¹⁾	329	300	1.85	19.1	34.6	0.17	267	2.2	21.5	0.26	-	-	II 3	
SKiiP39GB12E4V1 ⁸⁾	388	400	1.80	24	48.5	0.16	330	2.2	28.9	0.22	-	-	II 3	
SKiiP 26GH12T4V11	90	70	1.85	9.5	7.1	0.55	83	2.2	5.6	0.75	-	-	II 2	

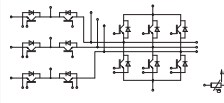
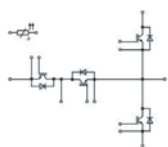
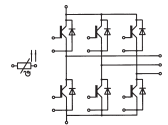
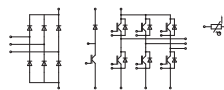
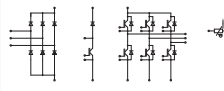
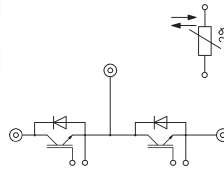
Footnotes: 1) New product / 2) Not for new design / 8) Target data

IGBT Modules / MiniSKiiP

Type	IGBT						Diode				Rectifier		Module	
	$I_c @ T_s = 25^\circ\text{C}$	I_{cnom}	$V_{CE(EMT)} @ T_j = 25^\circ\text{C typ.}$	E_{on}	E_{off}	$R_{th(j-s)}$	$I_F @ T_s = 25^\circ\text{C}$	$V_F @ T_j = 25^\circ\text{C typ.}$	E_{rr}	$R_{th(j-s)}$	$I_{FSM} @ T_j = 25^\circ\text{C}$	$R_{th(j-s)}$	Case	Circuit
	A	A	V	mJ	mJ	K/W	A	V	mJ	K/W	A	K/W		
1200V - IGBT4 (Trench)														
SKiiP 11AC12T4V1	12	8	1.85	0.87	0.75	1.84	15	2.3	0.53	2.53	-	-	II 1	
SKiiP 12AC12T4V1	18	15	1.85	1.65	1.5	1.3	23	2.4	0.79	1.92	-	-	II 1	
SKiiP 13AC12T4V1	41	25	1.85	3.7	2.4	1	32	2.4	1.64	1.52	-	-	II 1	
SKiiP 23AC12T4V1	41	25	1.85	3.7	2.4	1	32	2.4	1.64	1.52	-	-	II 2	
SKiiP 24AC12T4V1	52	35	1.85	3.7	3	0.85	44	2.3	2.3	1.2	-	-	II 2	
SKiiP 25AC12T4V1	69	50	1.85	6	4.5	0.71	60	2.2	3.2	0.95	-	-	II 2	
SKiiP 26AC12T4V1	90	70	1.85	9.5	7.1	0.55	83	2.2	5.6	0.75	-	-	II 2	
SKiiP 37AC12T4V1	90	75	1.85	11.5	6.8	0.58	83	2.2	5.5	0.75	-	-	II 3	
SKiiP 38AC12T4V1	115	100	1.80	13.7	9.7	0.48	100	2.2	6.5	0.66	-	-	II 3	
SKiiP 39AC12T4V1	167	150	1.85	22.5	14	0.33	136	2.1	11.4	0.52	-	-	II 3	
SKiiP 02NAC12T4V1	6	4	1.85	0.66	0.37	2.49	7.5	1.8	0.34	2.53	220	1.5	II 0	
SKiiP 03NAC12T4V1	7.5	8	1.85	0.9	0.7	1.84	9	2.3	0.5	2.53	220	1.5	II 0	
SKiiP 10NAB12T4V1	6	4	1.85	0.66	0.37	2.49	7.5	1.8	0.34	2.53	220	1.5	II 1	
SKiiP 11NAB12T4V1	12	8	1.85	0.87	0.74	1.84	15	2.3	0.57	2.53	220	1.5	II 1	
SKiiP 12NAB12T4V1	18	15	1.85	1.4	1.3	1.3	23	2.40	1.1	1.92	220	1.5	II 1	
SKiiP 23NAB12T4V1	37	25	1.85	2.65	2.3	1.2	32	2.40	1.6	1.52	370	1.25	II 2	
SKiiP 23NAB12T4V10	37	25	1.85	2.65	2.3	1.2	30	2.4	1.6	1.52	700	0.9	II 2	
SKiiP 24NAB12T4V1	48	35	1.85	4.3	3.25	1	44	2.3	2.4	1.2	370	1.25	II 2	
SKiiP 24NAB12T4V10	48	35	1.85	4.3	3.25	1	44	2.3	2.4	1.2	700	0.9	II 2	
SKiiP 34NAB12T4V1	52	35	1.85	4.3	3.3	0.85	44	2.3	2.4	1.2	370	1.25	II 3	
SKiiP 34NAB12T4V10	52	35	1.85	4.3	3.3	0.85	44	2.3	2.4	1.2	700	0.9	II 3	
SKiiP 35NAB12T4V1	69	50	1.85	6	4.7	0.71	60	2.25	3.4	0.95	700	0.9	II 3	
SKiiP 37NAB12T4V1	90	75	1.85	9.7	6.8	0.58	83	2.2	4.9	0.75	700	0.9	II 3	
SKiiP 37NAB12T4V10	90	75	1.85	-	-	-	-	2.2	-	0.75	700	-	II 3	
SKiiP 38NAB12T4V1	115	100	1.80	11.2	10	0.48	99	2.2	6.5	0.66	1000	0.7	II 3	
SKiiP 12ACC12T4V10 ¹⁾	18	15	1.85	1.7	1.4	1.3	23	2.4	1.1	1.92	60	2.5	II 1	
SKiiP 23ACC12T4V10 ¹⁾	41	25	1.85	3.7	2.4	1	32	2.4	1.64	1.52	65	1.92	II 2	
SKiiP 24ACC12T4V10 ¹⁾	52	35	1.85	4.2	3.1	0.85	44	2.3	2.2	1.2	100	1.52	II 2	
SKiiP 39TMLI12T4V2 ¹⁾	235	200	1.80	7.5	12.8	0.23	194	2.2	9.7	0.34	-	-	II 3	
SKiiP 39GA12T4V1	167	150	1.85	22.5	14	0.33	136	2.1	11.4	0.52	-	-	II 3	

Footnotes: 1) New product / 2) Not for new design / 8) Target data

IGBT Modules / MiniSKiiP

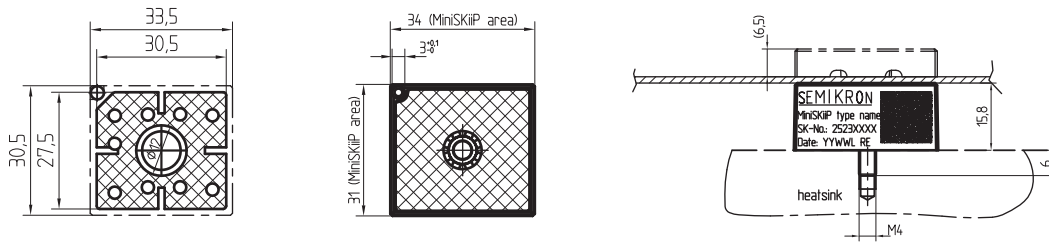
Type	IGBT						Diode				Rectifier		Module	
	$I_c @ T_s = 25^\circ\text{C}$	I_{cnom}	$V_{CE(EMT)} @ T_j = 25^\circ\text{C typ.}$	E_{on}	E_{off}	$R_{th(j-s)}$	$I_F @ T_s = 25^\circ\text{C}$	$V_F @ T_j = 25^\circ\text{C typ.}$	E_{rr}	$R_{th(j-s)}$	$I_{FSM} @ T_j = 25^\circ\text{C}$	$R_{th(j-s)}$	Case	Circuit
	A	A	V	mJ	mJ	K/W	A	V	mJ	K/W	A	K/W		
1200V - IGBT4 (Fast Trench)														
SKiiP35TMLI12F4V2 ⁸⁾	54	40	2.05	-	-	0.763	44	2.3	-	1.225	-	-	II 3	
SKiiP 28TMLI12F4V1 ¹⁾	93	80	2.05	3.4	2.2	0.49	76	2.2	1.7	0.86	-	-	II 2	
SKiiP 29TMLI12F4V1 ⁸⁾	-	150	2.05	-	-	0.33	-	2.2	-	0.45	-	-	II 2	
1700V - IGBT3 (Trench)														
SKiiP 38AC176V2 ¹⁾	-	100	2.00	23.8	32.2	-	-	1.8	26.2	-	-	-	II 3	
SKiiP 24NAB176V1 ¹⁾	38	29	2.00	5.1	6.3	0.91	48	2	4.9	1.14	370	1.32	II 2	
SKiiP 34NAB176V3 ¹⁾	67	58	2.00	11.2	12.8	0.57	66	2.1	6.6	0.84	635	0.86	II 3	
1700V - IGBT4 (Trench)														
SKiiP 22GB17E4V1 ¹⁾	117	100	1.90	22.2	30.7	0.43	91	2	20.9	0.7	-	-	II 2	
SKiiP 24GB17E4V1 ¹⁾	177	150	1.90	26	46	0.28	149	2	32.4	0.41	-	-	II 2	
SKiiP 36GB17E4V1 ¹⁾	224	200	1.90	37	66	0.23	193	2	47	0.32	-	-	II 3	
SKiiP 38GB17E4V1 ¹⁾	341	300	1.90	47	102	0.15	267	2	69	0.24	-	-	II 3	

Footnotes: 1) New product / 2) Not for new design / 8) Target data

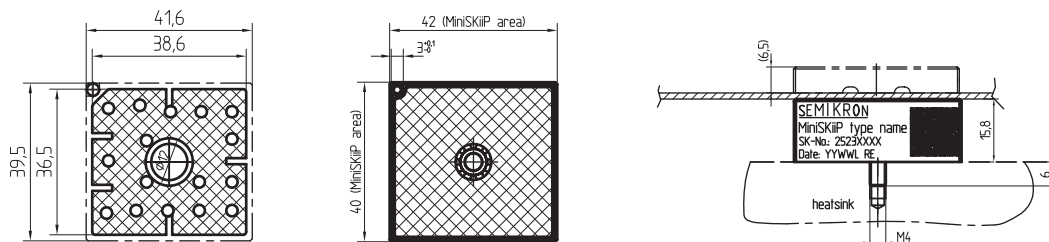
IGBT Modules / MiniSKiiP

Cases

MiniSKiiP II 0

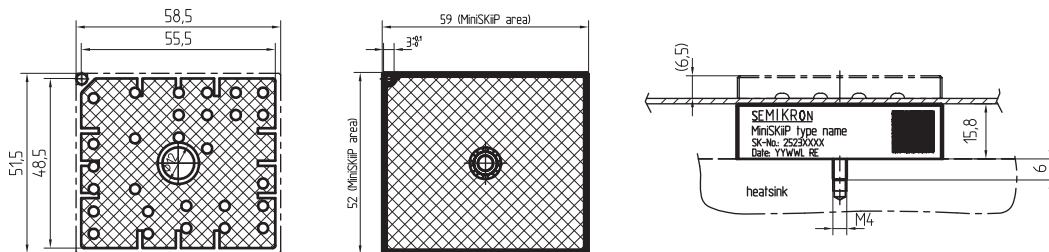


MiniSKiiP II 1



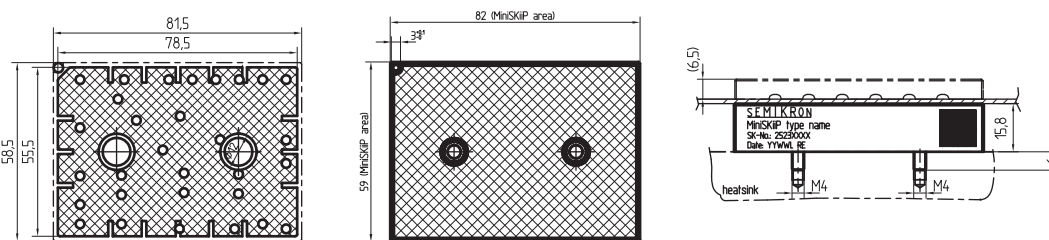
pin configuration depends on circuit
(details in data sheet)

MiniSKiiP II 2



pin configuration depends on circuit
(details in data sheet)

MiniSKiiP II 3



pin configuration depends on circuit
(details in data sheet)

Dimensions in mm

IGBT Modules / SEMITOP

Type	IGBT						Diode			Rectifier			Module	
	$I_c @ T_s = 25^\circ\text{C}$	$I_{c\text{nom}}$	$V_{CE(\text{sat})} @ T_j = 25^\circ\text{C typ.}$	E_{on}	E_{off}	$R_{\text{th(j-c)}}$	$I_f @ T_s = 25^\circ\text{C}$	$V_f @ T_j = 25^\circ\text{C typ.}$	E_{rr}	$R_{\text{th(j-s)}}$	$R_{\text{th(j-s)}}$	$I_{\text{FSM}} @ T_j = 25^\circ\text{C}$	Case	Circuit
	A	A	V	mJ	mJ	K/W	A	V	mJ	K/W	K/W	A		
600V - IGBT3 (Trench)														
SK 75 GB 066 T	77	75	1.45	3.1	2.8	0.94	62	1.35	0.85	1.55	-	-	3	
SK 100 GB 066 T	96	100	1.45	7	6	0.78	108	1.35	1.7	0.91	-	-	3	
SK 150 GB 066 T	124	150	1.45	6.25	5.7	0.55	135	1.35	1.7	0.73	-	-	3	
SK 30 GBB 066 T	40	30	1.45	0.97	1.77	1.65	36	1.45	0.26	2.1	-	-	3	
SK 50 GBB 066 T	60	50	1.45	2.2	1.73	1.11	56	1.50	0.72	1.7	-	-	3	
SK 75 GBB 066 T	77	75	1.45	3.1	2.8	0.94	77	1.35	0.85	1.55	-	-	3	
SK 20 MLI 066	30	20	1.45	0.4	1.07	1.95	30	1.60	0.2	2.46	-	-	3	
SK 30 MLI 066	40	30	1.45	0.97	1.77	1.65	37	1.50	0.26	2.3	-	-	3	
SK 30 MLI 066p ⁸⁾	37	30	1.45	0.97	1.77	1.65	34	1.50	0.26	2.3	-	-	3p	
SK 50 MLI 066	60	50	1.45	1.46	2.02	1.11	56	1.50	1.07	1.7	-	-	3	
SK 75 MLI 066 T	83	75	1.45	1.7	2.8	0.75	92	1.50	1.1	1.2	-	-	4	
SK 100 MLI 066 T	105	100	1.45	2.5	4.2	0.65	110	1.35	1.9	0.9	-	-	4	
SK 150 MLI 066 T	151	150	1.45	2.7	5.9	0.55	115	1.50	2.6	0.72	-	-	4	
SK 75 GD 066 T	83	75	1.45	3.1	2.8	0.75	92	1.35	0.85	1.2	-	-	4	
SK 100 GD 066 T	105	100	1.45	7	6	0.65	99	1.30	1.7	0.8	-	-	4	
SK 150 GD 066 T	151	150	1.45	6.25	5.7	0.55	198	1.30	1.7	0.54	-	-	4	
SK 200 GD 066 T	174	200	1.45	13.9	12	0.45	99	1.30	3.4	0.8	-	-	4	
SK 20 GD 066 ET	30	20	1.45	0.34	0.63	1.95	31	1.45	0.2	2.46	-	-	3	
SK 30 GD 066 ET	40	30	1.45	0.97	1.77	1.65	36	1.45	0.26	2.1	-	-	3	
SK 50 GD 066 ET	60	50	1.45	2.2	1.73	1.11	56	1.50	0.72	1.7	-	-	3	
SK 20 DGD L 066 ET	30	20	1.45	0.3	0.6	1.95	27	1.40	0.2	2.46	2.15	220	3	
SK 30 DGD L 066 ET	40	30	1.45	0.55	1.15	1.65	36	1.50	0.53	2.3	1.7	370	3	
SK 50 DGD L 066 T	69	50	1.45	2.2	1.74	0.95	54	1.35	0.73	1.6	1.5	370	4	
SK 75 DGD L 066 T	81	75	1.45	3.1	2.8	0.75	64	1.35	0.9	1.2	0.9	700	4	
SK 100 DGD L 066 T	106	100	1.45	4.4	3.5	0.65	99	1.10	1.45	0.8	0.9	700	4	
600V - NPT IGBT (Standard)														
SK 45 GAL 063	45	50	2.10	1.4	1.2	1	57	1.45	0.25	1.2	-	-	2	

Footnotes: 8) Target data

IGBT Modules / SEMITOP

1

Type	IGBT							Diode			Rectifier		Module	
	$I_c @ T_s = 25^\circ\text{C}$	$I_{c, \text{nom}}$	$V_{CE(\text{sat})} @ T_j = 25^\circ\text{C typ.}$	E_{on}	E_{off}	$R_{\text{th}(j-s)}$	$I_f @ T_s = 25^\circ\text{C}$	$V_f @ T_j = 25^\circ\text{C typ.}$	E_{rr}	$R_{\text{th}(j-s)}$	$R_{\text{th}(j-s)}$	$I_{\text{FSM}} @ T_j = 25^\circ\text{C}$	Case	Circuit
	A	A	V	mJ	mJ	K/W	A	V	mJ	K/W	K/W	A		
600V - NPT IGBT (Standard)														
SK 45 GAR 063	45	50	2.10	1.4	1.2	1	57	1.45	0.25	1.2	-	-	2	
SK 80 GM 063	81	100	2.00	3	2.3	0.6	105	1.30	0.2	1.2	-	-	2	
SK 45 GB 063	45	50	2.10	1.4	1.2	1	57	1.45	0.25	1.2	-	-	2	
SK 80 GB 063	81	100	2.10	4	3	0.6	79	1.40	1.2	0.9	-	-	3	
SK 15 GH 063	20	15	2.00	0.71	0.4	1.9	20	1.45	0.45	1.2	-	-	2	
SK 25 GH 063	30	30	2.10	1.1	0.8	1.4	36	1.45	0.25	1.7	-	-	2	
SK 45 GH 063	45	50	2.10	1.4	1.2	1	57	1.30	0.9	1.2	-	-	3	
SK 13 GD 063	18	10	2.10	0.6	0.4	2	22	1.45	0.1	2.3	-	-	3	
SK 25 GD 063	30	30	2.10	1.3	0.9	1.4	36	1.45	0.25	1.7	-	-	3	
SK 45 GD 063	45	50	2.10	1.4	1.2	1	36	1.45	0.25	1.7	-	-	3	
600V - NPT IGBT (Ultrafast)														
SK 50 GAL 065	54	60	2.00	1.1	0.7	0.85	57	1.30	0.2	1.2	-	-	2	
SK 50 GAR 065	54	60	2.00	1.1	0.7	0.85	57	1.30	0.2	1.2	-	-	2	
SK 55 GARL 065 E	54	60	1.70	1.1	0.76	0.85	36	1.45	0.9	1.7	-	-	3	
SK 75 GARL 065 E	80	90	1.70	2.71	2.75	0.6	57	1.30	0.2	1.2	-	-	3	
SK 50 GB 065	54	60	2.00	1.1	0.7	0.85	64	1.45	0.55	1.1	-	-	2	
SK 50 GARL 065 F	54	60	1.70	1.03	0.8	0.85	82	1.70	-	2.3	-	-	2	
SK 50 GARL 065 USA	54	60	1.70	1.07	0.76	0.85	64	1.40	-	2.3	-	-	2	

Footnotes: 8) Target data

IGBT Modules / SEMITOP

Type	IGBT						Diode			Rectifier			Module	
	$I_c @ T_s = 25^\circ\text{C}$	$I_{c\text{nom}}$	$V_{CE(\text{sat})} @ T_j = 25^\circ\text{C typ.}$	E_{on}	E_{off}	$R_{\text{th}(j-s)}$	$I_f @ T_s = 25^\circ\text{C}$	$V_f @ T_j = 25^\circ\text{C typ.}$	E_{rr}	$R_{\text{th}(j-s)}$	$R_{\text{th}(j-s)}$	$I_{FSM} @ T_j = 25^\circ\text{C}$	Case	Circuit
	A	A	V	mJ	mJ	K/W	A	V	mJ	K/W	K/W	A		
600V - NPT IGBT (Ultrafast)														
SK 50 GH 065 F	54	60	2.00	1.07	1.76	0.85	82	1.10	0.42	1.1	-	-	3	
SK 9 DGD 065 ET	12	6	2.00	0.22	0.12	2.6	20	1.35	0.31	2.7	2.15	220	3	
SK 20 DGD 065 ET	26	20	2.00	0.66	0.4	1.7	25	1.60	-	1.7	1.7	370	3	
SK 35 GD 065 ET	45	50	2.00	1.3	0.6	1	36	1.90	0.9	1.7	-	-	3	
SK 10 BGD 065 ET	17	6	2.00	0.18	0.13	2	22	1.30	0.18	2.3	2.7	220	3	
SK 9 BGD 065 ET	12	6	2.00	0.22	0.12	2.6	20	1.35	0.31	2.7	2.15	220	3	
SK 10 DGD 065 ET	17	6	2.00	0.18	0.13	2	22	1.30	0.18	2.3	2.7	220	3	
SK 20 DGD 065 ET	24	20	2.00	0.69	0.39	1.7	25	1.60	-	1.7	2	220	3	
1200V - IGBT3 (Trench)														
SK 50 GD 126 T	68	50	1.70	4.6	6.3	0.6	62	1.35	3.6	1	-	-	4	
SK 75 GD 126 T	88	75	1.70	11.3	10	0.5	91	1.46	6	0.7	-	-	4	
SK 100 GD 126 T	114	100	1.70	9.8	11.7	0.4	118	1.50	7.3	0.55	-	-	4	
SK 10 GD 126 ET	15	8	1.70	1	1	2	25	1.90	1.4	2.1	-	-	3	
SK 15 GD 126 ET	22	15	1.70	2	1.8	1.6	25	1.60	1.4	2.1	-	-	3	
SK 25 GD 126 ET	32	25	1.70	3.3	3.1	1.2	28	1.80	2.1	1.9	-	-	3	
SK 35 GD 126 ET	40	35	1.70	4.6	4.3	1.05	34	1.80	2.9	1.7	-	-	3	
SK 10 DGD 126 ET	15	8	1.70	1	1	2	25	1.90	1.4	2.1	2.7	220	3	
SK 15 DGD 126 ET	22	15	1.70	2	1.8	1.6	25	1.60	1.1	2.1	2	220	3	
SK 25 DGD 126 T	41	25	1.70	2.8	3.1	0.9	30	1.50	2	1.7	1.5	370	4	
SK 35 DGD 126 T	52	35	1.70	3.7	4.8	0.75	38	1.50	3	1.5	1.25	370	4	
SK 50 DGD 126 T	68	50	1.70	4.6	6.3	0.6	62	1.35	3.6	1	0.9	700	4	

Footnotes: 8) Target data

IGBT Modules / SEMITOP

Type	IGBT						Diode					Rectifier		Module	
	$I_c @ T_s = 25^\circ\text{C}$	$I_{c\text{nom}}$	$V_{CE(\text{sat})} @ T_j = 25^\circ\text{C typ.}$	E_{on}	E_{off}	$R_{\text{th}(j-s)}$	$I_f @ T_s = 25^\circ\text{C}$	$V_f @ T_j = 25^\circ\text{C typ.}$	E_{rr}	$R_{\text{th}(j-s)}$	$R_{\text{th}(j-s)}$	$I_{FSM} @ T_j = 25^\circ\text{C}$	Case	Circuit	
	A	A	V	mJ	mJ	K/W	A	V	mJ	K/W	K/W	A			
1200V - IGBT4 (Trench)															
SK 35 GAL 12T4	44	35	1.85	3.27	3.3	1.21	38	2.3	1.46	1.55	-	225	2		
SK 35 GAR 12T4	44	35	1.85	3.27	3.3	1.21	38	2.3	1.46	1.55	-	225	2		
SK 25 GB 12T4	37	25	1.85	2.27	2.7	1.31	30	2.40	1.28	1.91	-	-	2		
SK 35 GB 12T4	44	35	1.85	3.27	3.3	1.21	40	2.30	1.46	1.55	-	-	2		
SK 50 GB 12T4 T	71	50	1.85	8.3	5	0.9	50	2.20	2.15	1.24	-	-	3		
SK 75 GB 12T4 T	80	75	1.85	13.6	8.2	0.74	70	2.10	3.39	0.97	-	-	3		
SK 100 GB 12T4 T	100	100	1.85	16.6	10	0.6	85	2.25	5.2	0.87	-	-	3		
SK 50 GH 12T4 T	75	50	1.80	8.3	5	0.65	56	2.20	2.15	1.05	-	-	4		
SK 100 GH 12T4 T	126	100	1.80	16.6	10	0.43	102	2.20	5.2	0.62	-	-	4		
SK 25 GH 12T4	35	25	1.85	2.27	2.7	1.31	28	2.41	1.28	1.91	-	-	3		
SK 50 GD 12T4 T	75	50	1.85	8.3	5	0.65	60	2.20	2.15	0.97	-	-	4		
SK 50 GD 12T4 Tp	75	50	1.85	8.3	5	0.65	60	2.22	2.15	0.97	-	-	4p		
SK 75 GD 12T4 T	102	75	1.85	13.6	8.2	0.51	83	2.20	3.38	0.75	-	-	4		
SK 75 GD 12T4 Tp ⁸⁾	99	75	1.85	13.6	8.2	0.51	83	2.17	3.38	0.75	-	-	4p		
SK 100 GD 12T4 T	126	100	1.85	16.6	10	0.43	102	2.25	5.2	0.62	-	-	4		
SK 10 GD 12T4 ET	17	8	1.85	0.41	0.76	2.2	15	2.38	0.41	2.7	-	-	3		
SK 15 GD 12T4 ET	27	15	1.85	0.83	1.52	1.65	21	2.38	0.82	2.34	-	-	3		
SK 25 GD 12T4 ET	37	25	1.85	2.27	2.7	1.31	30	2.40	1.28	1.91	-	-	3		
SK 25 GD 12T4 ETp ^{NEW}	37	25	1.85	2.27	2.7	1.31	28	2.41	1.28	1.91	-	-	3p		
SK 35 GD 12T4 ET	44	35	1.85	3.27	3.3	1.21	40	2.30	1.46	1.55	-	-	3		
SK 10 DGD 12T4 ET	17	8	1.85	0.41	0.75	2.2	15	2.38	0.41	2.7	2	220	3		
SK 15 DGD 12T4 ET	27	15	1.85	0.82	1.52	1.65	21	2.38	0.82	2.34	2	220	3		

Footnotes: 8) Target data

IGBT Modules / SEMITOP

Type	IGBT						Diode			Rectifier		Module		
	$I_c @ T_s = 25^\circ\text{C}$	$I_{c\text{nom}}$	$V_{CE(\text{sat})} @ T_j = 25^\circ\text{C typ.}$	E_{on}	E_{off}	$R_{\text{th}(j-s)}$	$I_f @ T_s = 25^\circ\text{C}$	$V_f @ T_j = 25^\circ\text{C typ.}$	E_{rr}	$R_{\text{th}(j-s)}$	$R_{\text{th}(j-s)}$	$I_{\text{FSM}} @ T_j = 25^\circ\text{C}$	Case	Circuit
	A	A	V	mJ	mJ	K/W	A	V	mJ	K/W	K/W	A		

1200V - IGBT4 (Trench)

SK 25 DGD L 12T4 T	45	25	1.85	2.27	2.7	0.96	30	2.40	-	1.7	1.25	370	4	
SK 35 DGD L 12T4 T	58	35	1.85	3.27	3.3	0.8	46	2.30	1.46	1.37	1.25	370	4	
SK 50 DGD L 12T4 T	75	50	1.85	8.3	5	0.65	60	2.22	2.15	0.97	0.9	700	4	

1200V - NPT IGBT (Ultrafast)

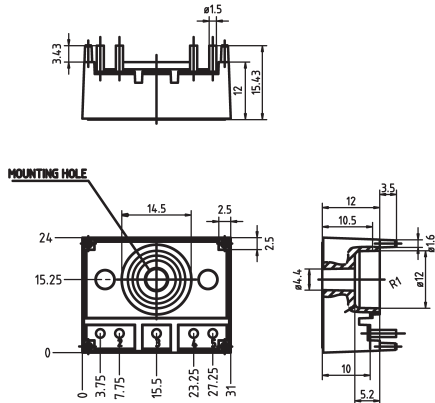
SK 60 GAL 125	51	50	3.20	8.36	3.32	0.6	43	2.00	2	1.16	-	-	2	
SK 60 GAR 125	51	50	3.20	8.36	3.32	0.6	43	2.00	2	1.16	-	-	2	
SK 60 GB 125	51	50	3.20	8.36	3.32	0.6	57	-	2	0.9	-	-	3	
SK 80 GB 125 T	85	75	3.20	9.9	5	0.32	90	2.00	1	0.65	-	-	3	

Footnotes: 8) Target data

Cases

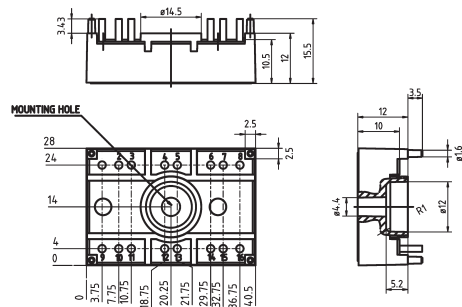
SEMISTOP 1

dimensions in mm
tolerance system: ISO 2768-m



SEMISTOP 2

dimensions in mm
tolerance system: ISO 2768-m



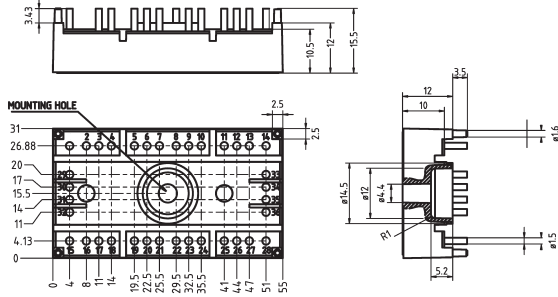
Dimensions in mm

IGBT Modules / SEMITOP

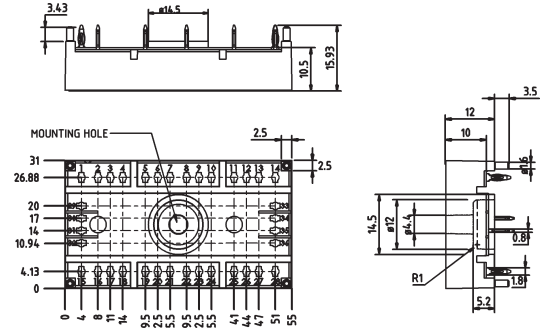
Cases

SEMISTOP 3

dimensions in mm
tolerance system: ISO 2768-m

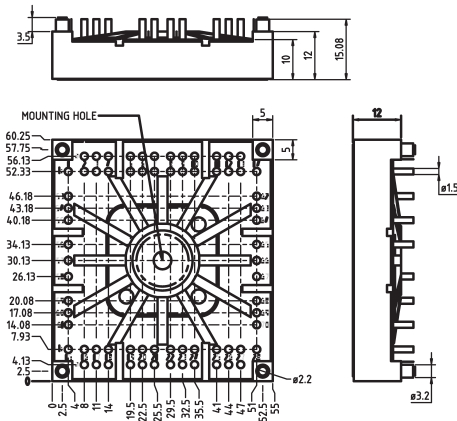


SEMISTOP 3 Press-Fit

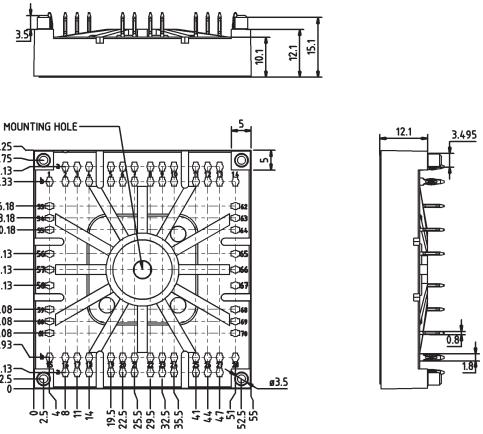


SEMISTOP 4

dimensions in mm
tolerance system: ISO 2768-m

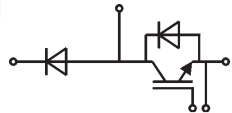
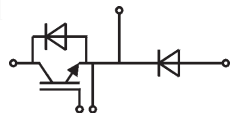
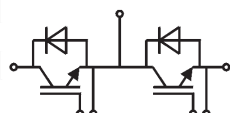
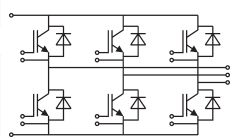
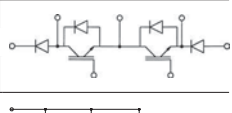
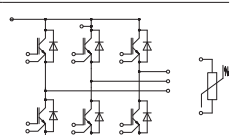
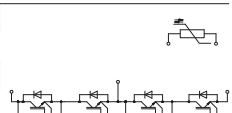
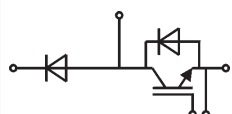
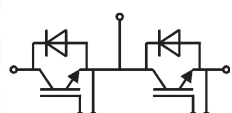


SEMISTOP 4 Press-Fit



Dimensions in mm

IGBT Modules / SEMiX

Type	IGBT						Diode				Module		Circuit
	$I_c @ T_c = 25^\circ\text{C}$ A	I_{cnom} A	$V_{CE(EM)} @ T_j = 25^\circ\text{C typ.}$ V	E_{on} mJ	E_{off} mJ	$R_{th(j-c)}$ K/W	$I_f @ T_c = 25^\circ\text{C}$ A	$V_f @ T_j = 25^\circ\text{C typ.}$ V	E_{rr} mJ	$R_{th(j-c)}$ K/W	Case	$R_{th(c-s)}$ K/W	
600V - IGBT3 (Trench)													
SEMiX402GAL066HDs	502	400	1.45	22	24	0.12	543	1.40	10	0.15	2s	0.045	
SEMiX603GAL066HDs	720	600	1.45	12	43	0.087	771	1.40	13	0.11	3s	0.04	
SEMiX402GAR066HDs													
SEMiX603GAR066HDs	720	600	1.45	12	43	0.087	771	1.40	13	0.11	3s	0.04	
SEMiX202GB066HDs	272	200	1.45	6	8	0.21	291	1.40	6.5	0.27	2s	0.045	
SEMiX302GB066HDs	379	300	1.45	11.5	15	0.16	419	1.40	7.5	0.19	2s	0.045	
SEMiX402GB066HDs	502	400	1.45	22	24	0.12	543	1.40	10	0.15	2s	0.045	
SEMiX603GB066HDs	720	600	1.45	12	43	0.087	771	1.40	13	0.11	3s	0.04	
SEMiX101GD066HDs	139	100	1.45	3	4	0.41	151	1.40	4.5	0.51	13	0.04	
SEMiX151GD066HDs	200	150	1.45	3.8	6.1	0.29	219	1.40	5.8	0.36	13	0.04	
SEMiX201GD066HDs	258	200	1.45	5	8	0.23	284	1.40	7.5	0.28	13	0.04	
650V - IGBT4 (Trench)													
SEMiX205GARL07E4 ⁸⁾	222	200	1.55	2.24	7.89	0.28	67	1.37	5.5	1.2	5p	0.009	
SEMiX305GARL07E4 ⁸⁾	319	300	1.55	3.36	11.8	0.2	67	1.37	8.25	1.2	5p	0.009	
SEMiX405GARL07E4 ⁸⁾	443	400	1.55	4.49	15.78	0.15	67	1.37	11	1.2	5p	0.009	
SEMiX305GD07E4 ⁸⁾	310	300	1.55	5.54	20.52	0.21	277	1.40	4.96	0.33	5p	0.009	
SEMiX155MLI07E4 ⁸⁾	187	150	1.55	1.5	7	0.31	125	1.40	3	0.64	5p	0.009	
SEMiX205MLI07E4 ⁸⁾	258	200	1.55	2.5	14	0.22	250	1.40	4	0.32	5p	0.009	
SEMiX305MLI07E4 ⁸⁾	367	300	1.55	2.5	18	0.16	250	1.40	7	0.32	5p	0.009	
SEMiX405MLI07E4 ⁸⁾	507	400	1.55	4	20	0.12	366	1.40	9	0.22	5p	0.009	
1200V - V-IGBT													
SEMiX151GAL12Vs	231	150	1.75	19.4	17.1	0.19	189	2.14	11.5	0.31	1s	0.075	
SEMiX151GB12Vs	231	150	1.75	19.4	17.1	0.19	189	2.14	11.5	0.31	1s	0.075	
SEMiX202GB12Vs	310	200	1.75	24.9	24.1	0.14	229	2.20	14.5	0.26	2s	0.045	
SEMiX223GB12Vs	323	225	1.85	19.9	27.2	0.14	263	2.17	16.4	0.23	3s	0.04	
SEMiX302GB12Vs	448	300	1.75	37.3	36.1	0.1	356	2.14	21.8	0.17	2s	0.045	
SEMiX303GB12Vs	448	300	1.75	26.5	36.3	0.1	327	2.20	21.4	0.19	3s	0.04	
SEMiX404GB12Vs	596	400	1.75	39.1	52.3	0.075	440	2.20	34.3	0.14	4s	0.03	
SEMiX453GB12Vs	673	450	1.75	39.8	54.4	0.067	516	2.14	32.7	0.12	3s	0.04	
SEMiX603GB12Vs	800	600	1.85	50	83	0.057	516	2.42	40	0.12	3s	0.04	

Footnotes: 8) Target data

IGBT Modules / SEMiX

Type	IGBT						Diode				Module		Circuit	
	$I_c @ T_c = 25^\circ\text{C}$ A	I_{cnom} A	$V_{CE(EMT)} @ T_j = 25^\circ\text{C typ.}$ V	E_{on} mJ	E_{off} mJ	$R_{th(j-c)}$ K/W	$I_F @ T_c = 25^\circ\text{C}$ A	$V_F @ T_j = 25^\circ\text{C typ.}$ V	E_{rr} mJ	$R_{th(j-c)}$ K/W	Case	$R_{th(c-s)}$ K/W		
1200V - V-IGBT														
SEMiX604GB12Vs	880	600	1.75	58.7	78.5	0.051	707	2.14	49.5	0.086	4s	0.03		
SEMiX101GD12Vs	159	100	1.75	12.9	11.4	0.27	121	2.20	7.7	0.48	13	0.04		
SEMiX151GD12Vs	231	150	1.75	19.4	17.1	0.19	189	2.14	11.5	0.31	13	0.04		
SEMiX223GD12Vc	323	225	1.85	19.9	27.2	0.14	263	2.17	16.4	0.23	33c	0.014		
SEMiX303GD12Vc	448	300	1.75	26.5	36.3	0.1	327	2.20	21.4	0.19	33c	0.014		
SEMiX453GD12Vc	673	450	1.75	39.8	54.4	0.067	516	2.14	32.7	0.12	33c	0.014		
1200V - IGBT4 (Trench)														
SEMiX151GAL12E4s	232	150	1.80	16.6	18.4	0.19	189	2.14	8.9	0.31	1s	0.075		
SEMiX302GAL12E4s	463	300	1.80	30	44	0.096	356	2.14	19	0.17	2s	0.045		
SEMiX453GAL12E4s	683	450	1.80	45	66.5	0.065	544	2.14	28	0.11	3s	0.04		
SEMiX604GAL12E4s	916	600	1.80	35	110	0.049	707	2.14	44	0.086	4s	0.03		
SEMiX151GAR12E4s	232	150	1.80	16.6	18.4	0.19	189	2.14	8.9	0.31	1s	0.075		
SEMiX302GAR12E4s	463	300	1.80	30	44	0.096	356	2.14	19	0.17	2s	0.045		
SEMiX453GAR12E4s	683	450	1.80	45	66.5	0.065	544	2.14	28	0.11	3s	0.04		
SEMiX604GAR12E4s	916	600	1.80	35	110	0.049	707	2.14	44	0.086	4s	0.03		
SEMiX151GB12E4s	232	150	1.80	16.6	18.4	0.19	189	2.14	8.9	0.31	1s	0.075		
SEMiX202GB12E4s	312	200	1.80	22	27.9	0.14	229	2.20	12	0.26	2s	0.045		
SEMiX302GB12E4s	463	300	1.80	30	44	0.096	356	2.14	19	0.17	2s	0.045		
SEMiX303GB12E4s	466	300	1.80	30	41.2	0.095	338	2.20	17.7	0.18	3s	0.04		
SEMiX303GB12E4p	469	300	1.80	23	38	0.094	378	2.20	23	0.15	3p	0.009		
SEMiX404GB12E4s	618	400	1.80	27	59.7	0.072	440	2.20	26.4	0.14	4s	0.03		
SEMiX453GB12E4s	683	450	1.80	45	66.5	0.065	544	2.14	28	0.11	3s	0.04		
SEMiX453GB12E4p	678	450	1.80	25	57	0.066	578	2.14	37	0.1	3p	0.009		
SEMiX604GB12E4s	916	600	1.80	35	110	0.049	707	2.14	44	0.086	4s	0.03		
SEMiX603GB12E4p	1110	600	1.80	69	80	0.037	856	2.08	40	0.065	3p	0.009		
SEMiX453GB12E4Ip	678	450	1.80	33	57	0.066	578	2.14	39	0.1	3Ip	0.009		
SEMiX603GB12E4Ip	1110	600	1.80	63	80	0.037	856	2.08	40	0.065	3Ip	0.009		
SEMiX71GD12E4s	115	75	1.85	7.5	9	0.38	97	2.17	5.3	0.58	13	0.04		
SEMiX101GD12E4s	160	100	1.80	10.8	13.3	0.27	121	2.20	6.5	0.48	13	0.04		
SEMiX151GD12E4s	232	150	1.80	14.1	19.2	0.19	189	2.14	8.9	0.31	13	0.04		

Footnotes: 8) Target data

IGBT Modules / SEMiX

Type	IGBT						Diode				Module		Circuit
	$I_c @ T_c = 25^\circ\text{C}$ A	I_{cnom} A	$V_{CE(EMT)} @ T_j = 25^\circ\text{C typ.}$ V	E_{on} mJ	E_{off} mJ	$R_{th(j-c)}$ K/W	$I_f @ T_c = 25^\circ\text{C}$ A	$V_f @ T_j = 25^\circ\text{C typ.}$ V	E_{rr} mJ	$R_{th(j-c)}$ K/W	Case	$R_{th(c-s)}$ K/W	
1200V - IGBT4 (Trench)													
SEMiX223GD12E4c	333	225	1.85	22	31.4	0.135	270	2.17	17.2	0.22	33c	0.014	
SEMiX303GD12E4c	466	300	1.80	29.4	41.8	0.095	338	2.20	22.9	0.18	33c	0.014	
SEMiX453GD12E4c	683	450	1.80	52	67.8	0.065	544	2.14	28	0.11	33c	0.014	
SEMiX205GD12E4 ⁸⁾	326	200	1.80	24.53	38.62	0.14	235	2.20	23.14	0.25	5p	0.009	
SEMiX155MLI12E4 ⁸⁾	164	75	1.85	3.5	19.6	0.2	115	2.17	5.6	0.44	5p	0.009	
SEMiX205MLI12E4 ⁸⁾	301	200	1.80	5	28	0.15	180	2.20	8	0.38	5p	0.009	
SEMiX205TMLI12E4B ⁸⁾	271	200	1.80	3	11.25	0.18	268	1.75	5.2	0.3	5p	0.009	
SEMiX205TMLI12E4C ⁸⁾	313	200	1.80	8	15	0.14	268	1.75	16	0.3	5p	0.009	
SEMiX305TMLI12E4B ⁸⁾	407	300	1.80	4.5	21	0.12	405	1.98	8.8	0.16	5p	0.009	
SEMiX305TMLI12E4C ⁸⁾	451	300	1.80	10	20	0.1	408	1.72	21	0.2	5p	0.009	
SEMiX405TMLI12E4B ⁸⁾	543	400	1.80	6	28	0.09	422	2.20	11.8	0.15	5p	0.009	
1200V - IGBT3 (Trench)													
SEMiX452GAL126HDs	455	300	1.70	35	45	0.083	394	1.60	33	0.15	2s	0.045	
SEMiX703GAL126HDs	642	450	1.70	32	68	0.061	561	1.60	60	0.11	3s	0.04	
SEMiX703GAR126HDs	642	450	1.70	32	68	0.061	561	1.60	60	0.11	3s	0.04	
SEMiX252GB126HDs	242	150	1.70	20	21	0.15	228	1.60	18	0.24	2s	0.045	
SEMiX302GB126HDs	311	200	1.70	30	26	0.12	292	1.60	22.5	0.19	2s	0.045	
SEMiX353GB126HDs	364	225	1.70	26.5	32.5	0.1	329	1.60	29	0.17	3s	0.04	
SEMiX452GB126HDs	455	300	1.70	35	45	0.083	394	1.60	33	0.15	2s	0.045	
SEMiX503GB126HDs	466	300	1.70	28	44	0.08	431	1.60	32.5	0.13	3s	0.04	
SEMiX604GB126HDs	590	400	1.70	36	60	0.065	533	1.60	46	0.11	4s	0.03	
SEMiX703GB126HDs	642	450	1.70	32	68	0.061	561	1.60	60	0.11	3s	0.04	
SEMiX904GB126HDs	821	600	1.70	60	88	0.05	752	1.60	75	0.081	4s	0.03	
SEMiX101GD126HDs	129	75	1.70	10	11	0.27	117	1.60	9	0.46	13	0.04	
SEMiX151GD126HDs	168	100	1.70	12	14	0.21	152	1.60	11.5	0.36	13	0.04	
SEMiX251GD126HDs	242	150	1.70	19	22	0.15	207	1.60	14.5	0.28	13	0.04	

Footnotes: 8) Target data

IGBT Modules / SEMiX

1

Type	IGBT						Diode				Module		Circuit
	$I_c @ T_c = 25^\circ\text{C}$ A	I_{cnom} A	$V_{CE(EM)} @ T_j = 25^\circ\text{C typ.}$ V	E_{on} mJ	E_{off} mJ	$R_{th(j-c)}$ K/W	$I_f @ T_c = 25^\circ\text{C}$ A	$V_f @ T_j = 25^\circ\text{C typ.}$ V	E_{rr} mJ	$R_{th(j-c)}$ K/W	Case	$R_{th(c-s)}$ K/W	
1200V - IGBT3 (Trench)													
SEMiX353GD126HDc	364	225	1.70	26.5	32.5	0.1	329	1.60	29	0.17	33c	0.014	
SEMiX503GD126HDc	466	300	1.70	28	44	0.08	412	1.60	32.5	0.14	33c	0.014	
SEMiX703GD126HDc	642	450	1.70	32	68	0.061	561	1.59	60	0.11	33c	0.014	
1700V - IGBT4 (Trench)													
SEMiX302GAL17E4s	516	300	1.90	140	122	0.083	324	1.98	70	0.184	2s	0.045	
SEMiX453GAL17E4s	762	450	1.90	250	190	0.056	482	1.98	100	0.125	3s	0.04	
SEMiX151GB17E4s	260	150	1.90	52	60	0.162	169	1.98	41	0.345	1s	0.075	
SEMiX202GB17E4s	321	200	1.90	75	82	0.122	213	2.00	55	0.276	2s	0.045	
SEMiX302GB17E4s	516	300	1.90	140	122	0.083	324	1.98	70	0.184	2s	0.045	
SEMiX303GB17E4s	477	300	1.90	140	125	0.083	311	2.00	85	0.191	3s	0.04	
SEMiX404GB17E4s	633	400	1.90	190	165	0.062	412	2.00	97	0.145	4s	0.03	
SEMiX453GB17E4s	762	450	1.90	250	190	0.056	482	1.98	100	0.125	3s	0.04	
SEMiX604GB17E4s	1015	600	1.90	255	255	0.042	629	1.98	150	0.095	4s	0.03	
SEMiX453GB17E4Ip	731	450	1.90	153	150	0.06	557	1.98	73	0.1	3Ip	0.009	
SEMiX453GD17E4c	762	450	1.90	186	183	0.056	482	1.98	122	0.125	33c	0.014	
1700V - IGBT3 (Trench)													
SEMiX653GAL176HDs	619	450	2.00	300	180	0.054	545	1.70	73	0.11	3s	0.04	
SEMiX653GAR176HDs	619	450	2.00	300	180	0.054	545	1.70	73	0.11	3s	0.04	
SEMiX252GB176HDs	246	150	2.00	90	55	0.12	288	1.55	32	0.19	2s	0.045	
SEMiX302GB176HDs	308	200	2.00	130	77	0.1	389	1.50	43	0.15	2s	0.045	
SEMiX353GB176HDs	353	225	2.00	155	85	0.086	428	1.55	45	0.13	3s	0.04	
SEMiX452GB176HDs	437	300	2.00	180	110	0.073	389	1.70	46	0.15	2s	0.045	
SEMiX453GB176HDs	444	300	2.00	215	125	0.071	545	1.50	65	0.11	3s	0.04	
SEMiX604GB176HDs	567	400	2.00	215	165	0.058	740	1.50	95	0.081	4s	0.03	
SEMiX653GB176HDs	619	450	2.00	300	180	0.054	545	1.70	73	0.11	3s	0.04	
SEMiX854GB176HDs	779	600	2.00	300	250	0.045	740	1.70	170	0.081	4s	0.03	

Footnotes: 8) Target data

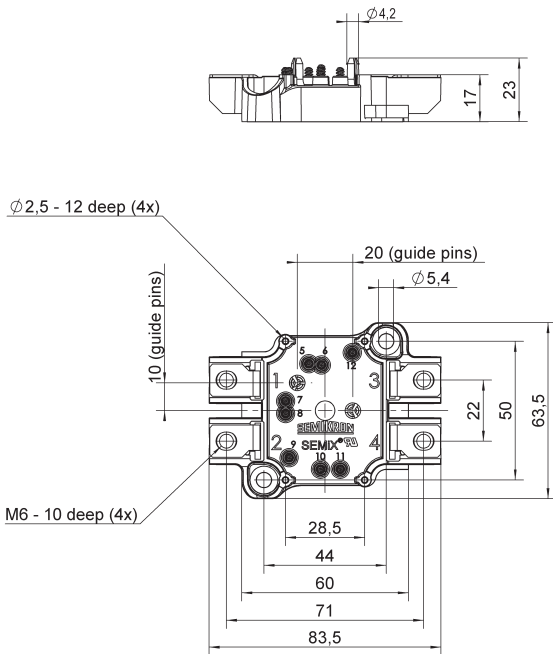
IGBT Modules / SEMiX

Type	IGBT						Diode				Module		
	$I_c @ T_c = 25^\circ\text{C}$	I_{cnom}	$V_{CE(EM)} @ T_j = 25^\circ\text{C typ.}$	E_{on}	E_{off}	$R_{th(j-c)}$	$I_f @ T_c = 25^\circ\text{C}$	$V_f @ T_j = 25^\circ\text{C typ.}$	E_{rr}	$R_{th(j-c)}$	Case	$R_{th(c-s)}$	Circuit
	A	A	V	mJ	mJ	K/W	A	V	mJ	K/W		K/W	
1700V - IGBT3 (Trench)													
SEMiX353GD176HDc	353	225	2.00	155	85	0.086	428	1.55	45	0.13	33c	0.014	
SEMiX453GD176HDc	444	300	2.00	215	125	0.071	545	1.50	65	0.11	33c	0.014	
SEMiX653GD176HDc	619	450	2.00	300	180	0.054	545	1.70	73	0.11	33c	0.014	

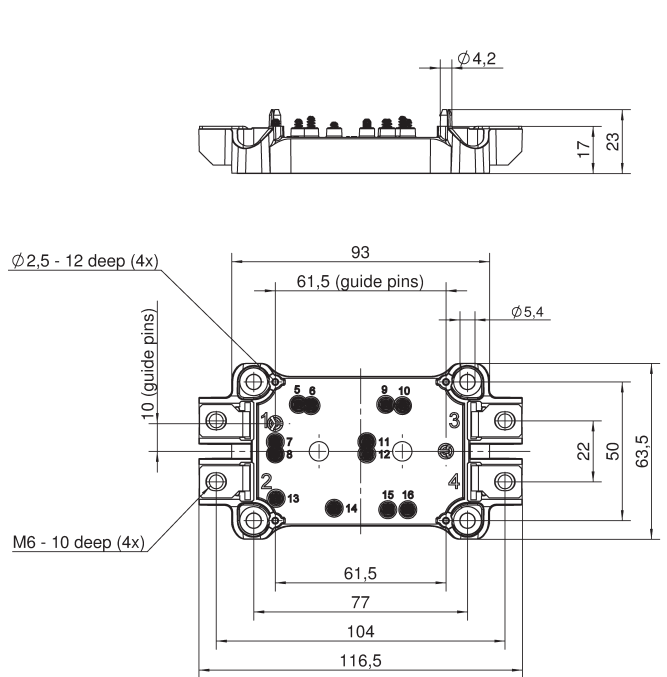
Footnotes: 8) Target data

Cases

SEMiX 1s



SEMiX 2s

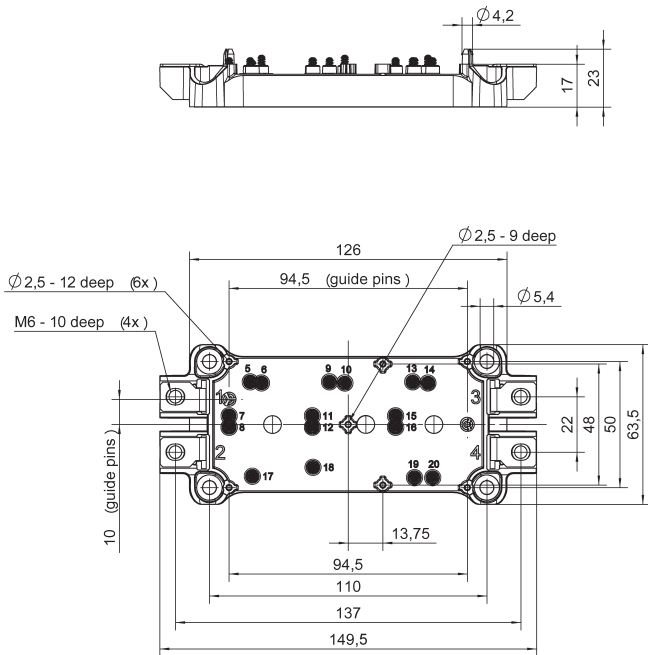


Dimensions in mm

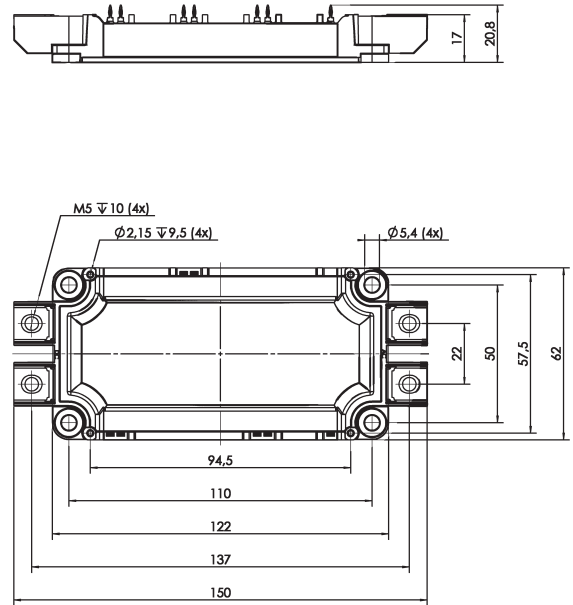
IGBT Modules / SEMiX

Cases

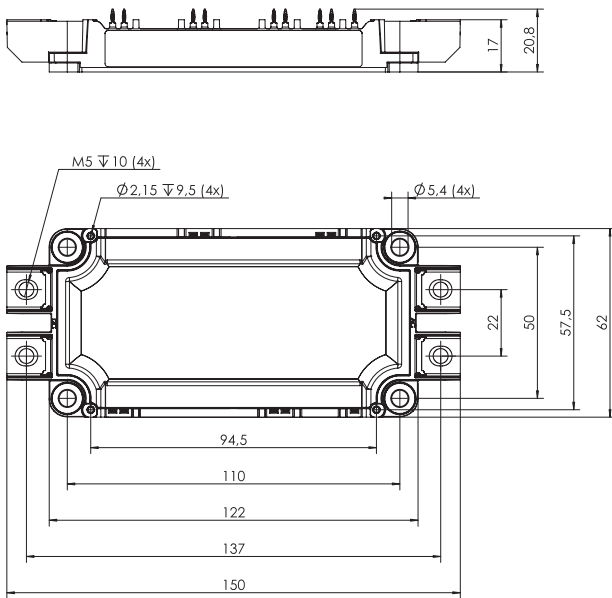
SEMIX 3s



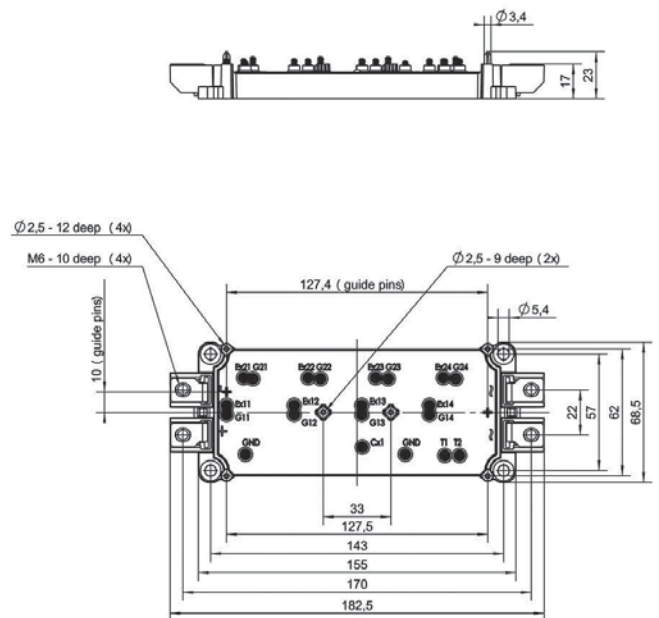
SEMIX 3p



SEMIX 3Ip



SEMIX 4s

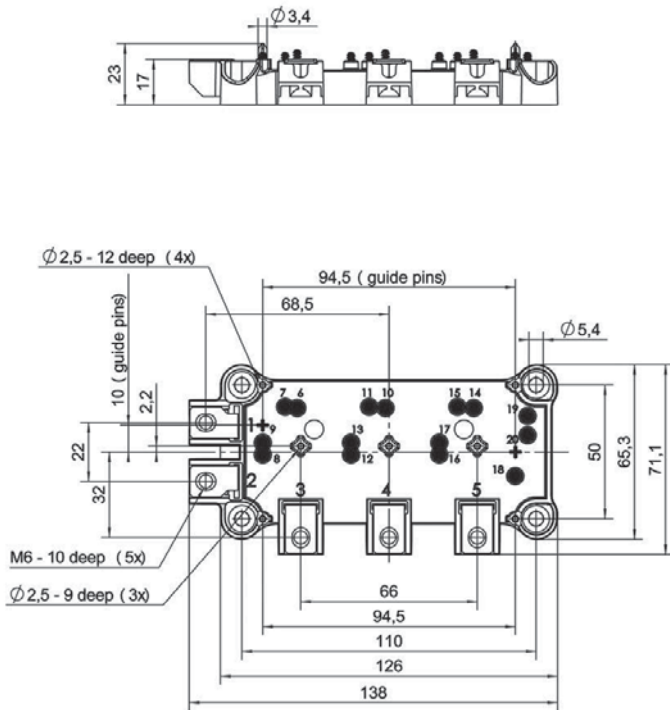


Dimensions in mm

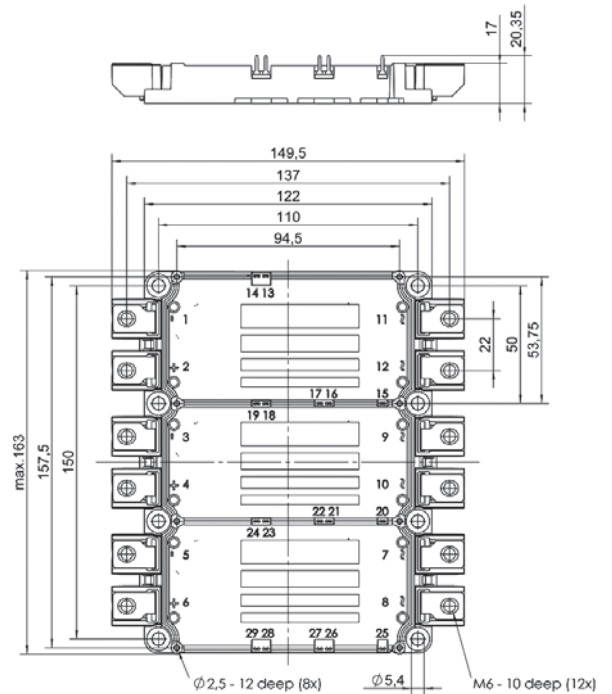
IGBT Modules / SEMiX

Cases

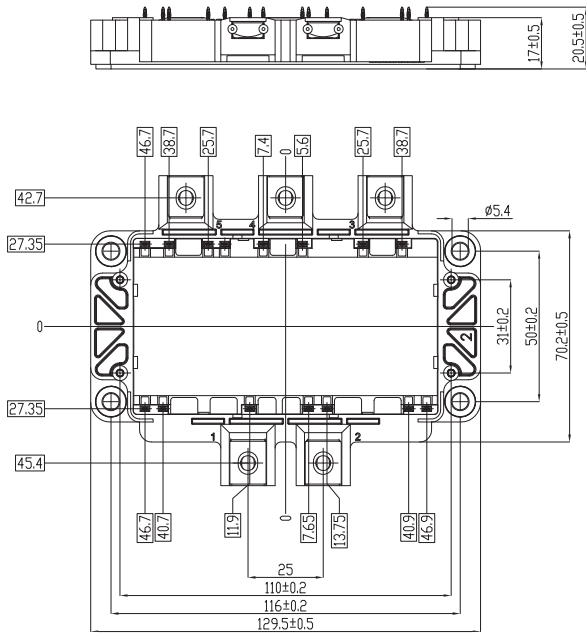
SEMIX 13



SEMIX 33c



SEMIX 5p



Dimensions in mm

IGBT Modules / SEMITRANS

1

Type	IGBT						Diode				Module		Circuit
	$I_c @ T_c = 25^\circ\text{C}$	I_{cnom}	$V_{CE(sat)} @ T_j = 25^\circ\text{C typ.}$	E_{on}	E_{off}	$R_{th(j-c)}$	$I_f @ T_c = 25^\circ\text{C}$	$V_f @ T_j = 25^\circ\text{C typ.}$	E_{rr}	$R_{th(j-c)}$	Case	$R_{th(c-s)}$	
	A	A	V	mJ	mJ	K/W	A	V	mJ	K/W		K/W	
600V - IGBT3 (Trench)													
SKM145GB066D	195	150	1.45	8.5	5.5	0.3	150	1.40	3.5	0.5	2	0.05	
SKM195GB066D	265	200	1.45	14	8	0.22	200	1.40	5.6	0.4	2	0.05	
SKM300GB066D	390	300	1.45	7.5	11.5	0.15	350	1.38	10.5	0.25	3	0.038	
SKM400GB066D	500	400	1.45	8	16	0.12	450	1.40	14	0.2	3	0.038	
SKM600GB066D	760	600	1.45	7.5	29.5	0.08	700	1.38	25	0.125	3	0.038	
SKM200GARL066T ¹⁾	280	200	1.45	2.24	7.89	0.21	270	1.45	4	0.39	5	0.038	
SKM300GARL066T ¹⁾	400	300	1.45	3.5	10.1	0.15	400	1.45	4	0.26	5	0.038	
SKM400GARL066T ¹⁾	504	400	1.45	4.48	15.78	0.12	421	1.54	8	0.28	5	0.038	
SKM150MLI066TAT ¹⁾	200	150	1.45	1.7	5.1	0.29	200	1.35	2	0.52	5	0.038	
SKM200MLI066TAT ¹⁾	280	200	1.45	2.53	6.82	0.21	270	1.4	4	0.39	5	0.038	
SKM300MLI066TAT ¹⁾	400	300	1.45	3.5	10.1	0.15	324	1.35	4	0.25	5	0.038	
600V - NPT IGBT (Standard)													
SKM75GAL063D	100	75	2.1	3	2.5	0.35	75	1.55	0.53	0.72	2	0.05	
SKM300GAL063D	400	300	2.1	14	13	0.09	250	1.65	4	0.25	3	0.038	
SKM75GAR063D	100	75	2.1	3	2.5	0.35	75	1.55	0.53	0.72	2	0.05	
SKM300GAR063D	400	300	2.1	14	13	0.09	250	1.65	4	0.25	3	0.038	
SKM50GB063D	70	50	2.10	2.5	1.8	0.5	75	1.35	0.48	1	2	0.05	
SKM75GB063D	100	75	2.1	3	2.5	0.35	75	1.55	0.53	0.72	2	0.05	
SKM100GB063D	130	100	2.1	4	3	0.27	100	1.55	1.5	0.6	2	0.05	
SKM200GB063D	260	200	2.1	11	7.5	0.14	200	1.55	2.1	0.3	3	0.038	
SKM300GB063D	400	300	2.1	14	13	0.09	250	1.65	4	0.25	3	0.038	
1200V - V-IGBT													
SKM150GAL12V	231	150	1.75	13.5	14.2	0.19	189	2.14	8.9	0.31	2	0.05	
SKM400GAL12V	612	400	1.75	39	42	0.072	440	2.20	26	0.14	3	0.038	
SKM400GAR12V	612	400	1.75	39	42	0.072	440	2.20	26	0.14	3	0.038	
SKM300GA12V	420	300	1.85	23	33	0.11	353	2.17	21	0.17	4	0.038	
SKM400GA12V	612	400	1.75	39	42	0.072	440	2.20	26	0.14	4	0.038	
SKM600GA12V	908	600	1.75	76	76	0.049	707	2.14	43	0.086	4	0.038	
SKM50GB12V	77	50	1.85	5	4	0.53	65	2.22	3.6	0.84	2	0.05	
SKM75GB12V	114	75	1.85	6.7	7.1	0.38	97	2.17	4.2	0.58	2	0.05	
SKM100GB12V	159	100	1.75	10.7	8.7	0.27	121	2.20	5.7	0.48	2	0.05	
SKM150GB12V	231	150	1.75	13.5	14.2	0.19	189	2.14	8.9	0.31	2	0.05	
SKM150GB12VG	222	150	1.85	10	16.5	0.2	187	2.17	11	0.31	3	0.038	

Footnotes: 1) New product

IGBT Modules / SEMITRANS

Type	IGBT						Diode				Module		Circuit
	$I_c @ T_c = 25^\circ\text{C}$	I_{cnom}	$V_{CE(sat)} @ T_j = 25^\circ\text{C typ.}$	E_{on}	E_{off}	$R_{th(j-c)}$	$I_f @ T_c = 25^\circ\text{C}$	$V_f @ T_j = 25^\circ\text{C typ.}$	E_{rr}	$R_{th(j-c)}$	Case	$R_{th(c-s)}$	
	A	A	V	mJ	mJ	K/W	A	V	mJ	K/W		K/W	
1200V - V-IGBT													
SKM200GB12V	311	200	1.75	14	22	0.14	229	2.20	13	0.26	3	0.038	
SKM300GB12V	420	300	1.85	23	33	0.11	353	2.17	21	0.17	3	0.038	
SKM400GB12V	612	400	1.75	39	42	0.072	440	2.20	26	0.14	3	0.038	
1200V - IGBT4 (Trench)													
SKM200GAL12E4	313	200	1.80	21	27	0.14	229	2.20	13	0.26	3	0.038	
SKM300GAL12E4	422	300	1.85	27	39	0.11	353	2.17	23	0.17	3	0.038	
SKM400GAL12E4	616	400	1.80	33	56	0.072	440	2.20	30.5	0.14	3	0.038	
SKM200GAR12E4	313	200	1.80	21	27	0.14	229	2.20	13	0.26	3	0.038	
SKM300GAR12E4	422	300	1.85	27	39	0.11	353	2.17	23	0.17	3	0.038	
SKM400GAR12E4	616	400	1.80	33	56	0.072	440	2.20	30.5	0.14	3	0.038	
SKM300GA12E4	422	300	1.85	23.4	35	0.11	353	2.17	22.2	0.17	4	0.038	
SKM400GA12E4	616	400	1.80	28	59	0.072	440	2.20	37	0.14	4	0.038	
SKM600GA12E4	913	600	1.80	74	84	0.049	707	2.14	38	0.086	4	0.038	
SKM900GA12E4	1305	900	1.83	130	121	0.035	871	2.31	53	0.07	4	0.038	
SKM200GB12E4	313	200	1.80	21	27	0.14	229	2.20	13	0.26	3	0.038	
SKM300GB12E4	422	300	1.85	27	39	0.11	353	2.17	23	0.17	3	0.038	
SKM400GB12E4	616	400	1.80	33	56	0.072	440	2.20	30.5	0.14	3	0.038	
SKM450GB12E4	700	450	1.82	32	60	0.062	440	2.31	28	0.14	3	0.038	
SKM450GM12E4 ¹⁾	700	450	1.82	32	60	0.062	440	2.31	28	0.14	3	0.038	
1200V - IGBT4 Fast (Trench)													
SKM50GAL12T4	81	50	1.85	5.5	4.5	0.53	65	2.22	3.6	0.84	2	0.05	
SKM100GAL12T4	160	100	1.80	15	10.2	0.27	121	2.20	5.9	0.48	2	0.05	
SKM150GAL12T4	232	150	1.80	19.2	15.8	0.19	189	2.14	13	0.31	2	0.05	
SKM200GAL12T4	313	200	1.80	21	20	0.14	229	2.20	13	0.26	3	0.038	
SKM300GAL12T4	422	300	1.85	27	29	0.11	353	2.17	23	0.17	3	0.038	
SKM400GAL12T4	616	400	1.80	33	42	0.072	440	2.20	30.5	0.14	3	0.038	
SKM150GAR12T4	232	150	1.80	19.2	15.8	0.19	189	2.14	13	0.31	2	0.05	
SKM400GAR12T4	616	400	1.80	33	42	0.072	440	2.20	30.5	0.14	3	0.038	
SKM300GA12T4	422	300	1.85	23.4	26	0.11	353	2.17	22.2	0.17	4	0.038	
SKM400GA12T4	616	400	1.80	28	44	0.072	440	2.20	37	0.14	4	0.038	
SKM600GA12T4	913	600	1.80	74	63	0.049	707	2.14	38	0.086	4	0.038	
SKM50GB12T4	81	50	1.85	5.5	4.5	0.53	65	2.22	3.8	0.84	2	0.05	
SKM75GB12T4	115	75	1.85	11	6.9	0.38	97	2.17	4.7	0.58	2	0.05	
SKM100GB12T4	160	100	1.80	15	10.2	0.27	121	2.20	5.9	0.48	2	0.05	
SKM100GB12T4G	154	100	1.85	16.1	8.6	0.29	118	2.22	6	0.49	3	0.038	
SKM150GB12T4	232	150	1.80	19.2	15.8	0.19	189	2.14	13	0.31	2	0.05	

Footnotes: 1) New product

IGBT Modules / SEMITRANS

1

Type	IGBT						Diode				Module		
	$I_c @ T_c = 25^\circ\text{C}$	I_{cnom}	$V_{CE(sat)} @ T_j = 25^\circ\text{C typ.}$	E_{on}	E_{off}	$R_{th(j-c)}$	$I_f @ T_c = 25^\circ\text{C}$	$V_f @ T_j = 25^\circ\text{C typ.}$	E_{rr}	$R_{th(j-c)}$	Case	$R_{th(c-s)}$	Circuit
	A	A	V	mJ	mJ	K/W	A	V	mJ	K/W		K/W	
1200V - IGBT4 Fast (Trench)													
SKM150GB12T4G	223	150	1.85	18.7	14.1	0.2	183	2.17	9	0.32	3	0.038	
SKM200GB12T4	313	200	1.80	21	20	0.14	229	2.20	13	0.26	3	0.038	
SKM300GB12T4	422	300	1.85	27	29	0.11	353	2.17	23	0.17	3	0.038	
SKM400GB12T4	616	400	1.80	33	42	0.072	440	2.20	30.5	0.14	3	0.038	
SKM150GM12T4G	229	150	1.85	19.2	15.8	0.19	187	2.17	13	0.31	3	0.038	
SKM200GM12T4	313	200	1.80	21	20	0.14	229	2.20	13	0.26	3	0.038	
SKM300GM12T4	422	300	1.85	27	29	0.11	353	2.17	23	0.17	3	0.038	
SKM400GM12T4	616	400	1.80	33	42	0.072	440	2.20	30.5	0.14	3	0.038	
SKM300GBD12T4	422	300	1.85	27	29	0.11	56	2.41	30.5	0.94	3	0.038	
1200V - IGBT3 (Trench)													
SKM195GAL126D	220	150	1.70	16	24.5	0.16	170	2.00	5.8	0.32	2	0.05	
SKM200GAL126D	260	150	1.70	18	24	0.13	200	1.60	18	0.3	3	0.038	
SKM400GAL126D	470	300	1.70	29	48	0.08	400	1.60	27	0.18	3	0.038	
SKM600GAL126D	660	400	1.70	39	64	0.055	490	1.60	41	0.125	3	0.038	
SKM600GA126D	660	400	1.70	39	64	0.055	490	1.60	41	0.125	4	0.038	
SKM800GA126D	960	600	1.70	65	95	0.042	680	1.69	59	0.09	4	0.038	
SKM195GB126D	220	150	1.70	16	24.5	0.16	170	2.00	5.8	0.32	2	0.05	
SKM200GB126D	260	150	1.70	18	24	0.13	200	1.60	18	0.3	3	0.038	
SKM300GB126D	310	200	1.70	21	33	0.12	250	1.60	18	0.25	3	0.038	
SKM400GB126D	470	300	1.70	29	48	0.08	400	1.64	27	0.18	3	0.038	
SKM600GB126D	660	400	1.70	39	64	0.055	490	1.60	41	0.125	3	0.038	
1200V - NPT IGBT (Ultrafast)													
SKM200GAL125D	200	150	3.3	14	8	0.09	200	2.06	8	0.25	3	0.038	
SKM400GAL125D	400	300	3.3	17	18	0.05	390	2.06	16	0.125	3	0.038	
SKM200GAR125D	200	150	3.3	14	8	0.09	200	2.06	8	0.25	3	0.038	
SKM400GAR125D	400	300	3.3	17	18	0.05	390	2.06	16	0.125	3	0.038	
SKM600GA125D	580	400	3.3	30	22	0.041	500	2.00	24	0.09	4	0.038	
SKM800GA125D	760	600	3.20	88	48	0.03	720	2.3	28	0.07	4	0.038	
SKM100GB125DN	100	75	3.3	9	3.5	0.18	95	2.06	4	0.5	2N	0.05	
SKM200GB125D	200	150	3.3	14	8	0.09	200	2.06	8	0.25	3	0.038	
SKM300GB125D	300	200	3.3	16	11	0.075	260	2.00	13	0.18	3	0.038	
SKM400GB125D	400	300	3.3	17	18	0.05	390	2.06	16	0.125	3	0.038	

Footnotes: 1) New product

IGBT Modules / SEMITRANS

Type	IGBT						Diode				Module		Circuit
	$I_c @ T_c = 25^\circ\text{C}$ A	I_{cnom} A	$V_{CE(sat)} @ T_j = 25^\circ\text{C typ.}$ V	E_{on} mJ	E_{off} mJ	$R_{th(j-c)}$ K/W	$I_f @ T_c = 25^\circ\text{C}$ A	$V_f @ T_j = 25^\circ\text{C typ.}$ V	E_{rr} mJ	$R_{th(j-c)}$ K/W	Case	$R_{th(c-s)}$ K/W	
1200V - NPT IGBT (Ultrafast)													
SKM25GD125D ¹⁾	39	25	3.20	3.9	1.6	0.56	47	2.13	1.1	1	6	0.05	
SKM50GD125D ¹⁾	73	50	3.20	8	3.2	0.32	77	2.00	2.1	0.6	6	0.05	
SKM25GAH125D ¹⁾	39	25	3.20	3.9	1.6	0.56	47	2.13	1.1	1	6	0.05	
1700V - IGBT3 (Trench)													
SKM145GAL176D	160	100	2.00	60	38	0.19	140	1.6	27.5	0.36	2	0.05	
SKM200GAL176D	260	150	2.00	93	58	0.12	210	1.70	31	0.25	3	0.038	
SKM400GAL176D	432	300	2.00	170	118	0.075	440	1.70	78	0.125	3	0.038	
SKM400GAR176D	432	300	2.00	170	118	0.075	440	1.70	78	0.125	3	0.038	
SKM600GA176D	660	400	2.00	255	155	0.044	600	1.6	102	0.09	4	0.038	
SKM800GA176D	830	600	2.00	335	245	0.04	630	1.6	155	0.07	4	0.038	
SKM75GB176D	80	50	2.00	25	18	0.38	80	1.70	14.5	0.55	2	0.05	
SKM100GB176D	125	75	2.00	44	28.5	0.24	100	1.6	21.4	0.45	2	0.05	
SKM145GB176D	160	100	2.00	60	38	0.19	140	1.6	27.5	0.36	2	0.05	
SKM200GB176D	260	150	2.00	93	58	0.12	210	1.70	31	0.25	3	0.038	
SKM400GB176D	432	300	2.00	170	118	0.075	440	1.70	78	0.125	3	0.038	
1700V - NPT IGBT (Standard)													
SKM200GAL173D	220	150	3.4	95	45	0.1	150	2.2	21	0.32	3	0.038	
SKM200GAR173D	220	150	3.4	95	45	0.1	150	2.2	21	0.32	3	0.038	
SKM400GA173D	440	300	3	180	10	0.05	300	2.2	46	0.17	4	0.038	

Footnotes: 1) New product

IGBT Modules / SEMITRANS

1

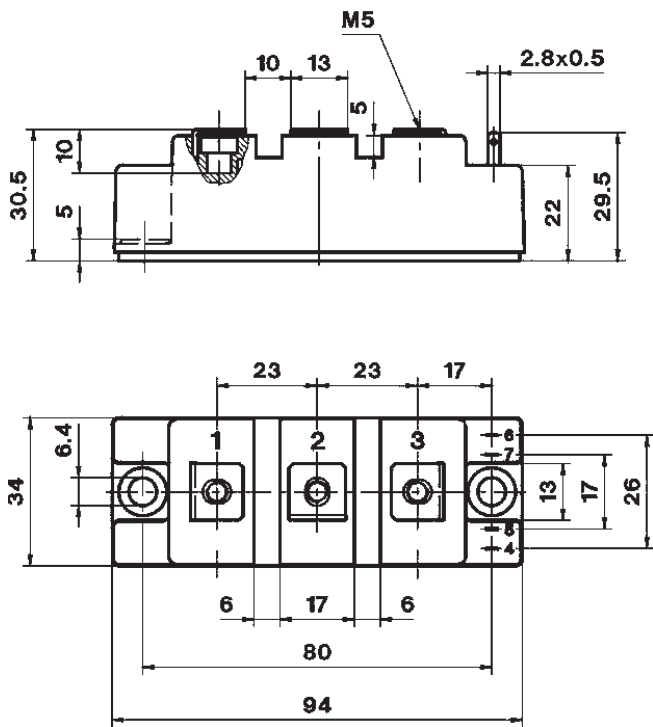
Type	IGBT						Diode				Module		Circuit
	$I_c @ T_c = 25^\circ\text{C}$	I_{cnom}	$V_{CE(sat)} @ T_j = 25^\circ\text{C typ.}$	E_{on}	E_{off}	$R_{th(j-c)}$	$I_f @ T_c = 25^\circ\text{C}$	$V_f @ T_j = 25^\circ\text{C typ.}$	E_{rr}	$R_{th(j-c)}$	Case	$R_{th(c-s)}$	
	A	A	V	mJ	mJ	K/W	A	V	mJ	K/W		K/W	
1700V - NPT IGBT (Standard)													
SKM75GB173D	75	50	3.4	18	13	0.25	60	2.2	10.5	0.75	2	0.05	
SKM100GB173D	110	75	3.4	35	21	0.2	80	2.2	11.5	0.63	2	0.05	
SKM150GB173D	150	100	3.4	60	32	0.125	125	2.2	14	0.4	3	0.038	
SKM200GB173D	220	150	3.4	95	45	0.1	150	2.2	21	0.32	3	0.038	
1700V - IGBT4 (Trench) (new product series, target data)													
SKM100GAL17E4 ¹⁾	164	100	1.90	43	39	0.234	113	2.00	26	0.504	2	0.05	
SKM200GAL17E4 ¹⁾	321	200	1.90	69	79	0.122	213	2.00	45	0.276	3	0.038	
SKM400GAL17E4 ¹⁾	614	400	1.90	156.5	180	0.066	443	2.00	130	0.13	3	0.038	
SKM100GAR17E4 ¹⁾	164	100	1.90	43	39	0.234	113	2.00	26	0.504	2	0.05	
SKM200GAR17E4 ¹⁾	321	200	1.90	69	79	0.122	213	2.00	45	0.276	3	0.038	
SKM400GAR17E4 ¹⁾	614	400	1.90	156.5	180	0.066	443	2.00	130	0.13	3	0.038	
SKM600GA17E4 ¹⁾	1021	600	1.90	234	270	0.042	629	1.98	140	0.095	4	0.038	
SKM75GB17E4 ¹⁾	125	75	1.90	22	34	0.304	88	2.00	24	0.632	2	0.05	
SKM100GB17E4 ¹⁾	164	100	1.90	43	39	0.234	113	2.00	26	0.504	2	0.05	
SKM150GB17E4 ¹⁾	261	150	1.90	67	59	0.162	169	1.98	32	0.345	2	0.05	
SKM200GB17E4 ¹⁾	321	200	1.90	69	79	0.122	213	2.00	45	0.276	3	0.038	
SKM300GB17E4 ¹⁾	476	300	1.90	88	121	0.083	314	2.00	77	0.19	3	0.038	
SKM400GB17E4 ¹⁾	614	400	1.90	156.5	180	0.066	443	2.00	130	0.13	3	0.038	
SKM400GM17E4 ¹⁾	614	400	1.90	156.5	180	0.066	443	2.00	130	0.13	3	0.038	
1700V - SPT ++ (new product series, target data)													
SKM1000GAL17S2	1460	1000	2.30	395	326	0.027	1344	1.78	185	0.043	10	0.003	
SKM1400GAL17S2	2000	1400	2.32	-	-	0.022	1874	1.84	-	0.032	10	0.003	
SKM1000GAR17S2	1460	1000	2.30	395	326	0.027	1344	1.78	185	0.043	10	0.003	
SKM1400GAR17S2	2000	1400	2.32	-	-	0.022	1874	1.84	-	0.032	10	0.003	
SKM1000GB17S2	1460	1000	2.30	395	326	0.027	1344	1.78	185	0.043	10	0.003	
SKM1400GB17S2	2000	1400	2.32	-	-	0.022	1874	1.84	-	0.032	10	0.003	

Footnotes: 1) New product

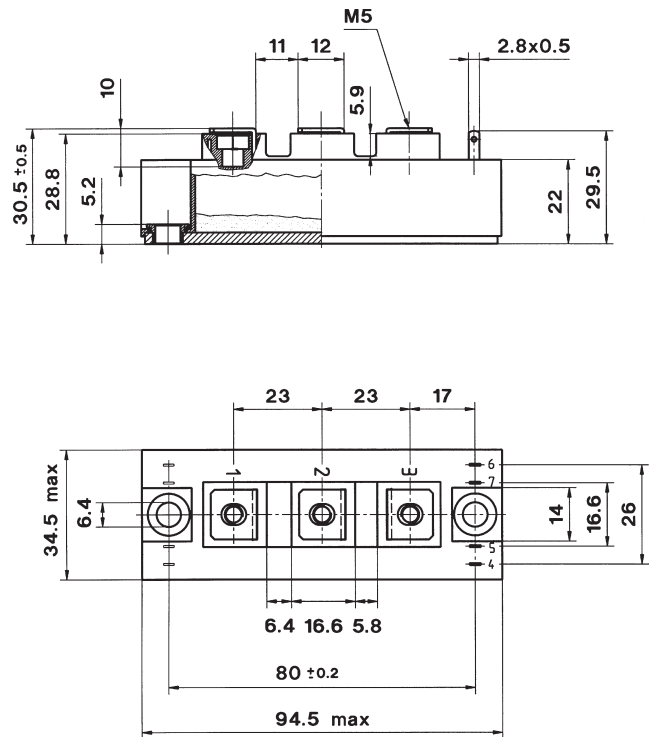
IGBT Modules / SEMITRANS

Cases

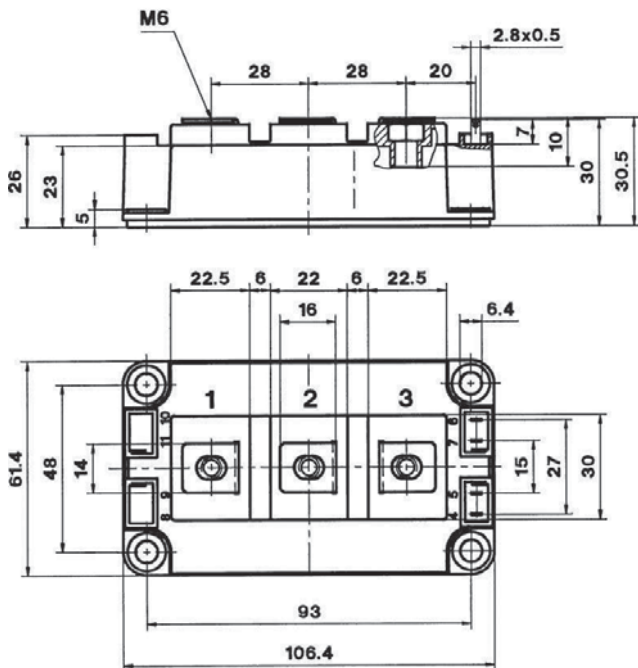
SEMISTRANS 2



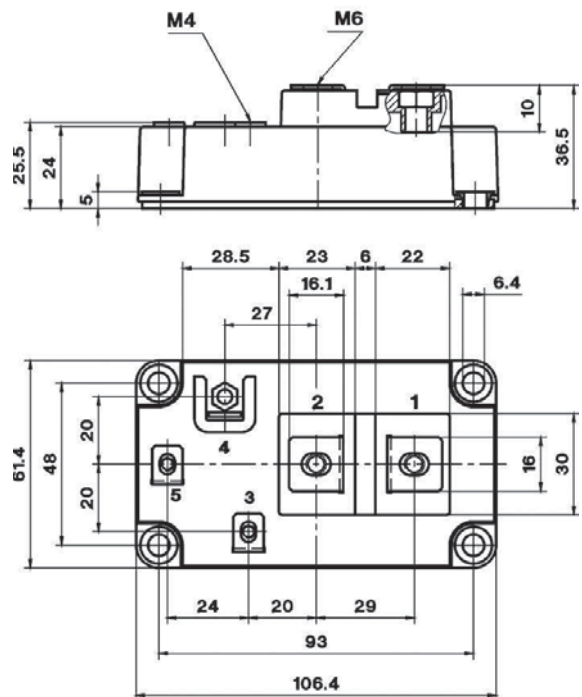
SEMISTRANS 2N



SEMISTRANS 3



SEMISTRANS 4



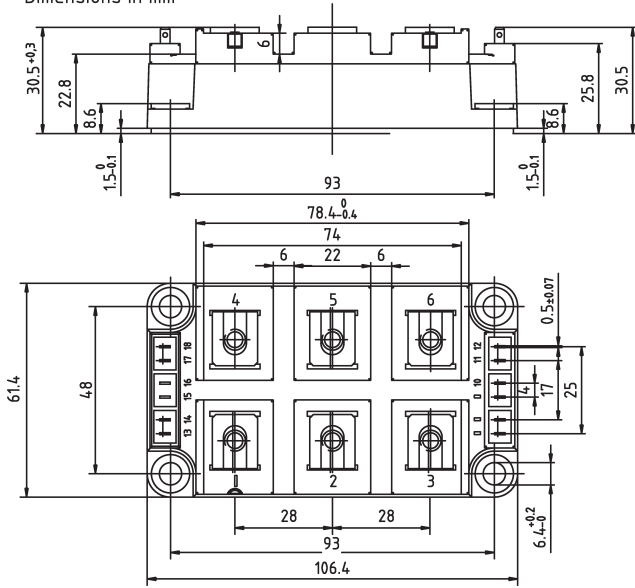
Dimensions in mm

IGBT Modules / SEMITRANS

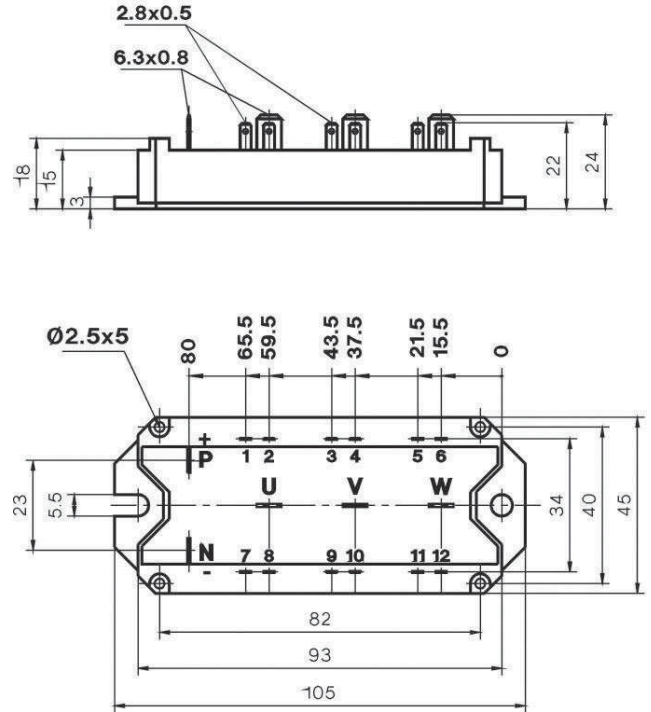
Cases

SEMISTRANS 5

Dimensions in mm



SEMISTRANS 6



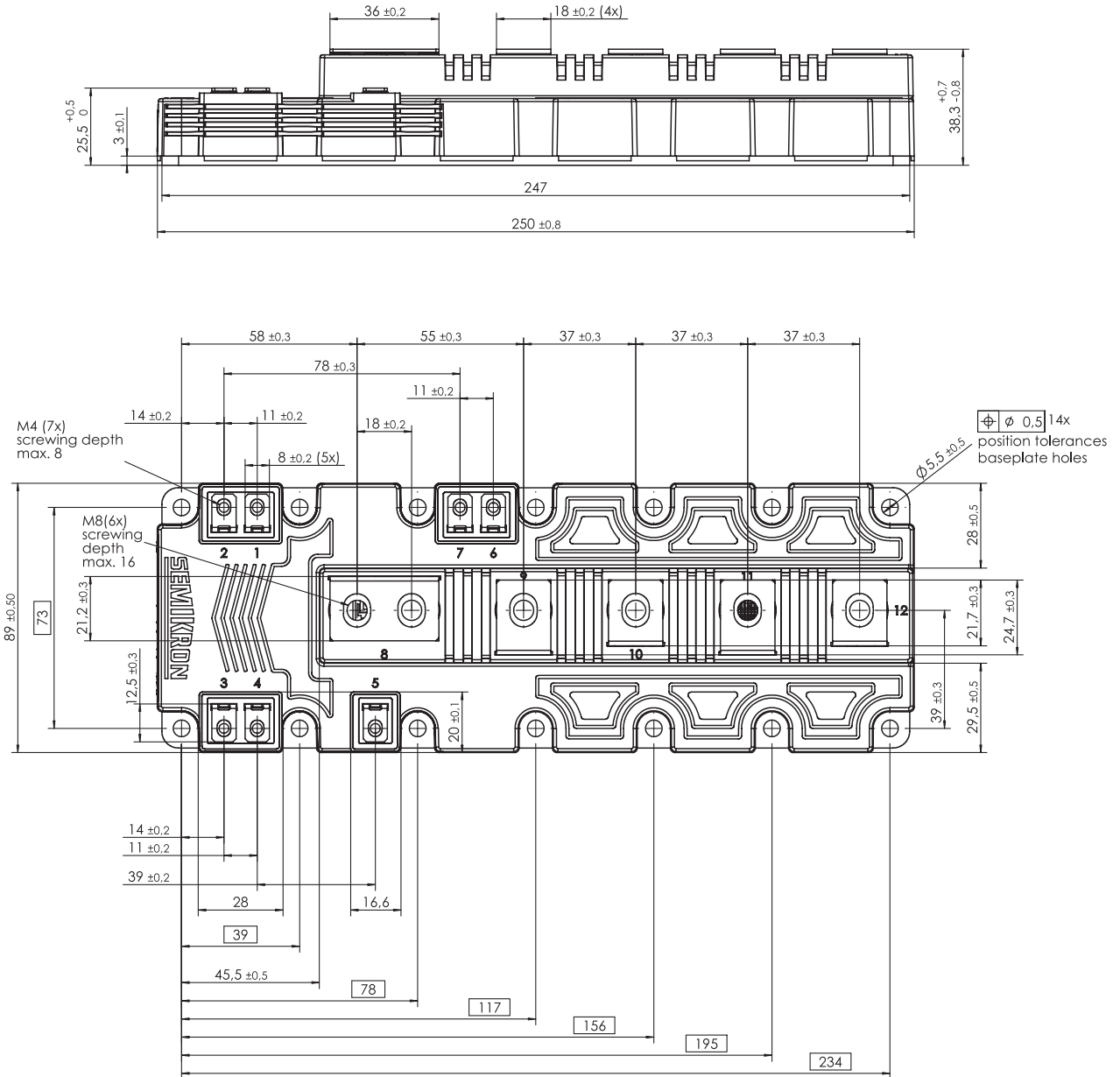
Dimensions in mm

IGBT Modules / SEMITRANS

Cases

SEMISTRANS 10

1



Dimensions in mm

IGBT Modules / SKiM 4/5

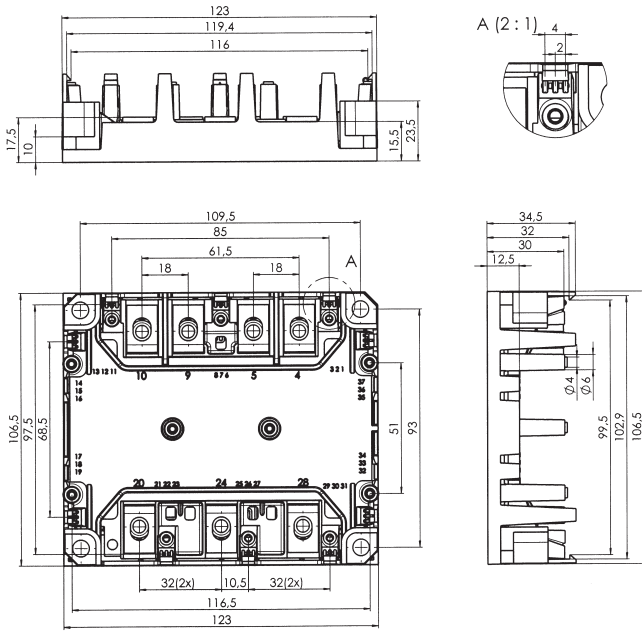
Type	IGBT						Diode				Module	Circuit
	$I_c @ T_s = 25^\circ\text{C}$ A	I_{cnom} A	$V_{CE(ant)} @ T_j = 25^\circ\text{C typ.}$ V	E_{on} mJ	E_{off} mJ	$R_{th(j-s)}$ K/W	$I_f @ T_s = 25^\circ\text{C}$ A	$V_f @ T_j = 25^\circ\text{C typ.}$ V	E_{rr} mJ	$R_{th(j-s)}$ K/W		
600V - IGBT3 (Trench)												
SKiM301MLI07E4	248	300	1.55	2.78	17.48	0.3	177	1.40	-	0.53	4	
SKiM401MLI07E4	319	400	1.55	3.32	20.91	0.25	289	1.40	1.8	0.31	4	
SKiM601MLI07E4	440	600	1.55	6.05	44	0.19	318	1.39	2.4	0.31	4	
1200V - IGBT3 (Trench)												
SKiM200GD126D	-	200	1.65	15	25	-	152	2.4	-	0.35	4	
SKiM300GD126D	265	300	1.70	28	47	0.2	260	1.9	-	0.285	4	
SKiM300GD126DL	265	300	1.65	28	47	0.2	260	1.9	-	0.285	4	
SKiM400GD126DM	330	300	1.70	29	46	0.134	300	1.9	-	0.19	4	
SKiM400GD126DLM	330	300	1.65	29	46	0.134	300	1.9	-	0.19	4	
SKiM450GD126D	390	450	1.70	42	70	0.13	345	1.9	-	0.19	5	
SKiM450GD126DL	390	450	1.65	42	70	0.13	345	1.9	-	0.19	5	
SKiM600GD126DLM	480	450	1.65	42	70	0.09	450	1.9	-	0.125	5	
SKiM601GD126DM	480	450	1.70	42	70	0.09	450	1.9	-	0.125	5	
1200V - IGBT4 (Trench)												
SKiM304GD12T4D	312	300	1.80	-	-	0.19	221	2.3	-	0.25	4	
SKiM455GD12T4D1	400	450	1.80	34	40	0.14	295	2.3	28	0.19	5	
SKiM201MLI12E4	206	200	1.80	14.81	22.6	0.29	187	2.20	14.78	0.36	4	
SKiM301MLI12E4	311	300	1.80	22.2	33.9	0.19	282	2.20	21.8	0.24	4	
SKiM301TMLI12E4B	311	300	1.80	6.62	19.37	0.19	249	2.20	1.79	0.29	4	
SKiM301TMLI12E4C	294	300	1.80	6.619	19.376	0.21	274	2.20	1.79	0.25	4	
SKiM401TMLI12E4B	411	400	1.80	8.83	25.83	0.145	365	2.20	2.391	0.188	4	
SKiM601TMLI12E4B	529	600	1.80	11.44	44.88	0.125	495	2.14	4.37	0.15	4	
1700V - IGBT3 (Trench)												
SKiM120GD176D	110	125	2	72	46	0.4	105	1.6	22	0.56	4	
SKiM220GD176DH4	220	250	2	145	100	0.21	220	1.7	65	0.26	4	

IGBT Modules / SKiM 4/5

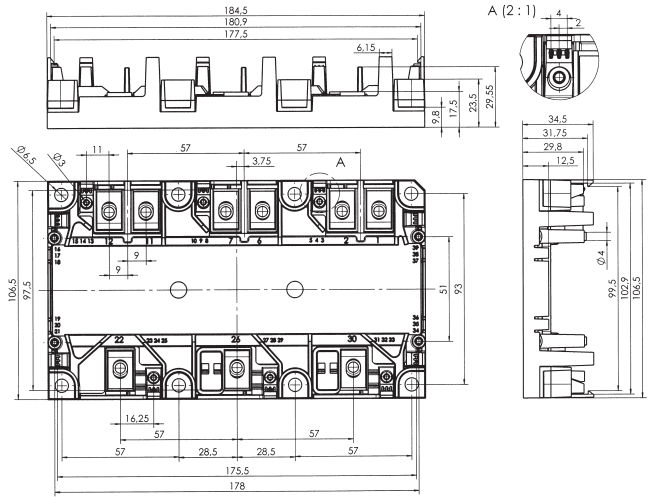
Type	IGBT					Diode					Module	
	$I_C @ T_S = 25^\circ\text{C}$	I_{Cnom}	$V_{CE(ant)} @ T_j = 25^\circ\text{C typ.}$	E_{on}	E_{off}	$R_{th(j-s)}$	$I_F @ T_S = 25^\circ\text{C}$	$V_F @ T_j = 25^\circ\text{C typ.}$	E_{rr}	$R_{th(j-s)}$	Case	Circuit
	A	A	V	mJ	mJ	K/W	A	V	mJ	K/W		
1700V - IGBT3 (Trench)												
SKiM270GD176D	260	300	2.00	170	120	0.175	215	1.7	-	0.29	5	

Cases

SKiM 4



SKiM 5



Dimensions in mm

IGBT Modules / SKiM 63/93

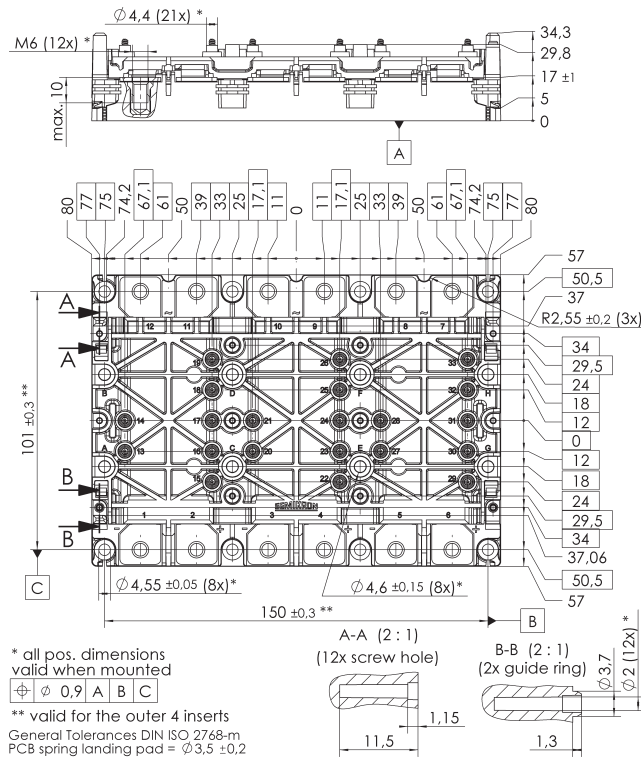
1

Type	IGBT						Diode				Module	Circuit
	$I_c @ T_s = 25^\circ\text{C}$ A	I_{cnom} A	$V_{CE(ant)} @ T_j = 25^\circ\text{C typ.}$ V	E_{on} mJ	E_{off} mJ	$R_{th(j-c)}$ K/W	$I_F @ T_s = 25^\circ\text{C}$ A	$V_F @ T_j = 25^\circ\text{C typ.}$ V	E_{rr} mJ	$R_{th(j-s)}$ K/W		
600V - IGBT3 (Trench)												
SKiM406GD066HD	468	400	1.45	8	25	0.135	360	1.5	12	0.243	63	
SKiM606GD066HD	641	600	1.45	16	53	0.105	453	1.6	21	0.201	63	
SKiM909GD066HD	899	900	1.45	36	88	0.078	712	1.5	29	0.135	93	
1200V - IGBT4 (Trench)												
SKiM609GAL12E4	748	600	1.85	136	83	0.068	1397	1.7	39	0.048	93	
SKiM609GAR12E4	748	600	1.85	136	83	0.068	1397	1.7	39	0.048	93	
SKiM306GD12E4	410	300	1.85	19	39	0.116	302	2.1	21	0.218	63	
SKiM459GD12E4	554	450	1.85	22	57	0.092	438	2.1	40	0.155	93	
1700V - IGBT4 (Trench)												
SKiM429GD17E4HD	595	420	1.90	245	180	0.079	413	1.7	99	0.169	93	

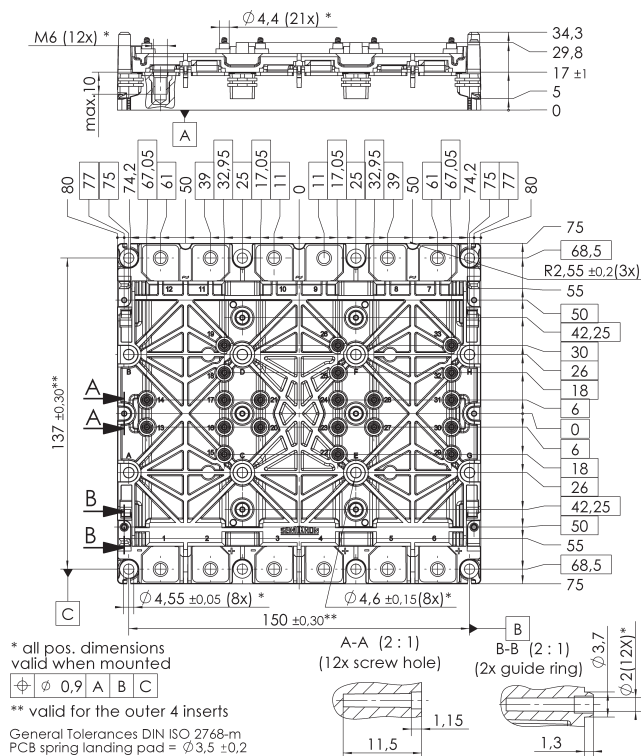
IGBT Modules / SKiM 63/93

Cases

SKiM 63



SKiM 93



Silicon Carbide Modules for Highest Energy Efficiency

SEMIKRON offers hybrid and full silicon carbide power modules in MiniSKiiP, SEMITOP, SEMITRANS 3 and SKiM63/93. Latest IGBT technology is combined with SiC Schottky diodes to increase the switching frequency and reduce power losses at the same time. Silicon carbide MOSFETs, either with or without anti-parallel SiC Schottky diodes, create even higher gains in switching frequency and power density.

The SEMIKRON silicon carbide power modules are available from 8A to 500A in 1200V. Covered topologies are 6-packs, also with split output configurations, half bridges and triple boost converters. Additionally further topologies like 3-level or H-bridge designs are easily adaptable to silicon carbide and will complete the portfolio.

Product	Page
Full SiC	
MiniSKiiP	76
SEMITOP 3	77
SEMITRANS 3	78
Hybrid SiC	
SKiM 93	79
SEMITRANS 3	80

▶ For detailed information please refer data sheets.

Further information:
<http://www.semikron.com/full-sic>
<http://www.semikron.com/hybrid-sic>

Silicon Carbide Modules

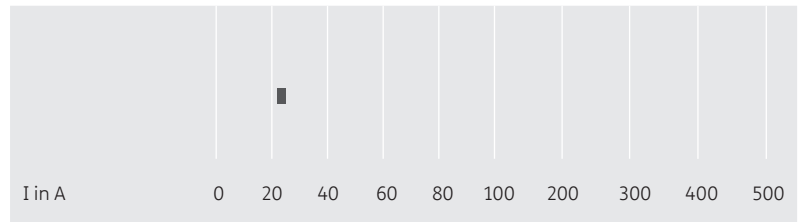
Full SiC

MiniSKiiP®

6-pack
H-bridge



1200V

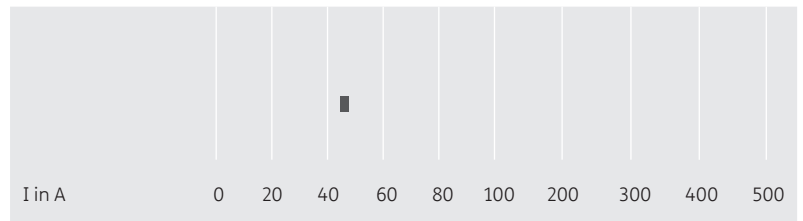


SEMITOP®

half bridge
6-pack
chopper
H-bridge



1200V

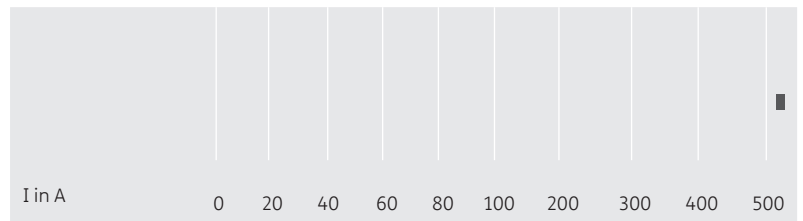


SEMITRANS®

half bridge



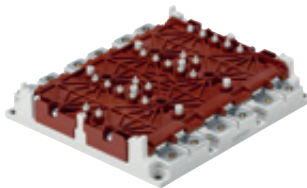
1200V



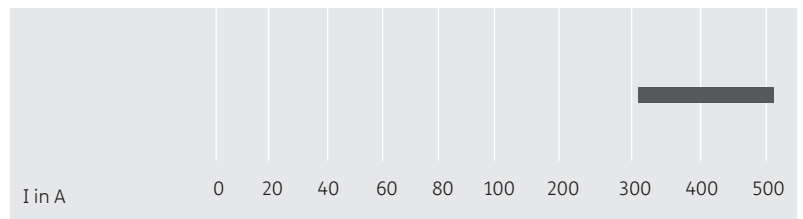
Hybrid SiC

SKiM® 63/93

6-pack



1200V

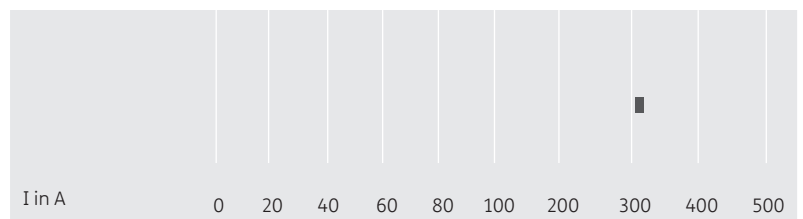


SEMITRANS®

half bridge

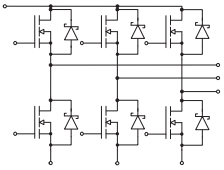


1200V



SiC Modules / Full SiC / MiniSKiiP

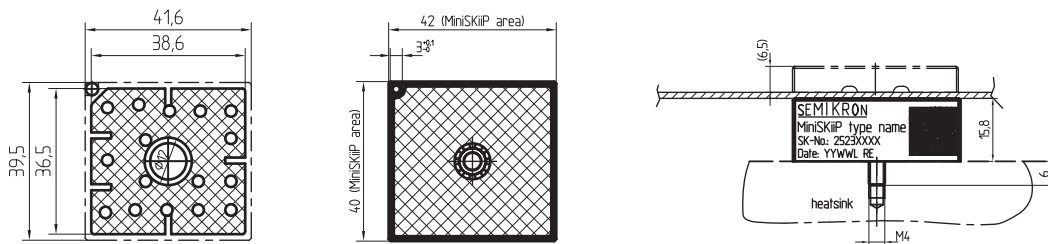
Type

Type	V_{DS} V	$I_D @ T_C = 25^\circ\text{C}$ A	$R_{DS(on)} @ T_J = 25^\circ\text{C typ.}$ m Ω	$R_{th(j-c)}$ K/W	Case	Circuit
1200V - IGBT4 (Trench)						
SKiiP 13ACM12V15 ⁸⁾	1200	22	80	1.25	II 1	

Footnotes: 8) Target data

Cases

MiniSKiiP II 1



pin configuration depends on circuit
(details in data sheet)

Dimensions in mm

SiC Modules / Full SiC / SEMITOP

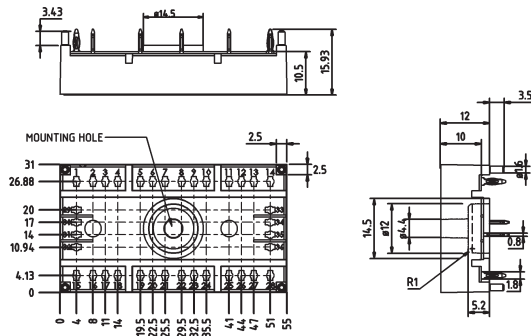
Type

	V_{DS} V	I_P @ $T_C = 25^\circ\text{C}$ A	$R_{DS(on)}$ @ $T_J = 25^\circ\text{C}$ typ. m Ω	$R_{th(j-c)}$ K/W	Case	Circuit
1200V - IGBT4 (Trench)						
SK45MAHT12SCp ⁸⁾	1200	45	45	0.87	3p	
SK45MLET12SCp ⁸⁾	1200	45	45	0.87	3p	

Footnotes: 8) Target data

Cases

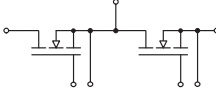
SEMITOP 3 Press-Fit



Dimensions in mm

SiC Modules / Full SiC / SEMITRANS

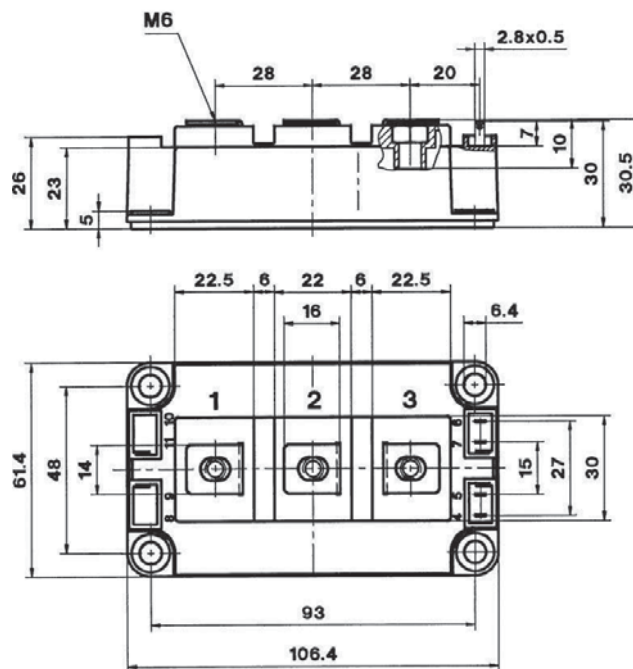
Type

Type	V_{DS} V	$I_P @ T_C = 25^\circ\text{C}$ A	$R_{DS(on)} @ T_J = 25^\circ\text{C typ.}$ m Ω	$R_{th(j-c)}$ K/W	Case	Circuit
SKM500MB120SC ⁸⁾	1200	541	3.75	0.07	3	

Footnotes: 8) Target data

Cases

SEMISTRANS 3



Dimensions in mm

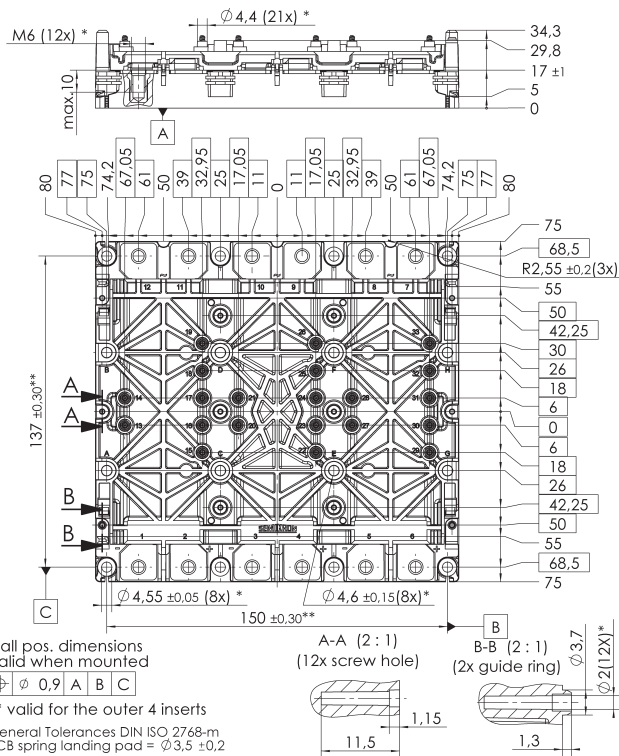
SiC Modules / Hybrid SiC / SKiM 63/93

Type	IGBT					Diode					Module	
	$I_c @ T_s = 25^\circ\text{C}$	Current (A)	$V_{CE(ant)} @ T_j = 25^\circ\text{C typ.}$	E_{on}	E_{off}	$R_{th(j-s)}$	$I_F @ T_s = 25^\circ\text{C}$	V_F	E_{rr}	$R_{th(j-s)}$	Case	Circuit
	A	A	V	mJ	mJ	K/W	A	V	mJ	K/W		
1200V - IGBT4 (Trench)												
SKiM309GD125SiC ⁽⁸⁾	307	300	3.20	12.8	16.8	0.086	196	1.6	0.68	0.151	93	
SKiM459GD12F4SiC ⁽⁸⁾	507	450	2.05	9	35	0.092	283	1.6	-	0.18	93	

Footnotes: 8) Target data

Cases

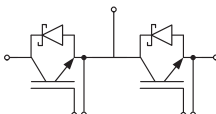
SKiM 93



Dimensions in mm

SiC Modules / Hybrid SiC / SEMITRANS

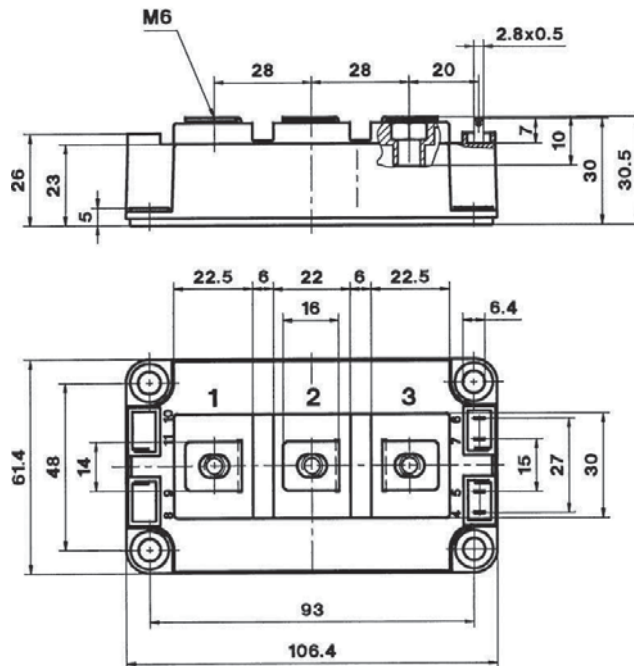
2

Type	IGBT						Diode				Module		
	$I_c @ T_c = 25^\circ\text{C}$	Current (A)	$V_{CE(sat)} @ T_j = 25^\circ\text{C typ.}$	E_{on}	E_{off}	$R_{th(j-c)}$	$I_F @ T_c = 25^\circ\text{C}$	V_F	E_{rr}	$R_{th(j-c)}$	Case	$R_{th(c-s)}$	Circuit
	A	A	V	mJ	mJ	K/W	A	V	mJ	K/W		K/W	
1200V - IGBT4 (Trench)													
SKM200GB12T4SiC ⁸⁾	313	200	1.80	7	20	0.14	174	2.00	0.1	0.2	3	0.038	

Footnotes: 8) Target data

Cases

SEMITRANS 3



Dimensions in mm

MOSFET Modules

Best in Class Switching Performance

SEMIKRON produces MOSFET (Metal Oxide Semiconductor Field Effect Transistor) modules in single switch, halfbridge, H-bridge and 6-pack configuration in SEMITOP and SEMITRANS packages.

The available MOSFET modules in the voltage range of 55V up to 600V and current ratings of 40A up to 290A are especially designed for high-speed switching offering low switching losses.

Product	Page
SEMITOP	84
SEMITRANS	86

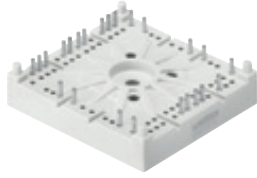
▶ For detailed information
please refer data sheets.

Further information:
www.semikron.com/mosfet-modules

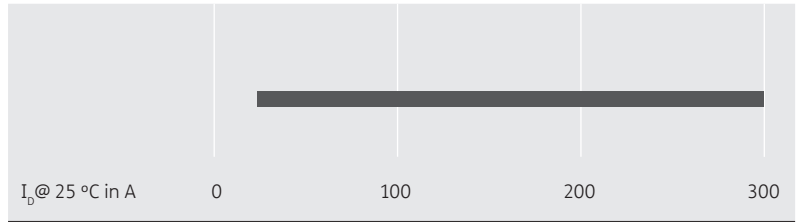
MOSFET Modules

SEMITOP®

6-pack
H-bridge
half bridge



55V up to 600V

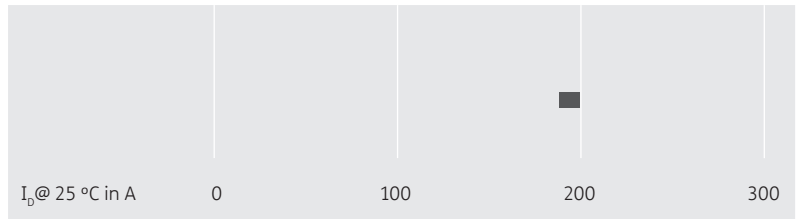


SEMITRANS®

single switch

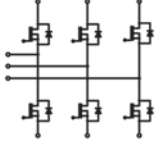
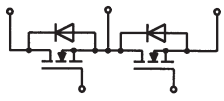
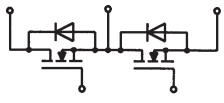
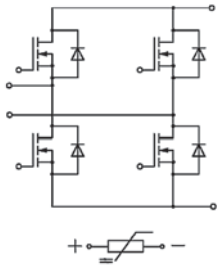
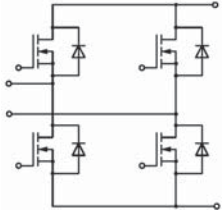


100V up to 200V



MOSFET Modules / SEMITOP

Type

Type	V_{DS} V	$I_D @ T_C = 25^\circ\text{C}$ A	$R_{DS(on)}$ @ $T_J = 25^\circ\text{C}$ typ. m Ω	$R_{th(j-c)}$ K/W	Case	Circuit
55V						
SK 80 MBBB 055	55	117	2.2	1.1	3	
75V						
SK 300 MB 075	75	290	-	0.45	3	
100V						
SK 260 MB 10	100	230	-	0.45	3	
SK 85 MH 10 T	100	80	-	1.1	2	
600V						
SK 60 MH 60 ¹⁾	600	60	33	0.54	4	

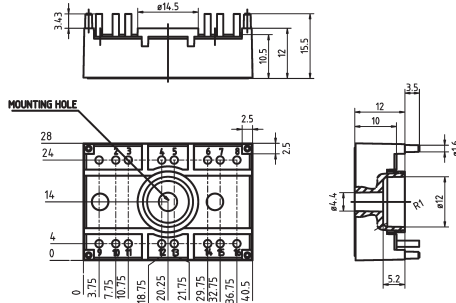
Footnotes: 1) New product

MOSFET Modules / SEMITOP

Cases

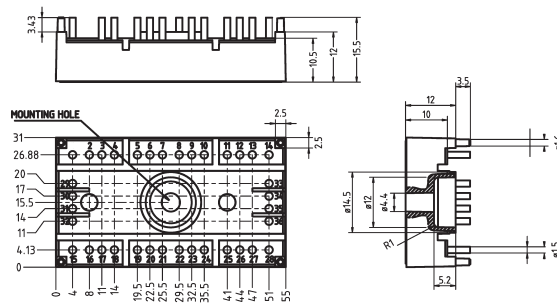
SEMISTOP 2

dimensions in mm
tolerance system: ISO 2768-m



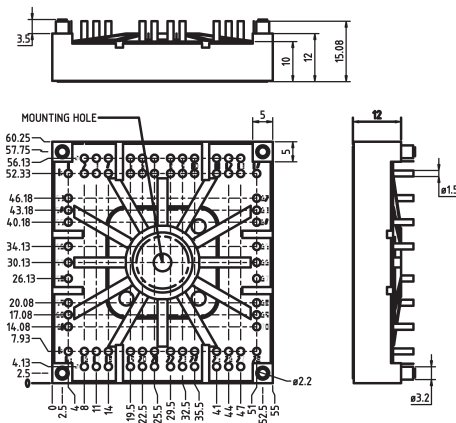
SEMISTOP 3

dimensions in mm
tolerance system: ISO 2768-m



SEMISTOP 4

dimensions in mm
tolerance system: ISO 2768-m



Dimensions in mm

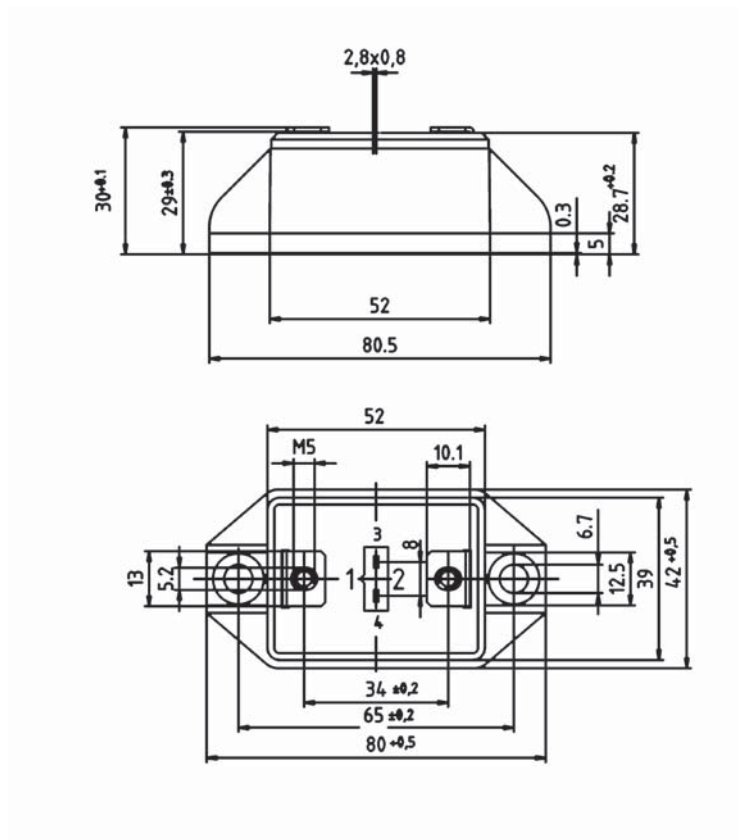
MOSFET Modules / SEMITRANS

Type

	V_{DS} V	$I_D @ T_c = 25^\circ\text{C}$ A	$R_{DS(on)} @ T_j = 25^\circ\text{C typ.}$ m Ω	$R_{th(j-c)}$ K/W	Case	Circuit
100V						
SKM 111 AR	100	200	7	0.18	M1	
SKM 111 RZR	100	200	7	0.18	M1	
200V						
SKM 180 A020	200	180	9	0.18	M1	

Cases

SEMISTRANS M1



Dimensions in mm

Thyristor / Diode Modules with Proven Packages

The SEMIKRON thyristor modules are available in different packages like SEMIPACK, SEMiSTART, Thyristor / Diode Modules, SEMIPONT and SEMITOP. Modules in different packaging technologies are available: soldered, wire bonded and pressure contact modules with and without baseplate.

PCB contacting is possible by soldered pins, pressfit contacts or plug connectors. The thyristor modules are offered in a variety of dual and single topologies for almost all phase control or rectifier applications.

All thyristor modules are equipped with SEMIKRON chips. The product line offers Thyristor / Diode Modules. A product range with voltages up to 2200V. Thanks to the comprehensive product range, the optimal solution for each application can be found.

Product	Page
SEMITOP 1 / 2 / 3	90
SEMIX 1 / 2	92
SEMIPONT 5	93
SEMIPACK 0 / 1 / 2 / 3 / 4 / 5 / 6	94
SEMiSTART	99

▶ For detailed information
please refer data sheets.

Further information:
www.semikron.com/thyristor-diode-modules

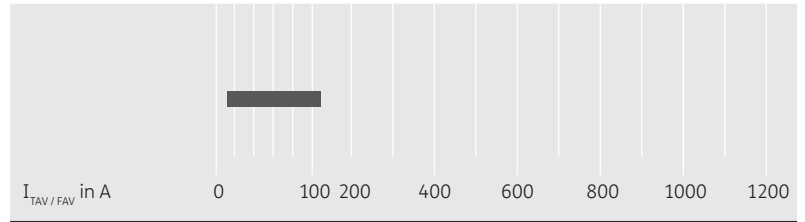
Thyristor / Diode Modules

SEMISTOP® 1/2/3

W1C, WT, W3C
single switch



800V up to 1600V

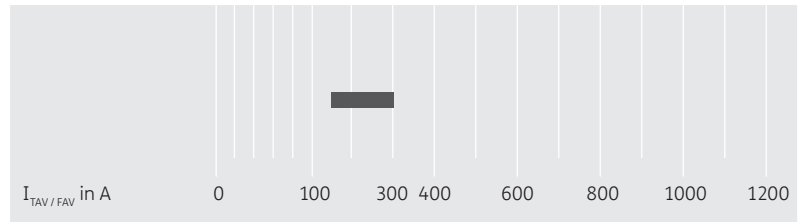


SEMiX® 1/2

half bridge



1600V

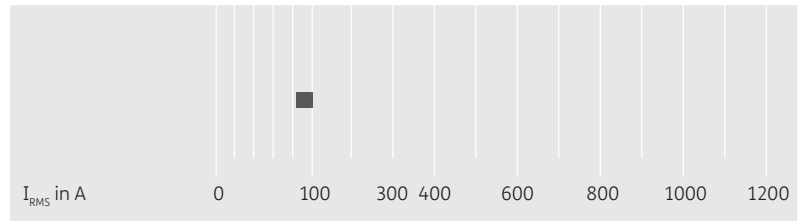


SEMIPONT® 5

W3C



1200V up to 1600V

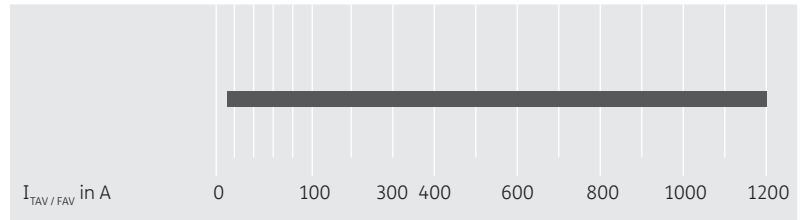


SEMIPACK® 0/1/2/3/4/5/6

single switch
half bridge

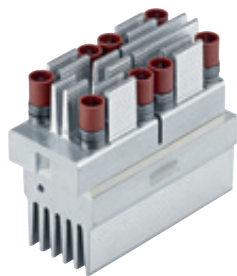


200V up to 2200V

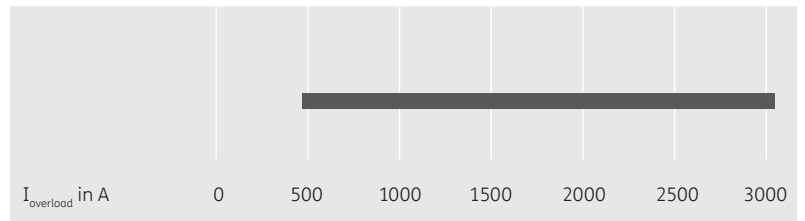


SEMiSTART®

W1C



1400V up to 1800V



Thyristor / Diode Modules / SEMITOP

Type

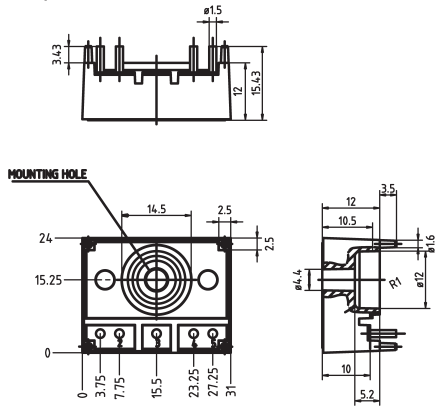
Type	$V_{FRM} V_{DRM}$ V	$I_{TAV} I_{FAV} @ T_s$ A	T_s °C	$I_{TSM} I_{FSM} @ T_{jmax}$ A	$V_{T(RO)} @ T_{jmax}$ V	$r_T @ T_{jmax}$ mΩ	$R_{th(j-c)}$ per chip K/W	T_j °C	Case	Circuit
SK 25 KQ	800-1600	29	85	280	1.1	20.00	1.7	-40 ... +125	1	
SK 45 KQ	800-1600	47	85	380	1	10.00	1.2	-40 ... +125	1	
SK 70 KQ	800-1600	72	85	900	1	6.00	0.8	-40 ... +125	1	
SK 100 KQ	800-1600	101	85	1350	0.9	4.50	0.6	-40 ... +125	2	
SK 120 KQ	800-1600	134	85	1800	0.9	3.50	0.45	-40 ... +125	2	
SK 35 TAA	800-1600	35	80	380	0.85	9.10	1.2	-40 ... +130	2	
SK 55 TAA	800-1600	55	80	900	0.85	5.70	0.8	-40 ... +130	2	
SK 75 TAA	800-1600	75	80	1500	0.9	4.50	0.6	-40 ... +130	2	
SK 100 TAA	800-1600	100	80	2000	0.9	3.50	0.45	-40 ... +130	2	
SK 75 TAE 12	1200	75	80	1250	0.85	4.40	0.6	-40 ... +130	2	
SK 25 WT	800-1600	29	85	280	1.1	20.00	1.7	-40 ... +125	2	
SK 45 WT	800-1600	47	85	380	1	10.00	1.2	-40 ... +125	2	
SK 70 WT	800-1600	72	85	900	1	6.00	0.8	-40 ... +125	3	
SK 100 WT	800-1600	101	85	1350	0.9	4.50	0.6	-40 ... +125	3	
SK 35 BZ	800-1600	35	80	270	0.85	14.00	1.7	-40 ... +125	2	
SK 45 STA	800-1600	47	75	380	1	10.00	1.2	-40 ... +125	3	
SK 25 UT	800-1600	29	85	280	1.1	20.00	1.7	-40 ... +125	3	
SK 45 UT	800-1600	47	85	380	1	10.00	1.2	-40 ... +125	3	
SK 30 DTA	800-1600	25	80	900	1	6.00	1.7	-40 ... +150	3	
SK 60 DTA	800-1600	61	80	1350	0.9	0.60	0.6	-40 ... +125	3	
SK 80 DTA	800-1600	65	80	1800	0.9	3.50	1	-40 ... +150	3	

Thyristor / Diode Modules / SEMITOP

Cases

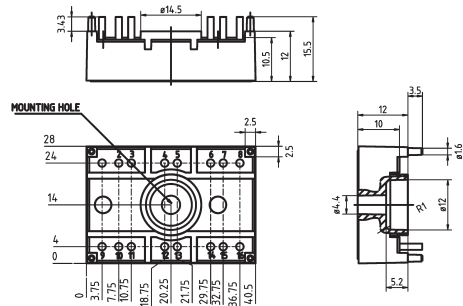
SEMISTOP 1

dimensions in mm
tolerance system: ISO 2768-m



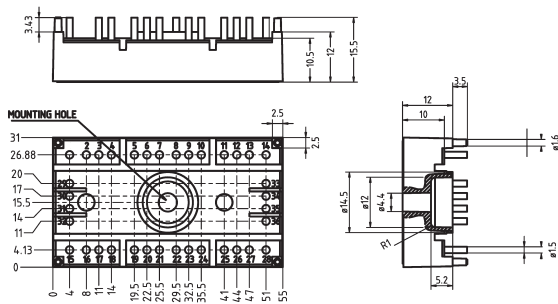
SEMISTOP 2

dimensions in mm
tolerance system: ISO 2768-m



SEMISTOP 3

dimensions in mm
tolerance system: ISO 2768-m



Dimensions in mm

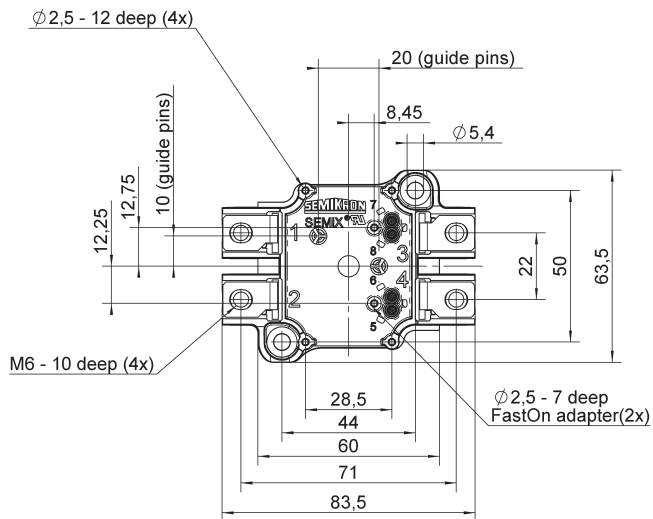
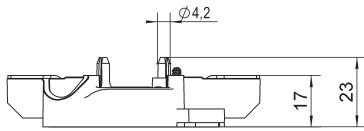
Thyristor / Diode Modules / SEMiX

Type

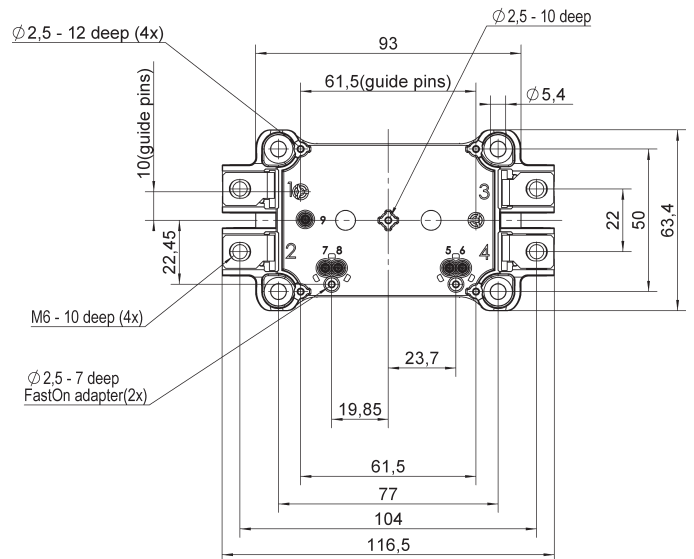
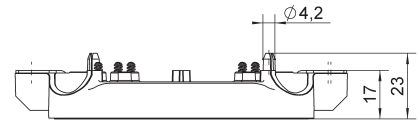
Type	$V_{RRM} V_{DRM}$ V	$I_{TAV} I_{FAV} @ T_C$ A	T_C °C	$I_{TSM} I_{FSM} @ T_{jmax}$ A	$V_{r(TO)} @ T_{jmax}$ V	$r_T @ T_{jmax}$ mΩ	$R_{th(j-c)}$ per chip K/W	$R_{th(c-s)}$ K/W	T_j °C	Case	Circuit
SEMiX191KD16s	1600	190	85	5000	0.85	0.95	0.18	0.075	-40 ... +130	1s	
SEMiX302KD16s	1600	300	85	7500	0.85	1.1	0.091	0.045	-40 ... +130	2s	
SEMiX171KH16s	1600	170	85	4800	0.85	1.5	0.18	0.075	-40 ... +130	1s	
SEMiX302KH16s	1600	300	85	8000	0.85	1.1	0.091	0.045	-40 ... +130	2s	
SEMiX141KT16s	1600	140	85	3000	0.85	2.1	0.21	0.075	-40 ... +130	1s	
SEMiX302KT16s	1600	300	85	8000	0.85	1.7	0.091	0.045	-40 ... +130	2s	

Cases

SEMiX 1s



SEMiX 2s



Dimensions in mm

Thyristor / Diode Modules / SEMIPONT

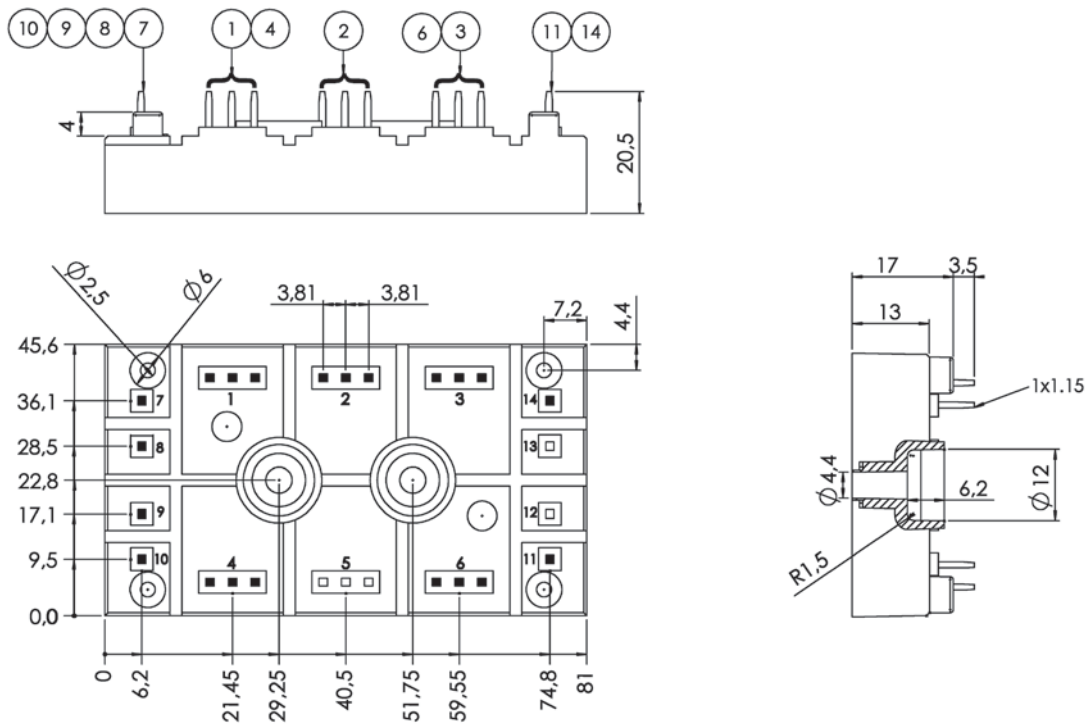
Type

	V_{RRM} V	$I_{TAV} I_{FAV}$ @ T_S A	T_S °C	$I_{FSM} I_{FSM}$ @ T_{jmax} A	$V_{T(TO)}$ @ T_{jmax} V	r_T @ T_{jmax} mΩ	$R_{th(j-s)}$ cont. per chip K/W	T_j °C	Case	Circuit
SKUT 85/16 T V2 ¹⁾	1600	94	85	1050	1.1	6.00	-	-40 ... +125	5	
SKUT 85/12 T V2 ¹⁾	1200	94	85	1050	1.1	6.00	-	-40 ... +125	5	
SKUT 115/16T V2 ¹⁾	1600	127	85	1250	0.9	5	-	-40 ... +125	5	
SKUT 115/12T V2 ¹⁾	1200	127	85	1250	0.9	5	-	-40 ... +125	5	
SKUT 85/12 V2 ¹⁾	1200	85	85	1050	1.1	6.00	0.85	-40 ... +125	5	
SKUT 85/16 V2 ¹⁾	1600	85	85	1050	1.1	6.00	0.85	-40 ... +125	5	
SKUT 115/12 V2 ¹⁾	1200	105	85	1250	0.9	5.00	0.63	-40 ... +125	5	
SKUT 115/16 V2 ¹⁾	1600	105	85	1250	0.9	5.00	0.63	-40 ... +125	5	

Footnotes: 1) New product

Cases

SEMIPONT 5



Dimensions in mm

Thyristor / Diode Modules / SEMIPACK

Type

	V_{RRM} V_{DRM} V	I_{TAV} I_{TAV} @ T_c A	T_c °C	I_{FSM} I_{FSM} @ T_{jmax} A	$V_{T(TO)}$ @ T_{jmax} V	r_T @ T_{jmax} mΩ	$R_{th(j-c)}$ cont. per chip K/W	$R_{th(c-a)}$ per chip K/W	T_j °C	Case	Circuit
SKET 330	800-2200	295	85	8000	1.2	0.55	0.09	0.02	-40 ... +130	4	
SKET 400	800-1800	392	85	12000	0.92	0.30	0.09	0.02	-40 ... +130	4	
SKET 741/22 E	2200	740	85	26500	0.9	0.21	0.0405	0.01	-40 ... +125	6	
SKET 801/18 E	1800	800	85	30000	0.85	0.17	0.0405	0.01	-40 ... +125	6	
SKKE 15	600-1600	14	85	280	0.85	15	2	0.2	-40 ... +125	0	
SKKE 81	400-2200	82	85	1750	0.85	1.80	0.4	0.2	-40 ... +125	1	
SKKE 162	800-1800	195	85	5000	0.85	1.20	0.18	0.1	-40 ... +135	2	
SKKE 380	1200-1600	380	100	10000	0.8	0.35	0.11	0.04	-40 ... +150	3	
SKKE 600	1200-2200	600	100	18000	0.75	0.25	0.07	0.02	-40 ... +150	4	
SKKE 1201/22	2200	1360	85	35000	0.75	0.07	0.047	0.015	-40 ... +125	6	
SKKL 92	800-1800	95	85	1750	0.9	2.00	0.28	0.2	-40 ... +125	1	
SKMT 92	800-1800	95	85	1750	0.9	2.00	0.28	0.2	-40 ... +125	1	
SKKD 15	600-1600	14	85	280	0.85	15	2	0.2	-40 ... +125	0	
SKKD 26	1200-1600	31	85	480	0.85	6.00	1	0.2	-40 ... +125	1	
SKKD 46	400-1800	47	85	600	0.85	5.00	0.6	0.2	-40 ... +125	1	
SKKD 81	400-1800	82	85	1750	0.85	1.80	0.4	0.2	-40 ... +125	1	
SKKD 81 H4	2000-2200	82	85	1750	0.85	1.80	0.4	0.2	-40 ... +125	1	
SKKD 100	400-1800	100	85	2000	0.85	1.30	0.35	0.2	-40 ... +125	1	
SKKD 101/16	1600	134	85	2000	0.87	2.45	0.19	0.22	-40 ... +130	1	
SKKD 152/16	1600	171	85	4500	0.82	1.35	0.2	0.1	-40 ... +125	2	
SKKD 162	800-2200	195	85	5000	0.85	1.20	0.18	0.1	-40 ... +135	2	
SKKD 212	1200-1800	212	85	5500	0.75	1.05	0.18	0.1	-40 ... +135	2	
SKKD 260	800-2200	260	85	10000	0.9	0.37	0.14	0.04	-40 ... +130	3	
SKKD 353	1200-1800	350	85	9500	0.84	0.75	0.091	0.08	-40 ... +125	3	
SKKD 380	800-2200	380	100	10000	0.8	0.35	0.11	0.04	-40 ... +150	3	
SKKD 701	1200-2200	701	100	22500	0.7	0.28	0.069	0.02	-40 ... +160	5	
SKKH 15	600-1600	13.5	85	280	1.1	20.00	1.6	0.2	-40 ... +125	0	
SKKH 27	800-1800	25	85	480	0.9	12.00	0.9	0.2	-40 ... +125	1	
SKKH 42	800-1800	40	85	850	1	4.50	0.65	0.2	-40 ... +125	1	
SKKH 57	800-1800	50	85	1250	0.9	3.50	0.57	0.2	-40 ... +125	1	
SKKH 57 H4	2000-2200	50	85	1250	0.9	3.50	0.57	0.2	-40 ... +125	1	
SKKH 58/16 E	1600	55	85	1200	1	4.80	0.47	0.22	-40 ... +130	1	
SKKH 72	800-1800	70	85	1450	0.9	3.50	0.35	0.2	-40 ... +125	1	
SKKH 72 H4	2000-2200	70	85	1450	0.9	3.50	0.35	0.2	-40 ... +125	1	
SKKH 92	800-1800	95	85	1750	0.9	2.00	0.28	0.2	-40 ... +125	1	
SKKH 106	800-1800	106	85	1900	0.9	2.00	0.28	0.2	-40 ... +130	1	
SKKH 107/16 E	1600	119	85	1900	0.9	3.35	0.19	0.22	-40 ... +130	1	
SKKH 122	800-1800	129	85	3200	0.85	2.00	0.2	0.13	-40 ... +125	2	
SKKH 132	800-1800	137	85	4000	1	1.60	0.18	0.1	-40 ... +125	2	
SKKH 132 H4	2000-2200	128	85	3800	1.1	2.00	0.17	0.1	-40 ... +125	2	
SKKH 162	800-1800	156	85	5000	0.85	1.50	0.17	0.1	-40 ... +125	2	
SKKH 162 H4	2000-2200	143	85	4800	0.95	2.00	0.16	0.1	-40 ... +125	2	
SKKH 172	1600	175	85	5000	0.83	1.30	0.155	0.1	-40 ... +125	2	
SKKH 250	1200-1800	250	85	8000	0.925	0.45	0.14	0.04	-40 ... +130	3	
SKKH 273	1200-1800	273	85	8000	0.9	0.92	0.104	0.08	-40 ... +130	3	
SKKH 280 H4	2000-2200	252	85	7500	0.9	0.75	0.11	0.04	-40 ... +125	3	
SKKH 323	1200-1600	320	85	8200	0.81	0.85	0.091	0.08	-40 ... +130	3	
SKKH 330	800-1800	305	85	8000	0.8	0.60	0.11	0.04	-40 ... +130	3	
SKKH 460	1600-2200	460	85	15500	0.88	0.45	0.072	0.02	-40 ... +130	5	
SKKH 570	1600-1800	570	85	15500	0.78	0.32	0.069	0.02	-40 ... +135	5	

Thyristor / Diode Modules / SEMIPACK

Type

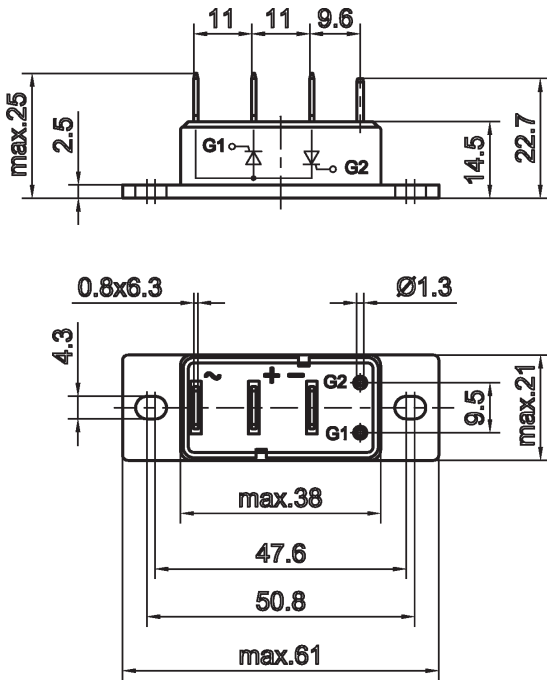
Type	V_{RRM} V	I_{TAV} A	I_{FAV} @ T_C A	T_C °C	I_{FSM} A	I_{FSM} @ T_{jmax} A	$V_{T(RO)}$ @ T_{jmax} V	r_T @ T_{jmax} mΩ	$R_{th(j-c)}$ cont. per chip K/W	$R_{th(c-s)}$ per chip K/W	T_j °C	Case	Circuit
SKKT 15	600-1600	13.5	85	280	1.1	20.00	1.6	0.2	-40 ... +125	0			
SKKT 20	800-1600	18	85	280	1	16.00	1.2	0.2	-40 ... +125	1			
SKKT 20B	800-1600	18	85	280	1	16.00	1.2	0.2	-40 ... +125	1			
SKKT 27	800-1600	25	85	480	0.9	12.00	0.9	0.2	-40 ... +125	1			
SKKT 27B	800-1600	25	85	480	0.9	12.00	0.9	0.2	-40 ... +125	1			
SKKT 42	800-1800	40	85	850	1	4.50	0.65	0.2	-40 ... +125	1			
SKKT 42B	800-1800	40	85	850	1	4.50	0.65	0.2	-40 ... +125	1			
SKKT 57	800-1800	50	85	1250	0.9	3.50	0.57	0.2	-40 ... +125	1			
SKKT 57B	800-1800	50	85	1250	0.9	3.50	0.57	0.2	-40 ... +125	1			
SKKT 57 H4	2000-2200	50	85	1250	0.9	3.50	0.57	0.2	-40 ... +125	1			
SKKT 58/16 E	1600	55	85	1200	1	4.80	0.47	0.22	-40 ... +130	1			
SKKT 58B16 E	1600	55	85	1200	1	4.80	0.47	0.22	-40 ... +130	1			
SKKT 72	800-1800	70	85	1450	0.9	3.50	0.35	0.2	-40 ... +125	1			
SKKT 72B	800-1800	70	85	1450	0.9	3.50	0.35	0.2	-40 ... +125	1			
SKKT 72 H4	2000-2200	70	85	1450	0.9	3.50	0.35	0.2	-40 ... +125	1			
SKKT 92	800-1800	95	85	1750	0.9	2.00	0.28	0.2	-40 ... +125	1			
SKKT 92B	800-1800	95	85	1750	0.9	2.00	0.28	0.2	-40 ... +125	1			
SKKT 106	800-1800	106	85	1900	0.9	2.00	0.28	0.2	-40 ... +130	1			
SKKT 106B	800-1800	106	85	1900	0.9	2.00	0.28	0.2	-40 ... +130	1			
SKKT 107/16 E	1600	119	85	1900	0.9	3.35	0.19	0.22	-40 ... +130	1			
SKKT 107B16 E	1600	119	85	1900	0.9	3.35	0.19	0.22	-40 ... +130	1			
SKKT 122	800-1800	129	85	3200	0.85	2.00	0.2	0.13	-40 ... +125	2			
SKKT 132	800-1800	137	85	4000	1	1.60	0.18	0.1	-40 ... +125	2			
SKKT 132 H4	2000-2200	128	85	3800	1.1	2.00	0.17	0.1	-40 ... +125	2			
SKKT 162	800-1800	156	85	5000	0.85	1.50	0.17	0.1	-40 ... +125	2			
SKKT 162 H4	2000-2200	143	85	4800	0.95	2.00	0.16	0.1	-40 ... +125	2			
SKKT 172	1400-1800	175	85	5000	0.83	1.30	0.155	0.1	-40 ... +125	2			
SKKT 250	800-1800	250	85	8000	0.925	0.45	0.14	0.04	-40 ... +130	3			
SKKT 273	1200-1800	273	85	8000	0.9	0.92	0.104	0.08	-40 ... +130	3			
SKKT 280 H4	2000-2200	252	85	7500	0.9	0.75	0.11	0.04	-40 ... +125	3			
SKKT 330	800-1800	305	85	8000	0.8	0.60	0.11	0.04	-40 ... +130	3			
SKKT 323	1200-1600	320	85	8200	0.81	0.85	0.091	0.08	-40 ... +130	3			
SKKT 460	1600	460	85	15500	0.88	0.45	0.072	0.02	-40 ... +130	5			
SKKT 460 H4	2200	460	85	15500	0.88	0.45	0.072	0.02	-40 ... +130	5			
SKKT 570	1200-1800	570	85	15500	0.78	0.32	0.069	0.02	-40 ... +135	5			



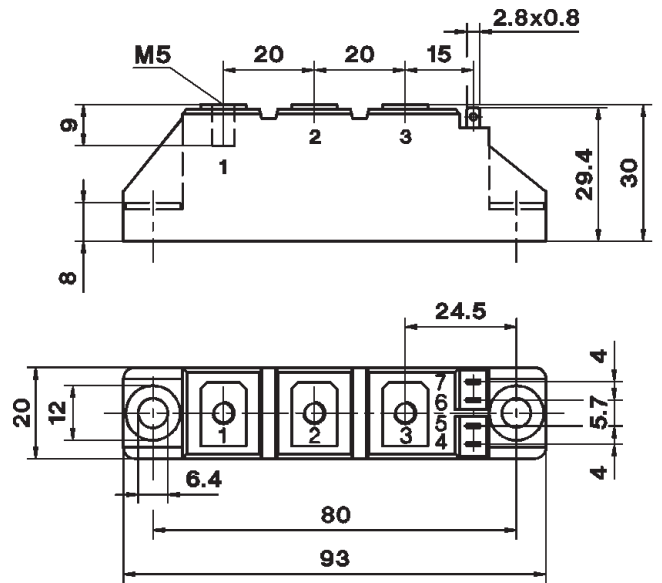
Thyristor / Diode Modules / SEMIPACK

Cases

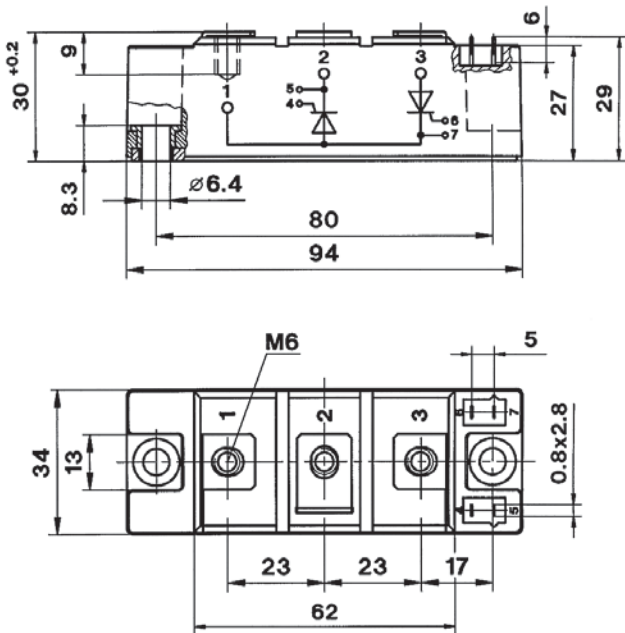
SEMIPACK 0



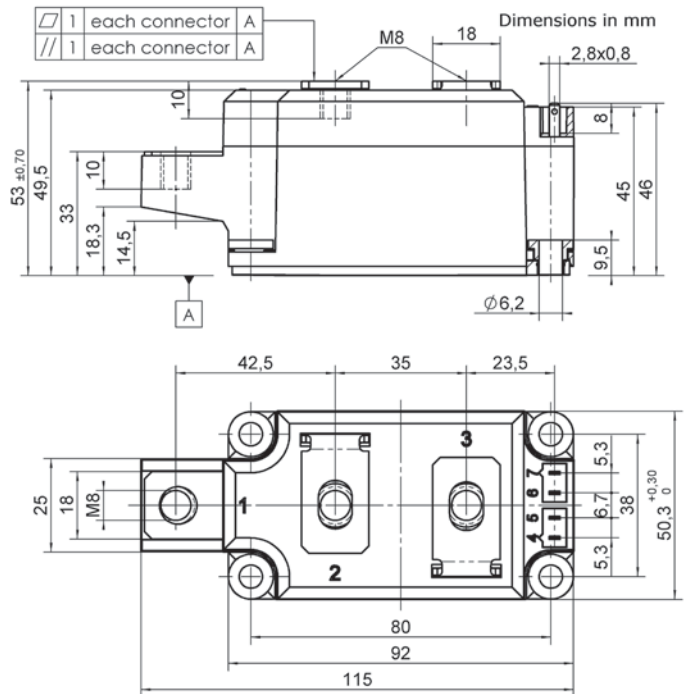
SEMIPACK 1



SEMIPACK 2



SEMIPACK 3



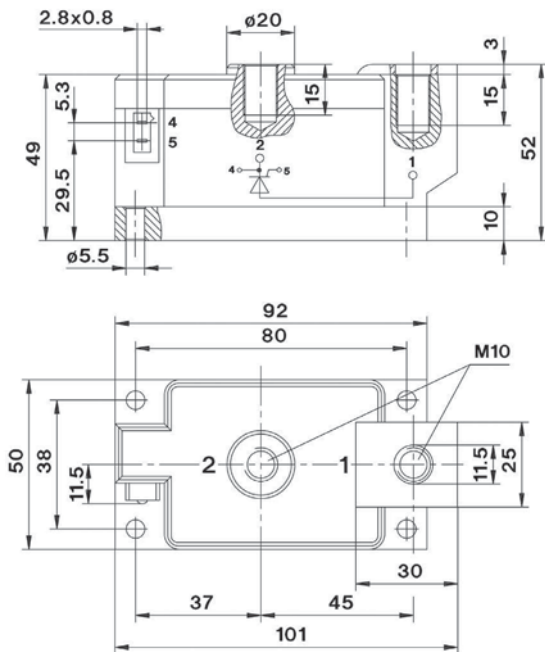
General tolerance ± 0.5 mm

Dimensions in mm

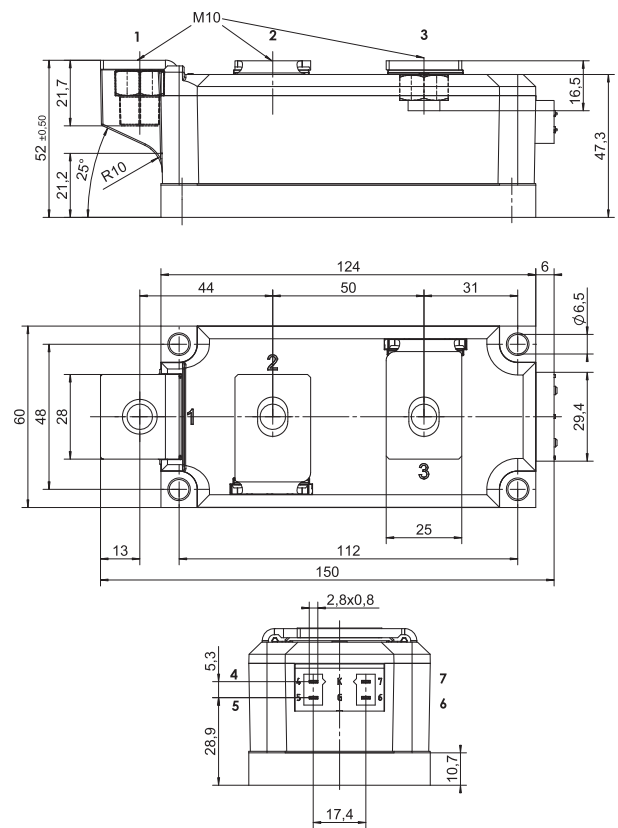
Thyristor / Diode Modules / SEMIPACK

Cases

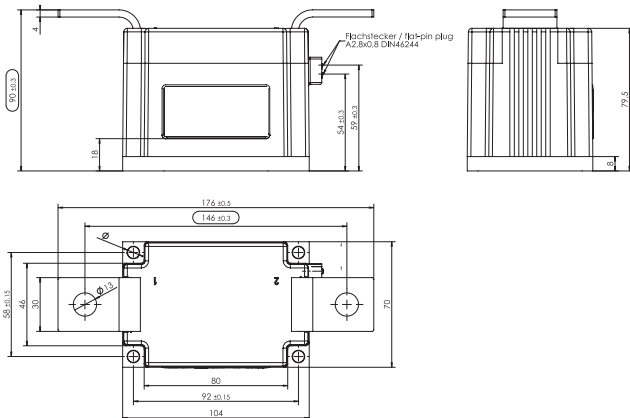
SEMIPACK 4



SEMIPACK 5



SEMIPACK 6



Dimensions in mm

Thyristor / Diode Modules / SEMIPACK FAST

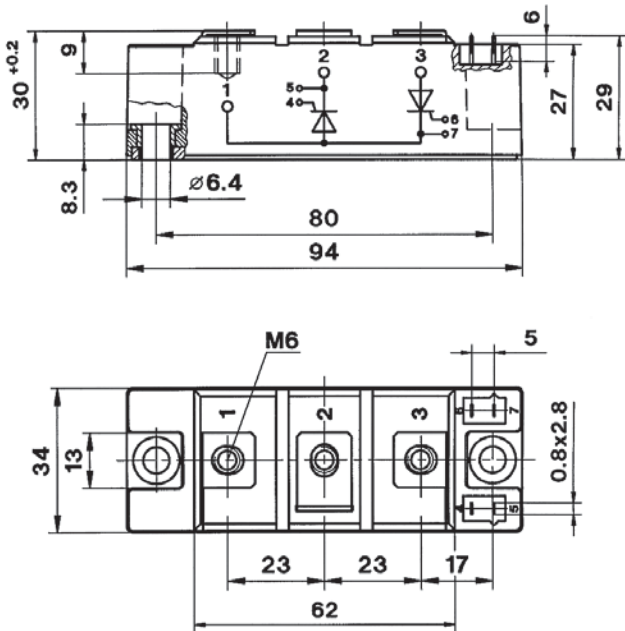
Type

	V_{RRM}	$I_{TAV} I_{FAV}$	T_C	I_{FSM}	$V_{T(RO)}$	r_T	$R_{th(j-c)}$ per chip	$R_{th(c-s)}$	T_j	Case	Circuit
	V	A		$^{\circ}C$	A	V		m Ω			
SKKE 120F	1700	120	82	1800	1.5	4.5	0.2	0.05	-40 ... +150	2	
SKKE 290F	600	290	109	6000	0.9	1.2	0.08	0.05	-40 ... +150	2	
SKKE 301F	1200	300	43	3600	1.2	2.75	0.11	0.05	-40 ... +150	2	
SKKE 310F	1200	310	84	5500	1.2	1.9	0.08	0.05	-40 ... +150	2	
SKKE 330F ³⁾	1700	330	70	5200	1.5	1.9	0.079	-	-40 ... +150	4	
SKKE 600F ³⁾	1200	600	85	5800	1.2	1.9	0.062	-	-40 ... +150	4	
SKKD 40F	600-1000	40	80	940	1.2	4	0.7	0.2	-40 ... +125	1	
SKKD 42F	1200-1400	42	85	1100	1	5	0.7	0.2	-40 ... +130	1	
SKKD 60F	1700	60	83	900	1.5	9	0.4	0.1	-40 ... +150	2	
SKKD 75F12	1200	75	55	900	1.2	11	0.4	0.1	-40 ... +150	2	
SKKD 150F	1200	150	54	1800	1.2	5.5	0.2	0.1	-40 ... +150	2	
SKKD 170F	1200	170	85	2300	1.2	3.5	0.14	0.1	-40 ... +150	2	
SKKD 205F	600	205	87	3000	0.9	2	0.16	0.1	-40 ... +150	2	
SKMD 150F12	1200	150	54	1800	1.2	5.5	0.2	0.1	-40 ... +150	2	
SKMD 202E	200-300	202	87	2800	0.8	1.5	0.2	0.1	-40 ... +150	2	
SKND 150F	1200	150	54	1800	1.2	5.5	0.2	0.1	-40 ... +150	2	
SKND 202E	200-300	202	87	2800	0.8	1.5	0.2	0.1	-40 ... +150	2	
SKND 205F	600	205	87	3000	0.9	2	0.16	0.1	-40 ... +150	2	

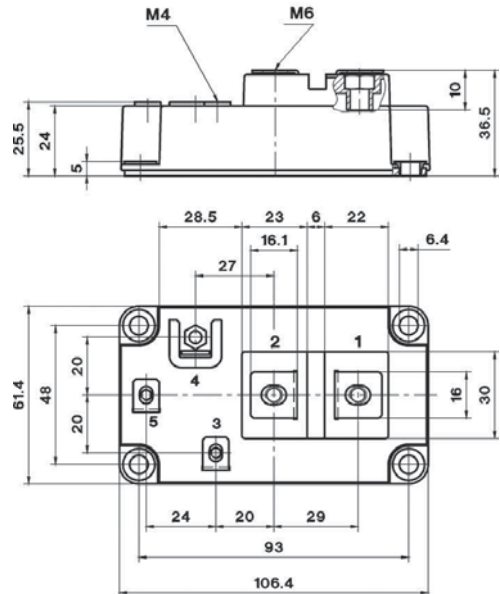
Footnotes: 3) SEMIPACK Fast in SEMITRANS 4 case

Cases

SEMIPACK 2



SEMIPACK Fast in SEMITRANS 4



Dimensions in mm

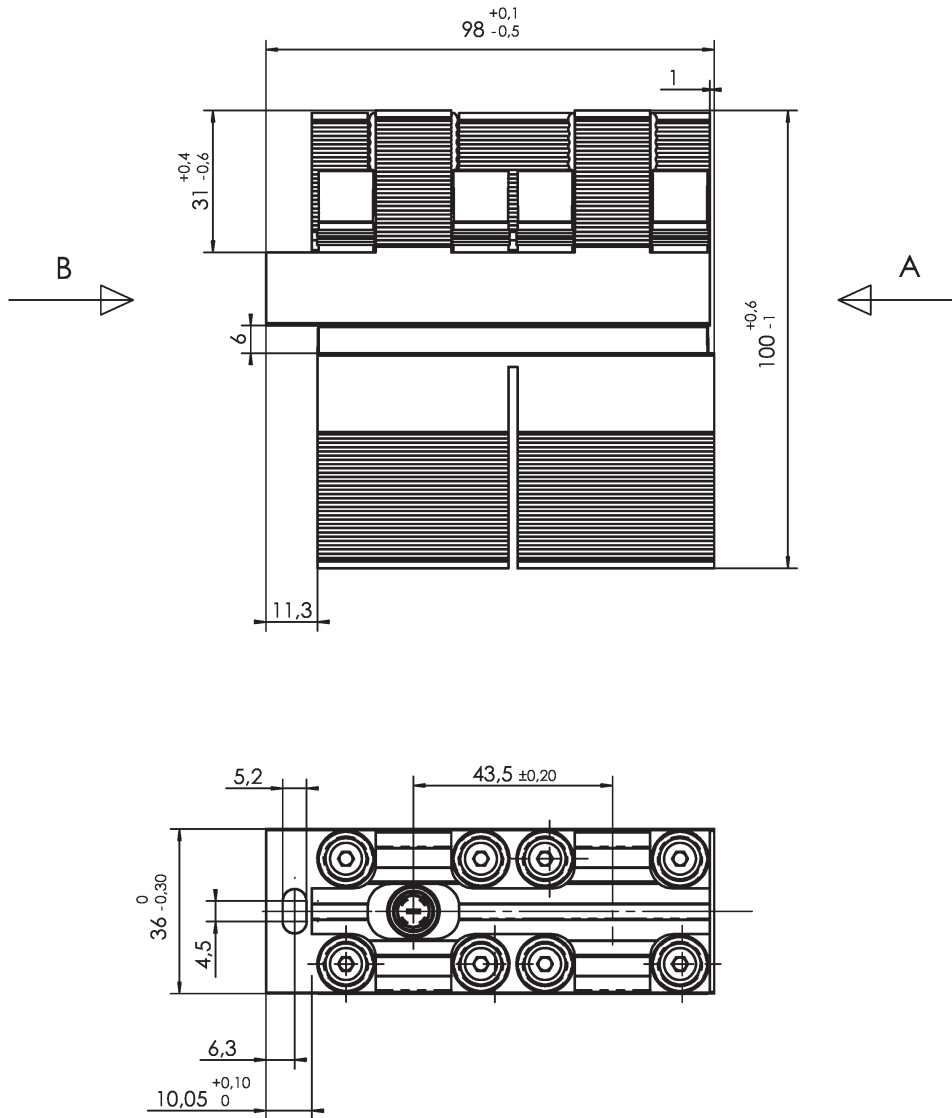
Thyristor Modules / SEMiSTART

Type

	V_{RRM} V_{DRM}	$I_{overload}$ W1C (for 20s)	T_c	I_{TSM} @ $T_j = 125^\circ C$	$V_{T(TO)}$ @ $T_{jmax} = 125^\circ C$	r_T @ $T_{jmax} = 125^\circ C$	$R_{th(j-r)}$ cont. per chip	T_{jmax} (for 20s)	Case	Circuit
	V	A	$^\circ C$	A	V	m Ω	K/W	$^\circ C$		
SKKQ 560	1400-1800	560	150	5200	0.9	0.9	0.106	150	1	
SKKQ 800	1400-1800	800	150	5200	0.9	0.8	0.106	150	2	
SKKQ 1200	1400-1800	1225	150	8000	0.9	0.5	0.066	150	2	
SKKQ 1500	1400-1800	1500	150	15000	0.85	0.3	0.037	150	2	
SKKQ 3000	1400-1800	3080	150	25500	0.95	0.18	0.026	150	3	

Cases

SEMiSTART 1

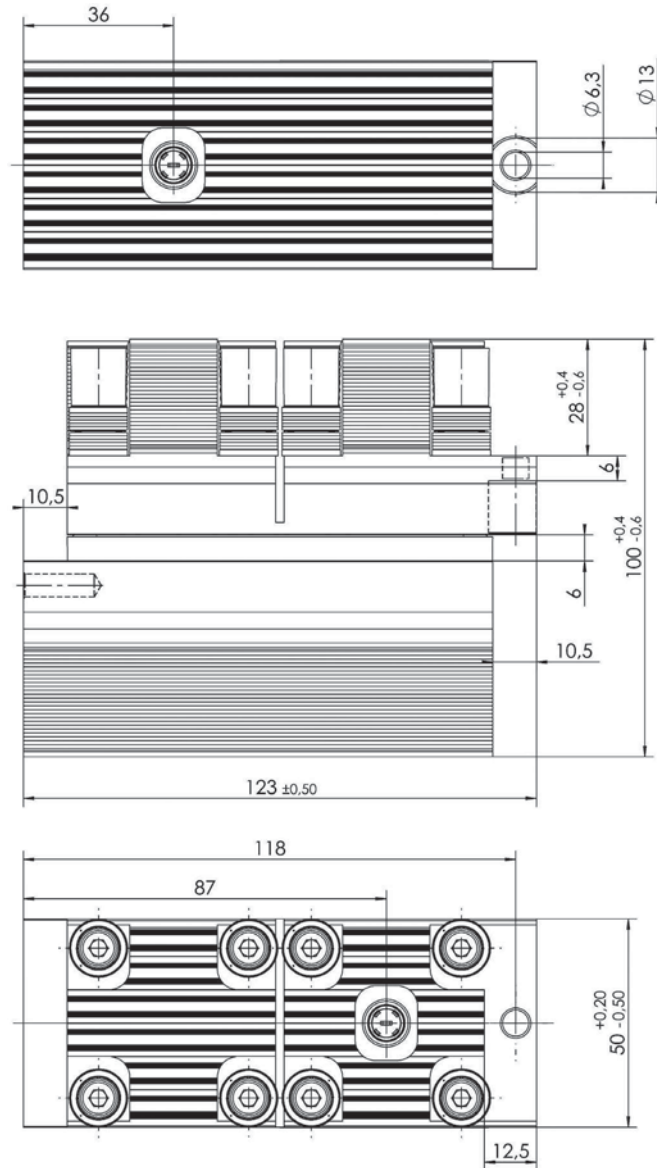


Dimensions in mm

Thyristor Modules / SEMiSTART

Cases

SEMiSTART 2

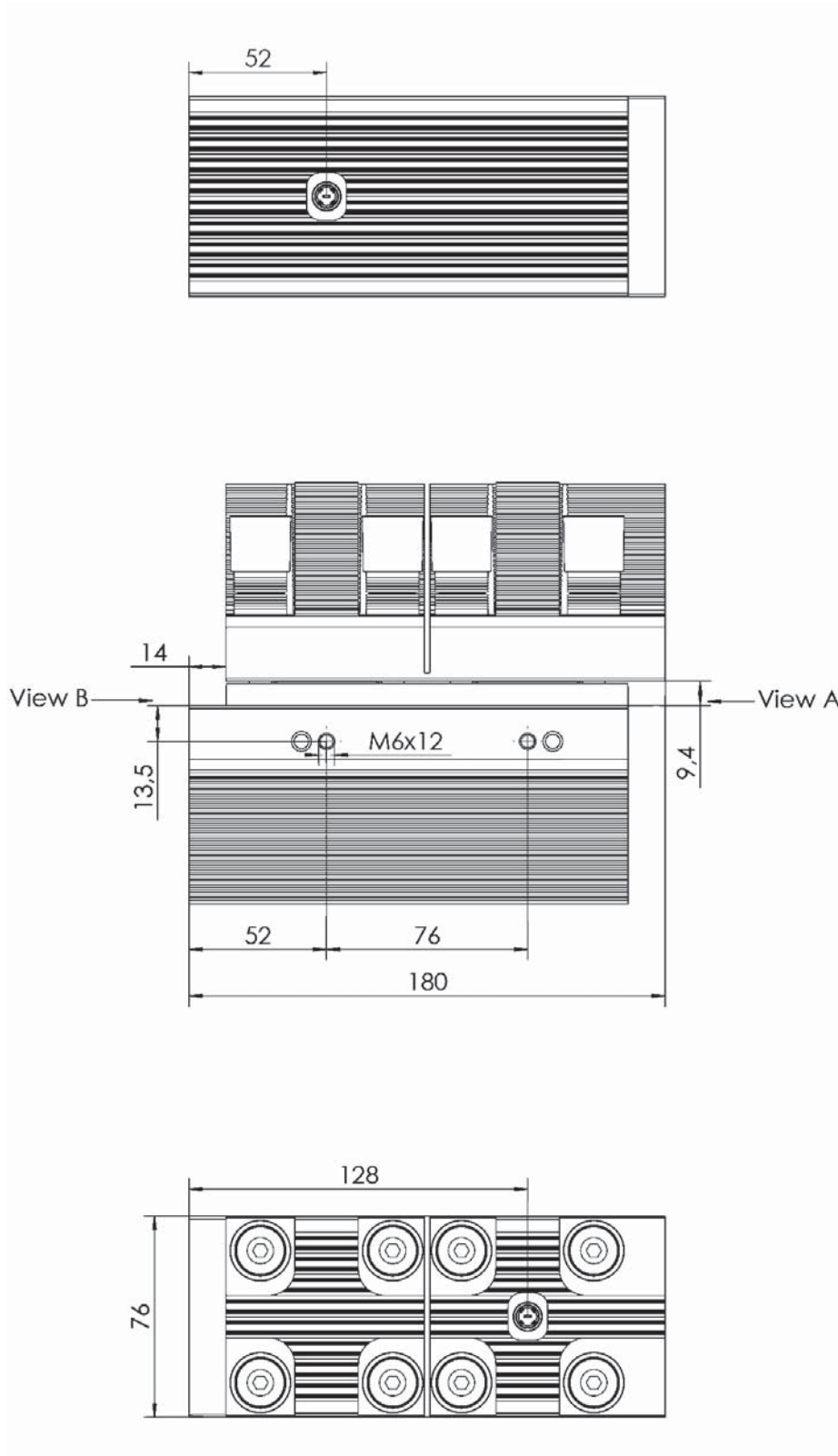


Dimensions in mm

Thyristor Modules / SEMiSTART

Cases

SEMISTART 3



Dimensions in mm

Bridge Rectifier Modules for Reliable Inverter Design

Bridge rectifiers are components which have every branch of a rectifier circuit in a single, compact case. Bridge rectifiers exist from a few amps to several hundred amps in different package types.

SEMIKRON offers bridge rectifier modules in single phase or 3-phase topology with or without brake chopper. The bridge rectifier modules are available in different package like SEMiX, SEMITOP, SEMIPONT, Power Bridge and MiniSKiiP.

Product	Page
MiniSKiiP	104
SEMITOP	106
SEMIPONT	108
SEMiX	112
Power Bridge	113

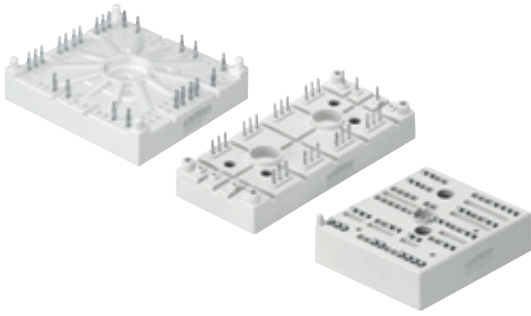
▶ For detailed information
please refer data sheets.

Further information:
www.semikron.com/bridge-rectifier-modules

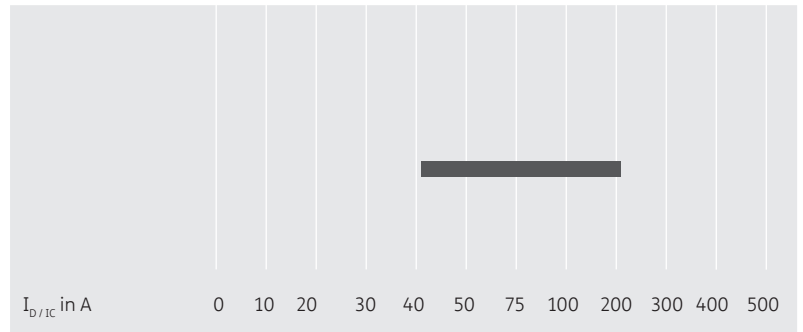
Bridge Rectifier Modules

SEMITOP®/SEMIPONT®/MiniSKiiP®

rectifier with
brake chopper



600V up to 1800V

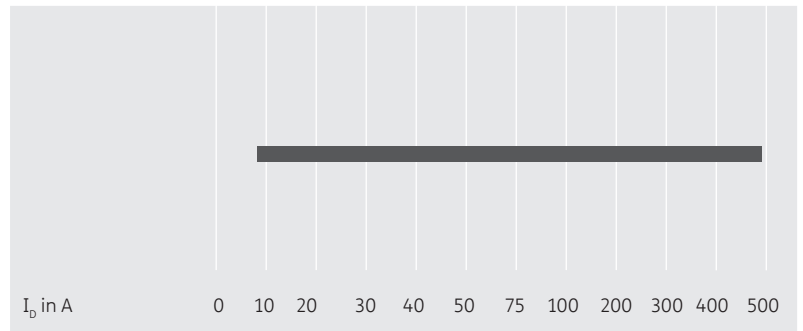


SEMITOP®/SEMIPONT®/SEMiX®/ Power Bridge

three phase



400V up to 1800V

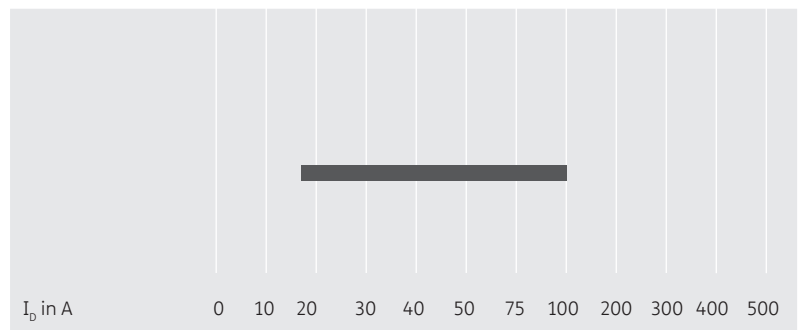


SEMIPONT®/SEMITOP®/ Power Bridge

single phase



400V up to 1800V



Bridge Rectifier Modules / MiniSKiiP

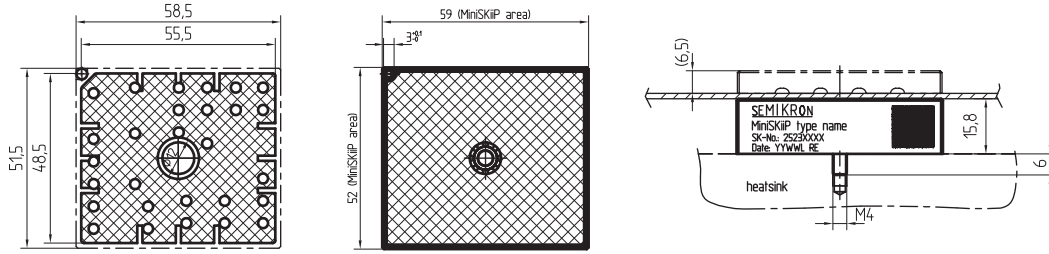
Type	IGBT						Diode					Rectifier		Module		Circuit
	$I_C@T_s=25^\circ\text{C}$ A	I_{Cnom} A	$V_{CE(sat)}@T_j=25^\circ\text{C typ.}$ V	E_{on} mJ	E_{off} mJ	$R_{th(j-s)}$ K/W	$I_F@T_s=25^\circ\text{C}$ A	$V_F@T_j=25^\circ\text{C typ.}$ V	E_{rr} mJ	$R_{th(j-s)}$ K/W	$R_{th(j-s)}$ K/W	$I_{FSM}@T_s=25^\circ\text{C}$ A	Case	$R_{th(c-s)}$ K/W		
1200V - IGBT3 (Trench)																
SKiiP 28ANB16V1	1000	83	1.70	13.1	13	0.4	118	1.60	11.2	0.55	0.7	1000	II 2	-		
SKiiP 39ANB16V1	1600	124	1.70	19.9	17.2	0.3	167	1.50	16.2	0.4	0.5	1600	II 3	-		
1700V - IGBT3 (Trench)																
SKiiP 28AHB16V1	1000	82	1.70	14.4	13.3	0.4	118	1.60	10.8	0.55	0.7	1000	II 2	-		
SKiiP 39AHB16V1	1250	121	1.70	19.9	17.3	0.3	167	1.50	16.2	0.4	0.5	1250	II 3	-		
1700V - IGBT3 (Trench)																
SKiiP 28ANB18V3 ¹⁾	1000	98	2.00	23	32.7	0.33	119	1.8	26.4	0.58	0.64	1000	II 2	-		

Footnotes: 1) New product

Bridge Rectifier Modules / MiniSKiiP

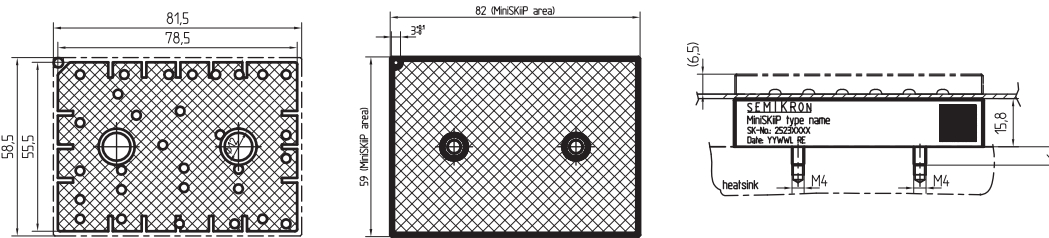
Cases

MiniSKiiP II 2



pin configuration depends on circuit
(details in data sheet)

MiniSKiiP II 3



pin configuration depends on circuit
(details in data sheet)

Dimensions in mm

Bridge Rectifier Modules / SEMITOP

Type

Type	V_{RRM} V_{DRM} V	I_p @ T_s A	T_s °C	I_{FSM} @ T_{jmax} A	$V_{T(ro)}$ @ T_{jmax} V	r_T @ T_{jmax} mΩ	$R_{th(j-c)}$ per chip K/W	T_j °C	Case	Circuit
1 and 3 phase										
SK 50 B 06 UF	600	46	80	400	0.8	11.00	0.45	-40 ... +150	2	
SK 50 B	800-1600	51	80	270	0.8	13.00	1.7	-40 ... +150	2	
SK 55 B 06 F	600	54	80	440	0.9	16.00	1.2	-40 ... +150	2	
SK 55 B 12 F	1200	57	80	550	1.2	22.00	0.9	-40 ... +150	2	
SK 70 B	800-1600	68	80	560	0.8	11.00	1.2	-40 ... +150	2	
SK 100 B	800-1600	100	80	890	0.83	3.90	1	-40 ... +150	2	
SK 40 DT	800-1600	42	80	280	1.1	20.00	1.7	-40 ... +125	3	
SK 70 DT	800-1600	68	80	380	1	10.00	1.2	-40 ... +125	3	
SK 55 D	800-1600	55	80	200	0.8	13.00	2.15	-40 ... +150	2	
SK 70 D	800-1600	70	80	270	0.8	13.00	1.7	-40 ... +150	2	
SK 80 D 12F	1200	80	80	550	1.2	22.00	0.9	-40 ... +150	3	
SK 95 D	800-1600	95	80	560	0.8	11.00	1.2	-40 ... +150	2	
SK 95 D 16p ⁸⁾	1600	95	80	560	0.8	11.00	1.2	-40 ... +150	2p	
SK 40 DH	800-1600	42	80	270	1.1	20.00	1.7	-40 ... +150	3	
SK 70 DH	800-1600	68	80	270	1	10.00	1.2	-40 ... +125	3	
SK 55 DGL 126	1200	55	80	370	0.8	13.00	2	-40 ... +150	3	
SK 95 DGL 126	1600	96	80	700	0.8	11.00	1.2	-40 ... +150	3	
SK 170 DHL 126	1200	170	70	1000	0.8	7.00	0.51	-40 ... +150	4	
SK 200 DHL 066	600	210	70	1250	0.8	4.00	0.52	-40 ... +150	4	

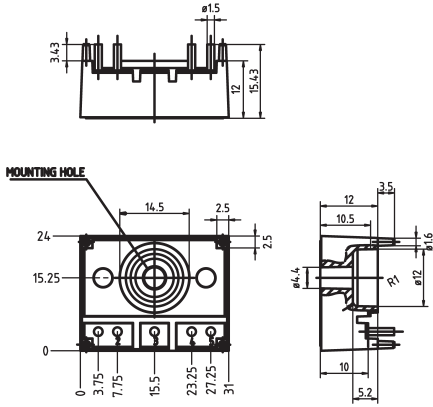
Footnotes: 8) Target data

Bridge Rectifier Modules / SEMITOP

Cases

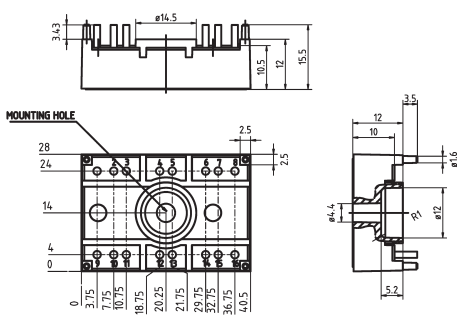
SEMISTOP 1

dimensions in mm
tolerance system: ISO 2768-m

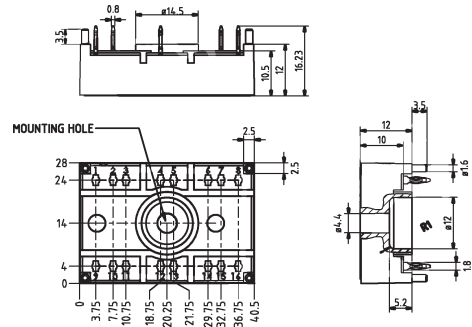


SEMISTOP 2

dimensions in mm
tolerance system: ISO 2768-m

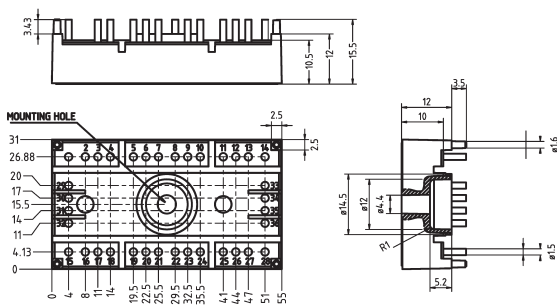


SEMISTOP 2 Press-Fit



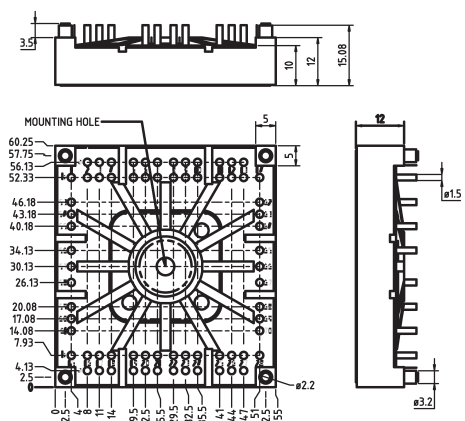
SEMISTOP 3

dimensions in mm
tolerance system: ISO 2768-m



SEMISTOP 4

dimensions in mm
tolerance system: ISO 2768-m



Dimensions in mm

Bridge Rectifier Modules / SEMIPONT

Type

Type	$V_{RRM} V_{DRM}$ V	$I_p @ T_c$ A	T_c °C	$I_{TSM} I_{FSM} @ T_{jmax}$ A	$V_{T(TO)} @ T_{jmax}$ V	$r_T @ T_{jmax}$ mΩ	$R_{th(j-c)}$ cont. per chip K/W	T_j °C	Case	Circuit
1 and 3 phase										
SKB 52	400-1800	50	99	425	0.85	8	1.5	-40 ... +150	3	
SKB 60	400-1600	60	88	850	0.85	5	1	-40 ... +125	2	
SKB 72	400-1800	70	101	640	0.85	5	1.1	-40 ... +150	3	
SKBH 28	600-1400	28	89	280	1	16	1.8	-40 ... +125	1	
SKBZ 28	400-1400	28	89	280	1	16	1.8	-40 ... +125	1	
SKBT 28	600-1400	28	89	280	1	16	1.8	-40 ... +125	1	
SKBT 40	800-1400	40	92	400	1	16	1	-40 ... +125	2	
SKCH 28	400-1400	28	89	280	1	16	1.8	-40 ... +125	1	
SKCH 40	400-1600	40	92	400	1	16	1	-40 ... +125	2	

Bridge Rectifier Modules / SEMIPONT

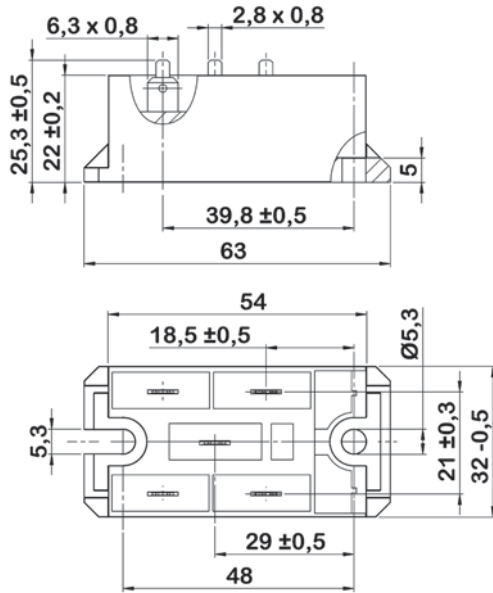
Type

	V_{RRM} V_{DRM}	I_p @ T_c	T_c	I_{FSM} $I_{FSM}@T_{jmax}$	$V_{TTO}@T_{jmax}$	r_T $r_T@T_{jmax}$	$R_{th(j-c)}$ cont. per chip	T_j	Case	Circuit
	V	A	°C	A	V	mΩ	K/W	°C		
1 and 3 phase										
SKDT 60	400-1400	60	86	400	1	16	1	-40 ... +125	2	
SKDT 115	1200-1600	110	80	950	1.1	6.00	0.84	-40 ... +125	5	
SKDT 145	1200-1600	145	80	1250	0.9	5.00	0.6	-40 ... +125	5	
SKD 31	200-1600	31	100	320	0.85	12	2	-40 ... +125	1	
SKD 60	400-1600	60	102	850	0.85	5	1	-40 ... +125	2	
SKD 62	400-1800	60	110	425	0.85	8	1.5	-40 ... +150	3	
SKD 82	400-1800	80	110	640	0.85	5	1.1	-40 ... +150	3	
SKD 100	400-1600	100	93	1000	0.85	5	0.85	-40 ... +125	2	
SKD 110	800-1800	110	100	1000	0.85	4	0.9	-40 ... +150	4	
SKD 115	1200-1800	110	85	1150	0.8	7.00	1	-40 ... +150	5	
SKD 145	1200-1800	145	85	1700	0.8	4.00	0.8	-40 ... +150	5	
SKD 160	800-1800	205	100	1500	0.85	3	0.65	-40 ... +150	4	
SKD 210	900-1800	207	99	1600	0.85	3	0.5	-40 ... +150	4	
SKDH 100	800-1400	100	84	850	1	4.5	0.85	-40 ... +125	2	
SKDH 115	1200-1600	110	80	950	1.1	6.00	0.84	-40 ... +125	5	
SKDH 145	1200-1600	145	80	1250	0.9	5.00	0.63	-40 ... +125	5	
3 phase with brake chopper										
SKD 146/..-L105	1200-1600	140	85	1250	0.8	4	0.8	-40 ... +125	6	
SKD146/..-L140T4	1200-1600	140	85	1250	0.8	4	0.8	-40 ... +125	6	
SKD 116/18-L 75	1800	110	85	1050	0.8	7.00	0.8	-40 ... +125	6	
SKD 116/..-L105	1200-1600	110	85	1050	0.8	7	1	-40 ... +125	6	
SKD 116/..-L140	1200-1600	110	85	1050	0.8	7	1	-40 ... +125	6	
SKDH116/..L105	1200-1600	110	85	1000	0.8	7	1	-40 ... +125	6	
SKDH116/..L140	1200-1600	110	85	1000	0.8	7	1	-40 ... +125	6	
SKDH146/..-L105	1200-1600	140	85	1250	0.8	4	0.8	-40 ... +125	6	
SKDH146/..-L140	1200-1600	140	85	1250	0.8	4	0.8	-40 ... +125	6	

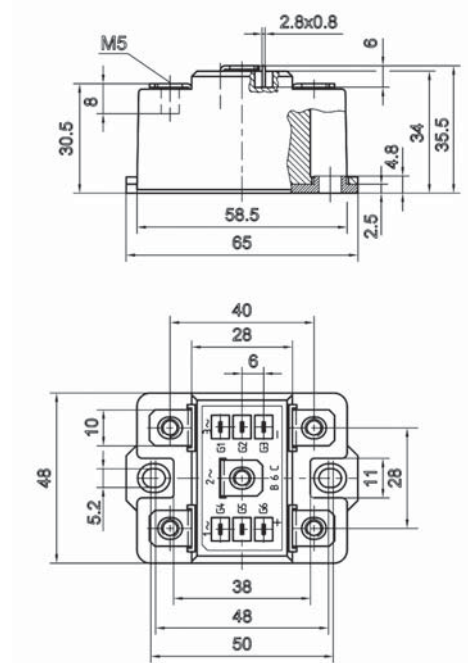
Bridge Rectifier Modules / SEMIPONT

Cases

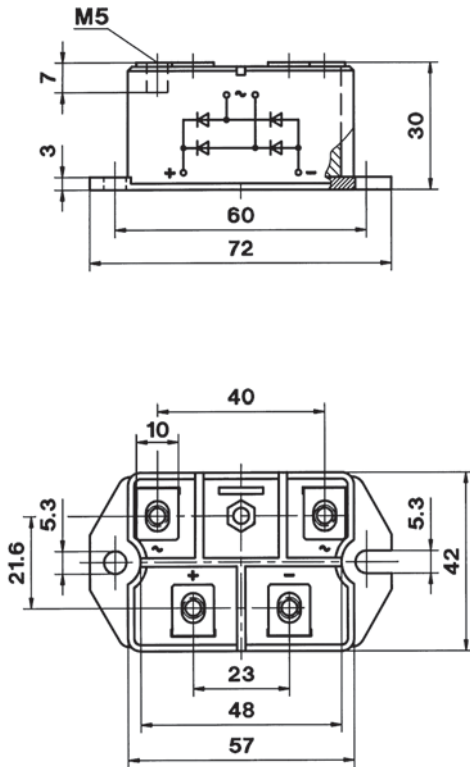
SEMIPONT 1



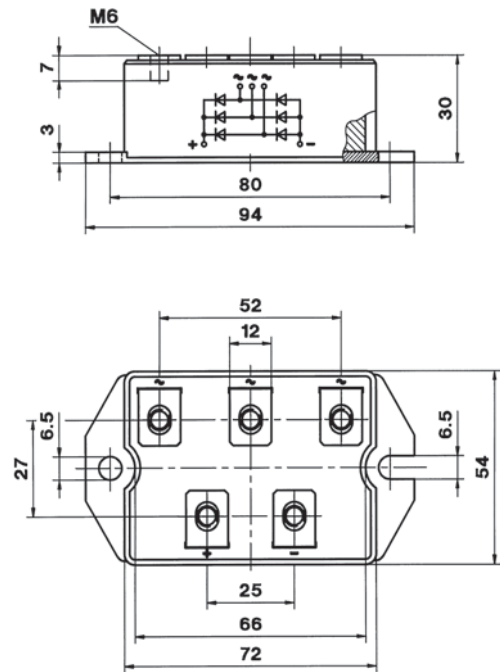
SEMIPONT 2



SEMIPONT 3



SEMIPONT 4

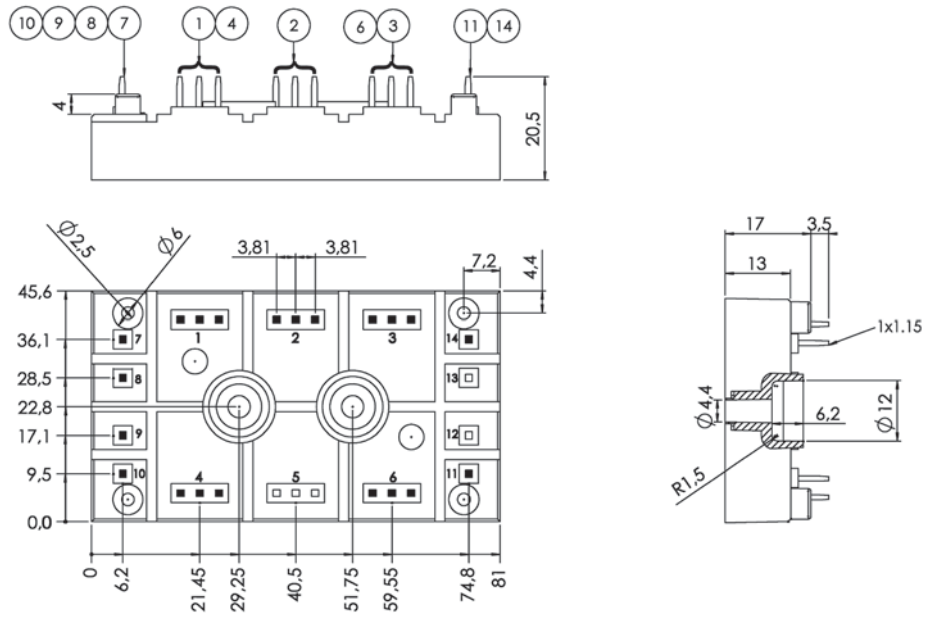


Dimensions in mm

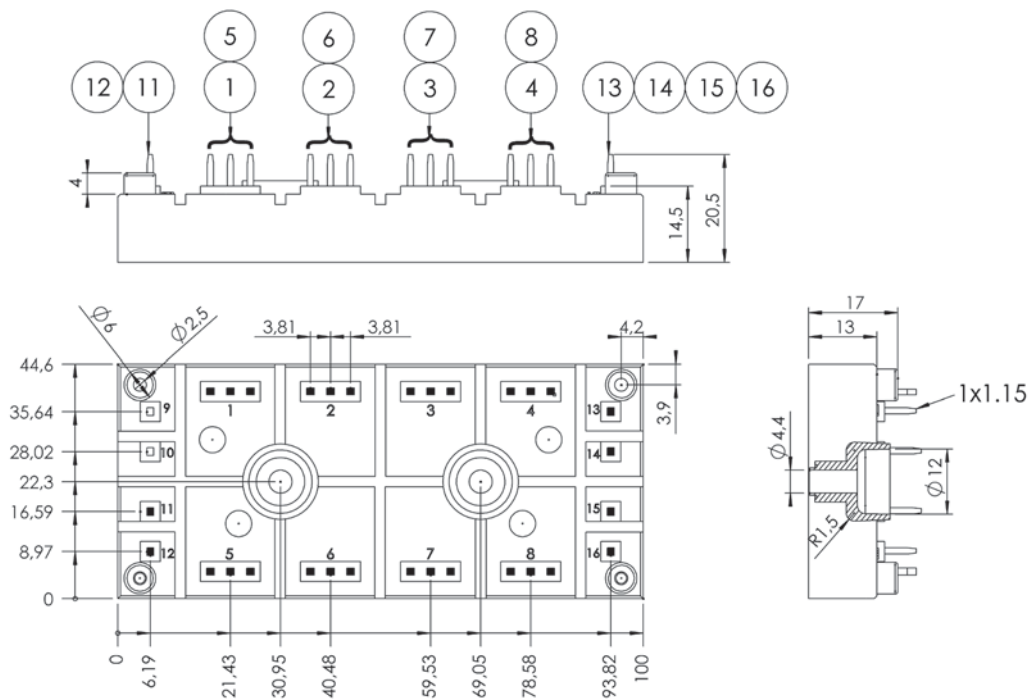
Bridge Rectifier Modules / SEMIPONT

Cases

SEMIPONT 5



SEMIPONT 6



Dimensions in mm

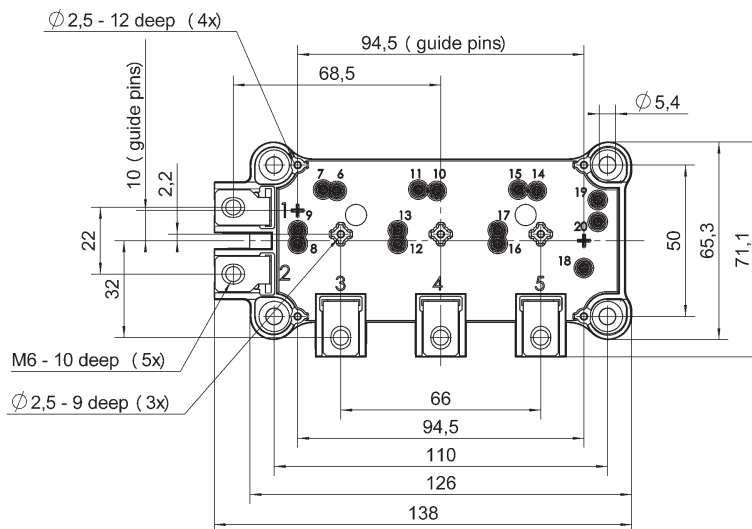
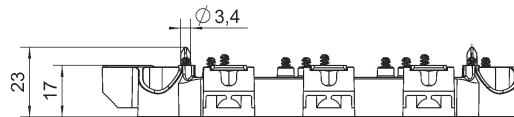
Bridge Rectifier Modules / SEMiX

Type

	$V_{RRM} V_{DRM}$ V	$I_p @ T_c$ A	T_c °C	$I_{FSM} I_{FSM} @ T_{jmax}$ A	$V_{(TTO)} @ T_{jmax}$ V	$r_T @ T_{jmax}$ mΩ	$R_{th(j-c)}$ per chip K/W	$R_{th(c-s)}$ K/W	T_j °C	Case	Circuit
3 phase											
SEMiX251D12Fs	1200	250	85	1330	1.2	7	0.26	0.04	-40 ... +150	13	
SEMiX291D16s	1600	290	85	1380	0.83	4.6	0.45	0.04	-40 ... +150	13	
SEMiX341D16s	1600	340	85	2000	0.9	2.7	0.22	0.04	-40 ... +130	13	
SEMiX501D17Fs	1700	489	85	2140	1.1	2.7	0.165	0.04	-40 ... +150	13	
SEMiX241DH16s	1600	240	85	1900	0.85	4	0.32	0.04	-40 ... +130	13	

Cases

SEMiX 13



Dimensions in mm

Bridge Rectifier Modules / Power Bridge

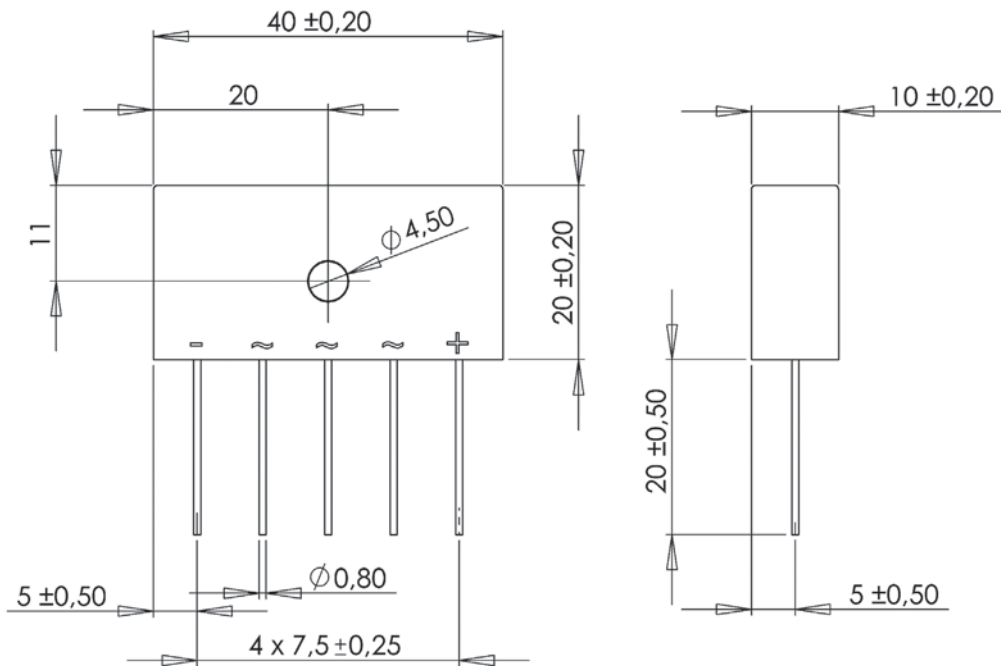
Type

	V_{RRM}, V_{DRM} V	$I_p @ T_{CS}$ A	T_{CS} °C	$I_{FSM} @ T_{jmax}$ A	$V_{T(ro)} @ T_{jmax}$ V	$r_{Tj} @ T_{jmax}$ mΩ	$R_{th(j-s)}$ cont. per chip K/W	T_j °C	Case	Circuit
1 phase										
SKB 25	100-1600	17	75	320	0.85	12.00	8.6	-40 ... +150	G 10b, G 11b	
SKB 26	200-1600	18	75	320	0.85	12.00	8.2	-40 ... +150	G 50a	
SKB 30	200-1600	30	94	320	0.85	12.00	3.2	-40 ... +150	G 12, G 13	
3 phase										
DBI 6	200-1600	9	90	150	0.85	30.00	18.9	-40 ... +150	DBI	
DBI 15	200-1600	15	75	210	0.85	12.00	15.3	-40 ... +150	DBI	
DBI 25	200-1600	25	32	310	0.85	9.00	14.1	-40 ... +150	DBI	
SKD 25	200-1600	20	73	320	0.85	12.00	11.4	-40 ... +150	G 10b, G 11b	
SKD 30	200-1600	30	98	320	0.85	12.00	4.8	-40 ... +150	G 12, G 13	
SKD 33	400-1800	33	110	240	0.8	18.00	2.5	-40 ... +150	G55	
SKD 51	400-1800	50	127	700	0.8	8.50	1.2	-40 ... +150	G51	
SKD 53	400-1800	53	100	270	0.8	13.00	1.9	-40 ... +150	G55	
SKD 83	400-1800	83	95	560	0.8	7.50	1.4	-40 ... +150	G55	

Bridge Rectifier Modules / Power Bridge

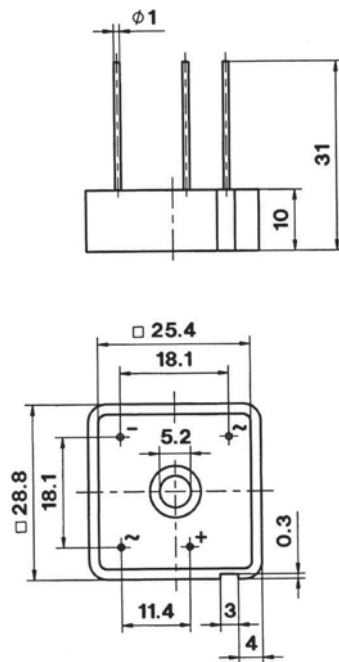
Cases

DBI



5

G 50a

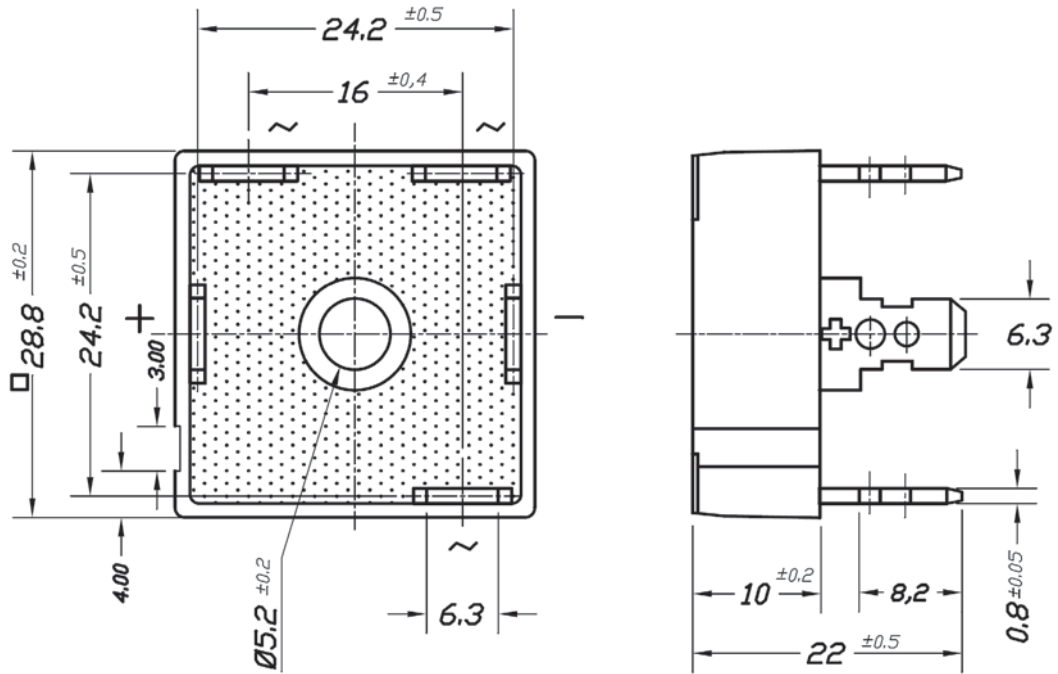


Dimensions in mm

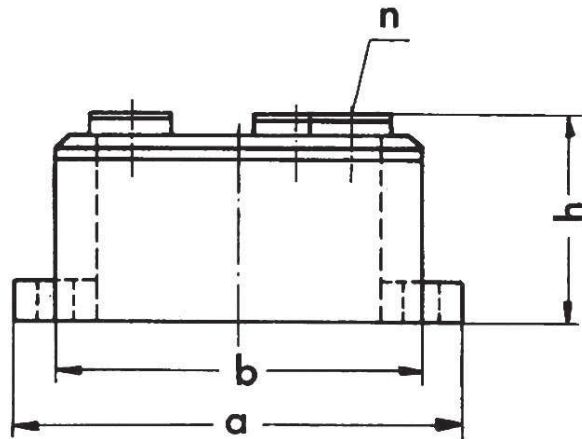
Bridge Rectifier Modules / Power Bridge

Cases

G 10b, G 11b



G 12, G 13



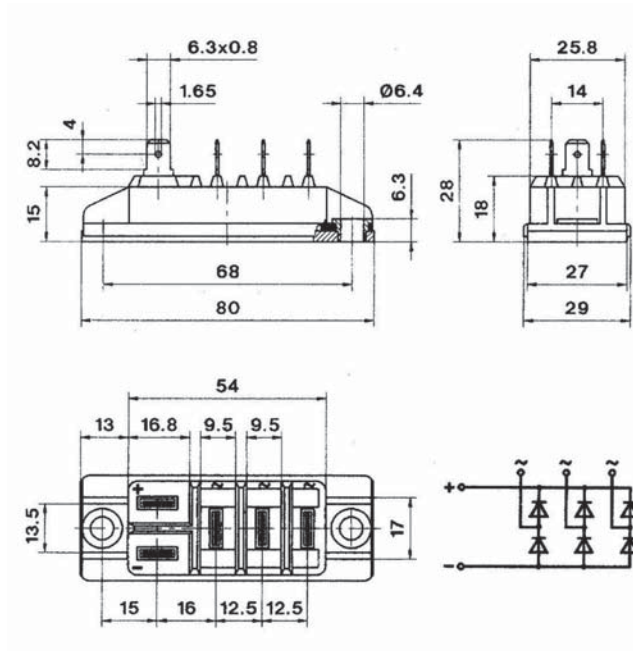
Cases	a	b	h	n
G 12, 13	55	45	24	M 4

Dimensions in mm

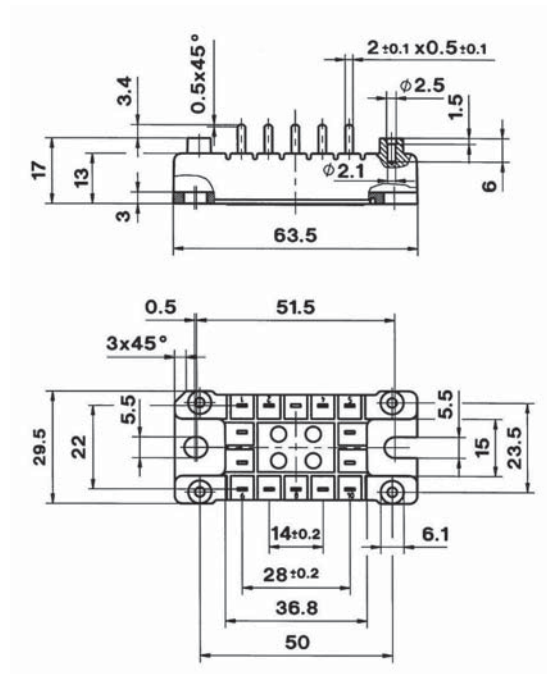
Bridge Rectifier Modules / Power Bridge

Cases

G 51



G 55



Dimensions in mm

IPM

SEMIKRON Offers Highly Integrated IPMs

The SKiiP IPMs represent the benchmark for regenerative inverter solutions up to 5MW.

Product	Page
SKiiP 3/4	120
SKiiP Accessories	129

▶ For detailed information please refer data sheets.

Further information:
www.semikron.com/ipm

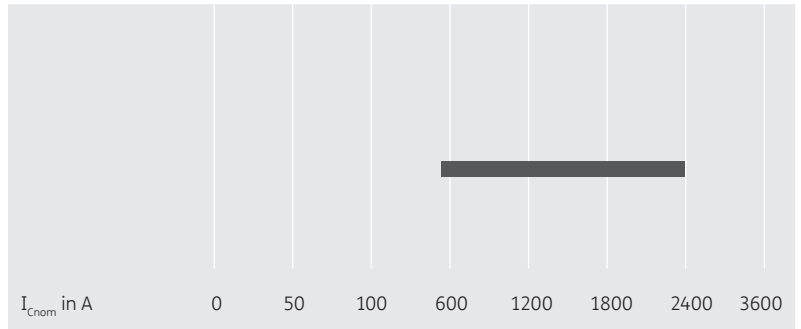
IPM

SKiiP[®]3

6-pack
half bridge



1200V up to 1700V

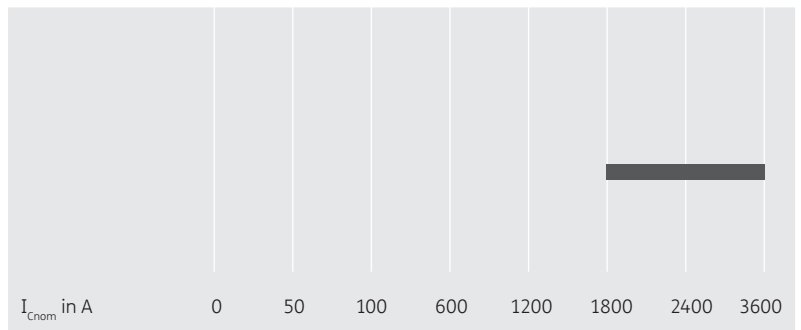


SKiiP[®]4

half bridge



1200V up to 1700V



IPM / SKiiP

Type	IGBT				Diode			Options F=F-Option U=U-Option S=SKiFace Adapter	Case	Circuit
	$I_c @ T_s = 25^\circ\text{C}$ A	I_{nom} A	$V_{CE(sat)} @ T_j = 25^\circ\text{C typ.}$ V	$E_{on} + E_{off}$ mJ	$I_T @ T_s = 25^\circ\text{C}$ A	$V_T @ T_j = 25^\circ\text{C typ.}$ V	E_{rr} mJ			
1200V - IGBT 3 (Trench) - SKiiP3										
SKiiP 603 GD123-3DUL V3	627	600	1.7	195	508	1.50	28	-	S33	
SKiiP 603 GD123-3DUW V3	627	600	1.7	195	508	1.50	28	-	S33	
SKiiP 613 GD123-3DUL V3	577	600	1.7	195	466	1.50	28	-	S33	
SKiiP 613 GD123-3DUW V3	577	600	1.7	195	466	1.50	28	-	S33	
SKiiP 1213 GB123-2DL V3	1145	1200	1.7	390	925	1.50	56	F	S23	
SKiiP 1213 GB123-2DW V3	1145	1200	1.7	390	925	1.50	56	F	S23	
SKiiP 1813 GB123-3DL V3	1695	1800	1.7	585	1411	1.50	84	F,U	S33	
SKiiP 1813 GB123-3DW V3	1695	1800	1.7	585	1411	1.50	84	F,U	S33	
SKiiP 2413 GB123-4DL V3	2280	2400	1.7	780	1807	1.50	112	F,U	S43	
SKiiP 2413 GB123-4DW V3	2280	2400	1.7	780	1807	1.50	112	F,U	S43	
1200V - IGBT 4 (Trench) - SKiiP4										
SKiiP 1814 GB12E4-3DUL	2345	1800	2.01	1260	1776	2.33	150	F,S	S34	
SKiiP 1814 GB12E4-3DUW	2345	1800	2.01	1260	1776	2.33	150	F,S	S34	
SKiiP 1814 GB12E4-3DUSL	2345	1800	2.01	1260	1776	2.33	150	F,S	S34	
SKiiP 2414 GB12E4-4DUL	3109	2400	2.01	1680	2369	2.33	200	F,S	S44	
SKiiP 2414 GB12E4-4DUW	3109	2400	2.01	1680	2369	2.33	200	F,S	S44	
SKiiP 2414 GB12E4-4DUSL	3109	2400	2.01	1680	2369	2.33	200	F,S	S44	
SKiiP 3614 GB12E4-6DUL	4664	3600	2.01	2520	3558	2.33	300	F,S	S64	
SKiiP 3614 GB12E4-6DUW	4664	3600	2.01	2520	3558	2.33	300	F,S	S64	
SKiiP 3614 GB12E4-6DULR	4664	3600	2.01	2520	3558	2.33	300	F,S	S64	
SKiiP 3614 GB12E4-6DUSL	4664	3600	2.01	2520	3558	2.33	300	F,S	S64	
1700V - IGBT 3 (Trench) - SKiiP3										
SKiiP 513 GD172-3DUL V3	540	500	1.9	288	438	2.00	43	-	S33	
SKiiP 513 GD172-3DUW V3	540	500	1.9	288	438	2.00	43	-	S33	
SKiiP 603 GD172-3DUL V3	587	570	1.9	288	476	2.00	43	-	S33	
SKiiP 603 GD172-3DUW V3	570	570	1.9	288	476	2.00	43	-	S33	

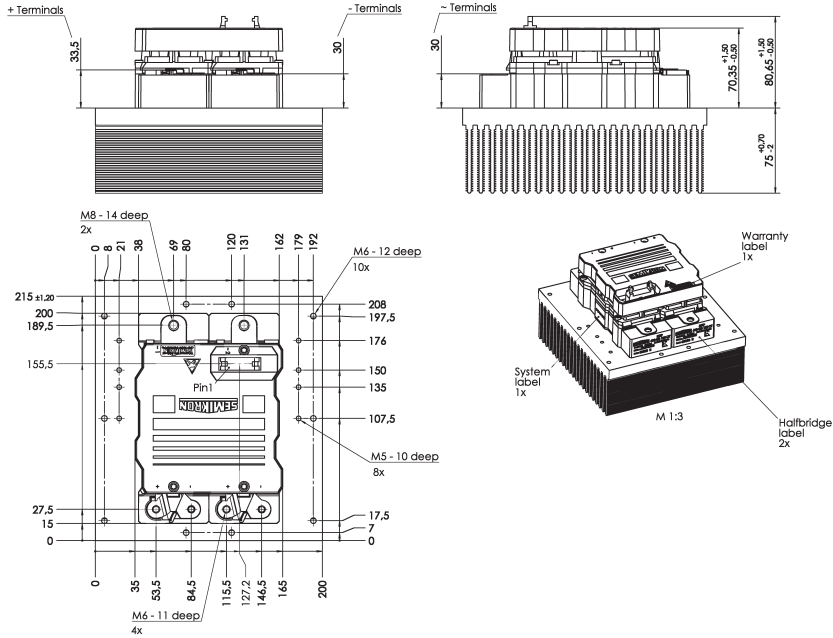
IPM / SKiiP

Type	IGBT				Diode			Options F=F-Option U=U-Option S=SKiFace Adapter	Case	Circuit
	$I_c @ T_s = 25^\circ\text{C}$ A	I_{nom} A	$V_{CE(sat)} @ T_j = 25^\circ\text{C typ.}$ V	$E_{on} + E_{off}$ mJ	$I_f @ T_s = 25^\circ\text{C}$ A	$V_f @ T_j = 25^\circ\text{C typ.}$ V	E_{rr} mJ			
1700V - IGBT 3 (Trench) - SKiiP3										
SKiiP 1013 GB172-2DL V3	1072	1000	1.9	575	879	2.00	86	F	S23	
SKiiP 1013 GB172-2DW V3	1072	1000	1.9	575	879	2.00	86	F	S23	
SKiiP 1203 GB172-2DL V3	1159	1200	1.9	575	961	2.00	86	F	S23	
SKiiP 1203 GB172-2DW V3	1159	1200	1.9	575	961	2.00	86	F	S23	
SKiiP 1513 GB172-3DL V3	1589	1500	1.9	863	1336	2.00	128	F,U	S33	
SKiiP 1513 GB172-3DW V3	1589	1500	1.9	863	1336	2.00	128	F,U	S33	
SKiiP 1803 GB172-3DL V3	1744	1800	1.9	863	1454	2.00	128	F,U	S33	
SKiiP 1803 GB172-3DW V3	1744	1800	1.9	863	1454	2.00	128	F,U	S33	
SKiiP 2013 GB172-4DL V3	2102	2000	1.9	1150	1758	2.00	171	F,U	S43	
SKiiP 2013 GB172-4DW V3	2102	2000	1.9	1150	1758	2.00	171	F,U	S43	
SKiiP 2403 GB172-4DL V3	2282	2400	1.9	1150	1921	2.00	171	F,U	S43	
SKiiP 2403 GB172-4DW V3	2282	2400	1.9	1150	1921	2.00	171	F,U	S43	
1700V - IGBT 4 (Trench) - SKiiP4										
SKiiP 1814 GB17E4-3DUL	2547	1800	2.12	2130	1771	2.02	498	F,S	S34	
SKiiP 1814 GB17E4-3DUW	2547	1800	2.12	2130	1771	2.02	498	F,S	S34	
SKiiP 2414 GB17E4-4DUL	3385	2400	2.12	2840	2362	2.02	664	F,S	S44	
SKiiP 2414 GB17E4-4DUW	3385	2400	2.12	2840	2362	2.02	664	F,S	S44	
SKiiP 3614 GB17E4-6DUL	5078	3600	2.12	6840	3547	2.02	996	F,S	S64	
SKiiP 3614 GB17E4-6DUW	5078	3600	2.12	6840	3547	2.02	996	F,S	S64	
SKiiP 3614 GB17E4-6DULR	5078	3600	2.12	6840	3547	2.02	996	F,S	S64	

IPM / SKiiP

SKiiP 3

Case S 23 mounted on P3016 heat sink



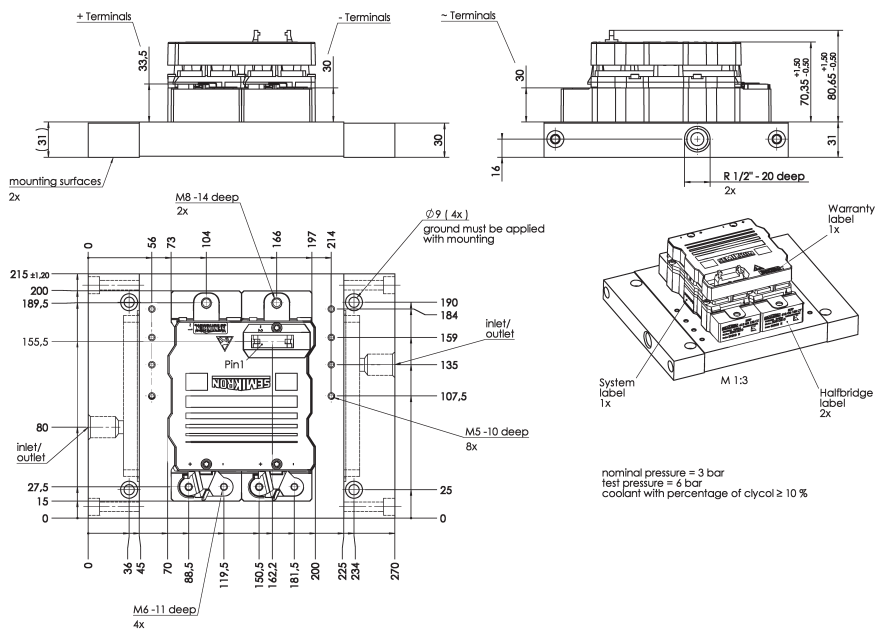
Weight without heat sink:

1,7 kg

P3016:

4,4 kg

Case S 23 mounted on liquid cooled heat sink NWK 40



NWK 40:

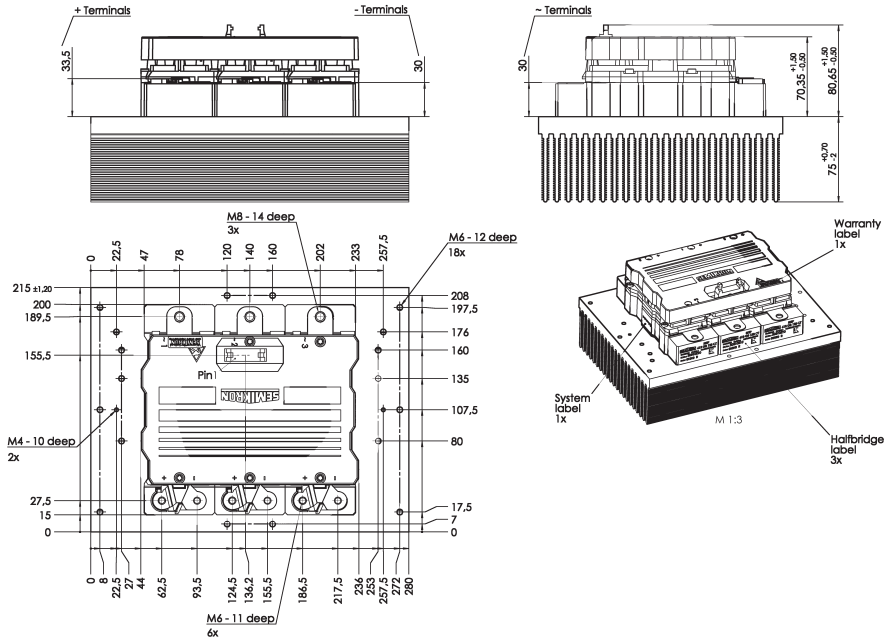
2,8 kg

Dimensions in mm

IPM / SKiP

SKiP 3

Case S 33 mounted on P3016 heat sink



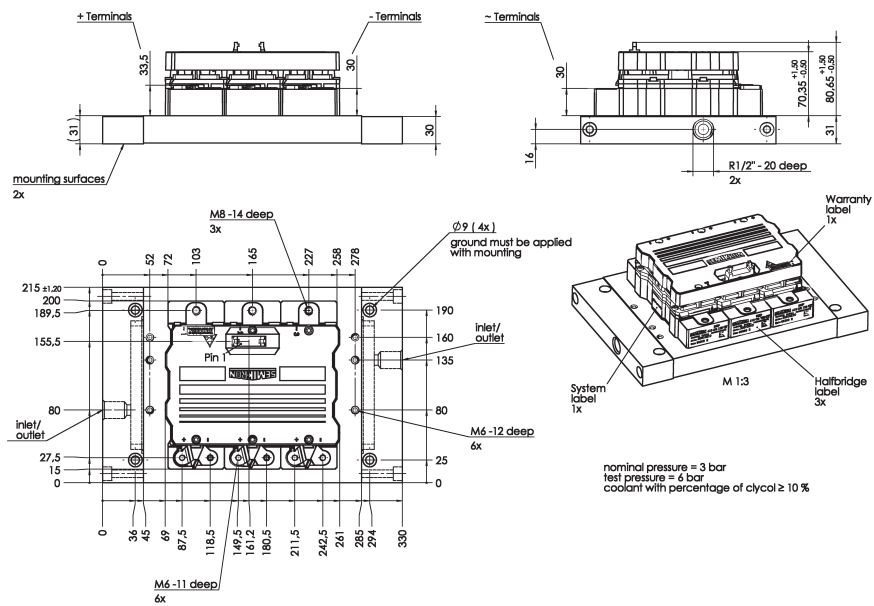
Weight without heat sink:

2,4 kg

P3016:

6,2 kg

Case S 33 mounted on liquid cooled heat sink NWK 40



NWK 40:

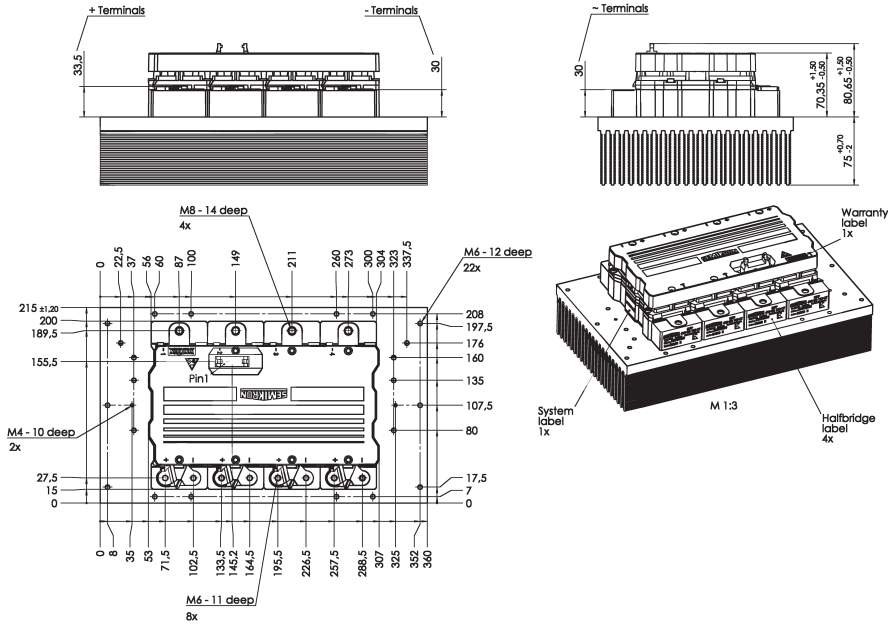
5,2 kg

Dimensions in mm

IPM / SKiP

SKiP 3

Case S 43 mounted on P3016 heat sink



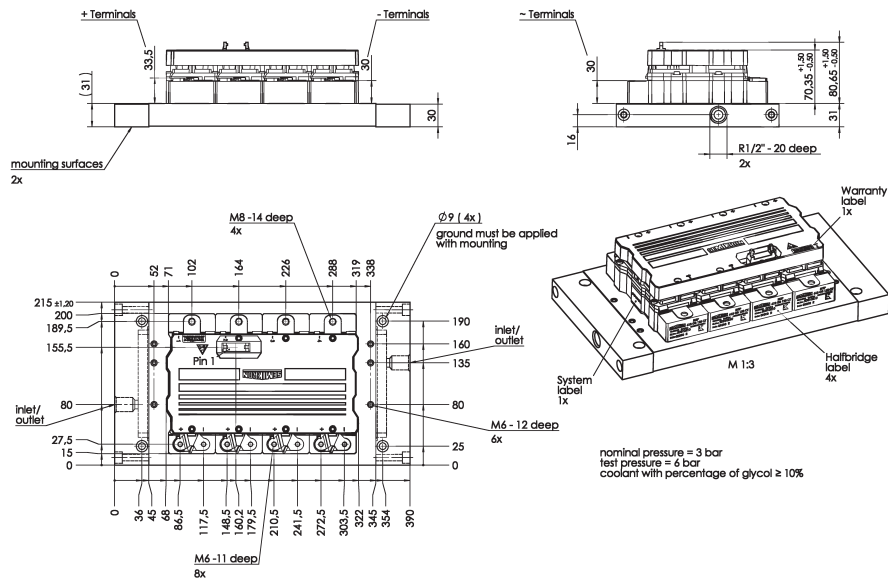
Weight without heat sink:

3,1 kg

P3016:

8,0 kg

Case S 43 mounted on liquid cooled heat sink NWK 40



NWK 40:

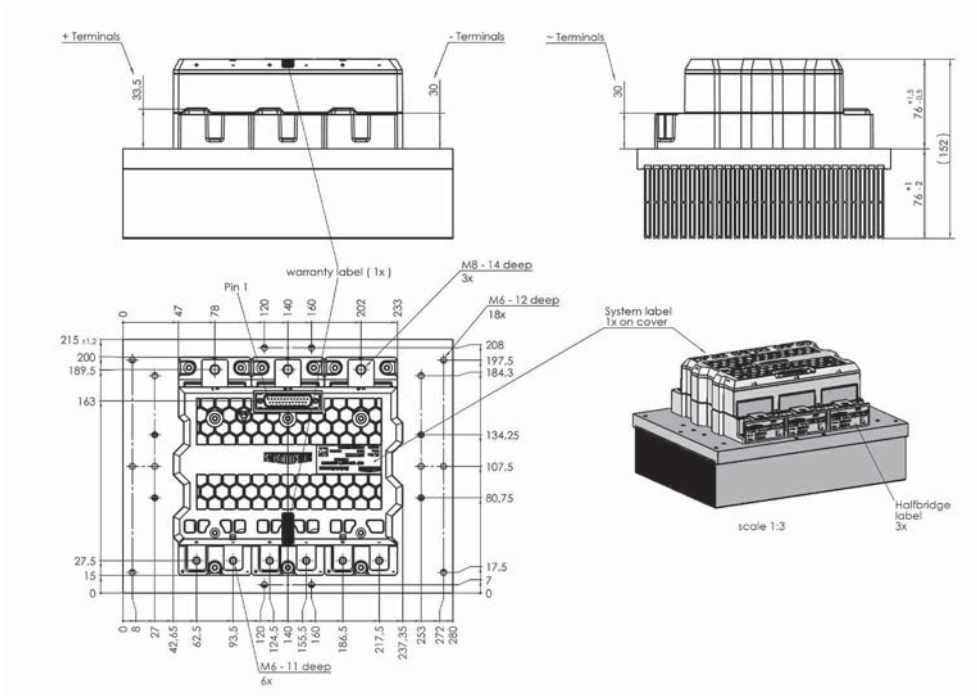
6,2 kg

Dimensions in mm

IPM / SKiP

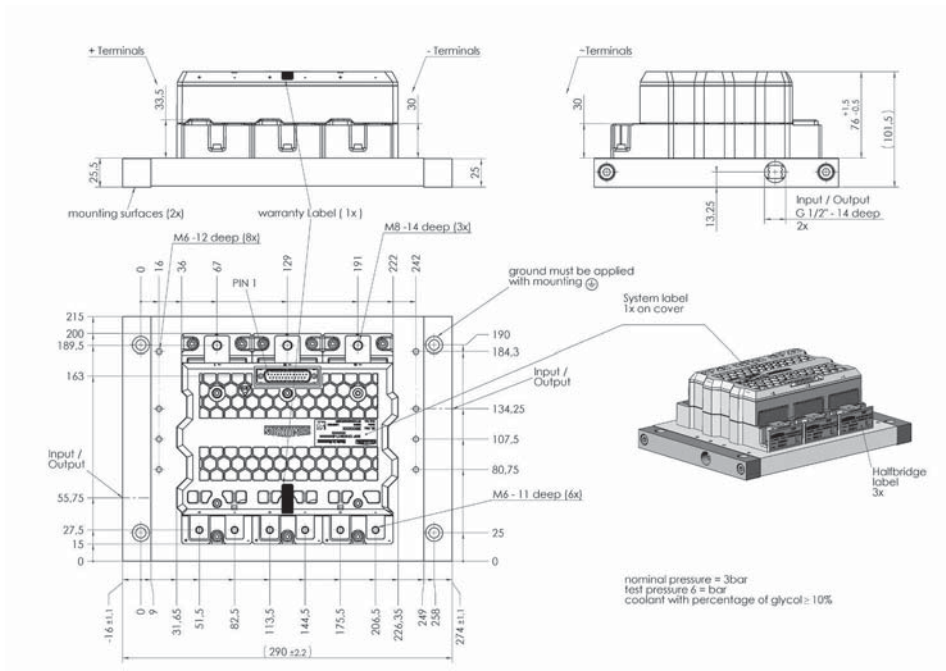
SKiP 4

Case S 34 mounted on P4016 heat sink



Weight without heat sink: 2,48 kg
 P4016: 5,9 kg

Case S 34 mounted on liquid cooled heat sink NHC



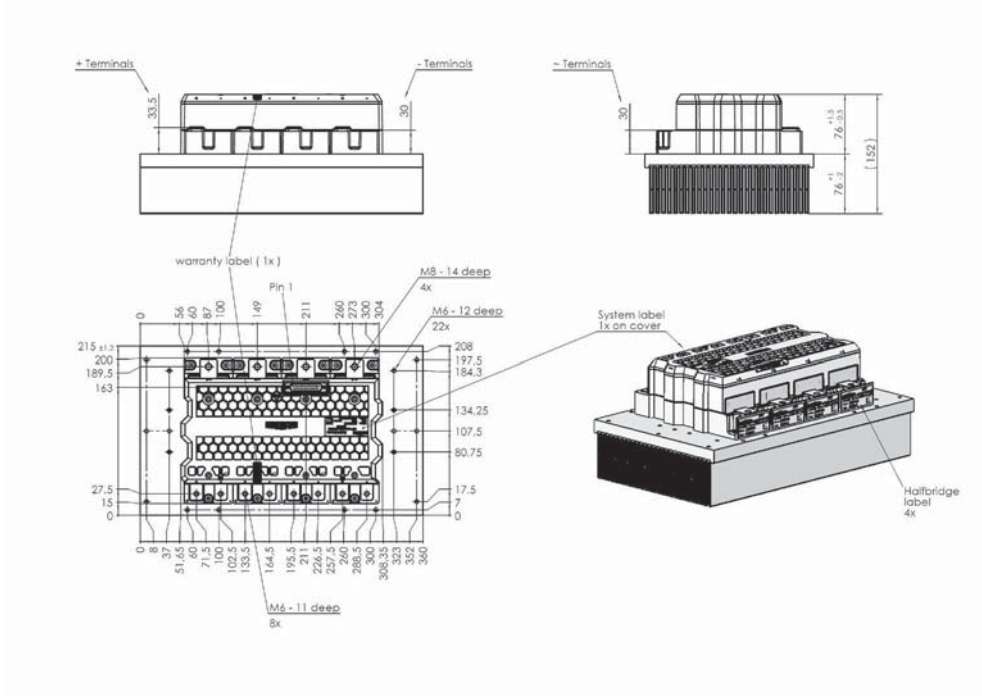
NHC: 3,49 kg

Dimensions in mm

IPM / SKiP

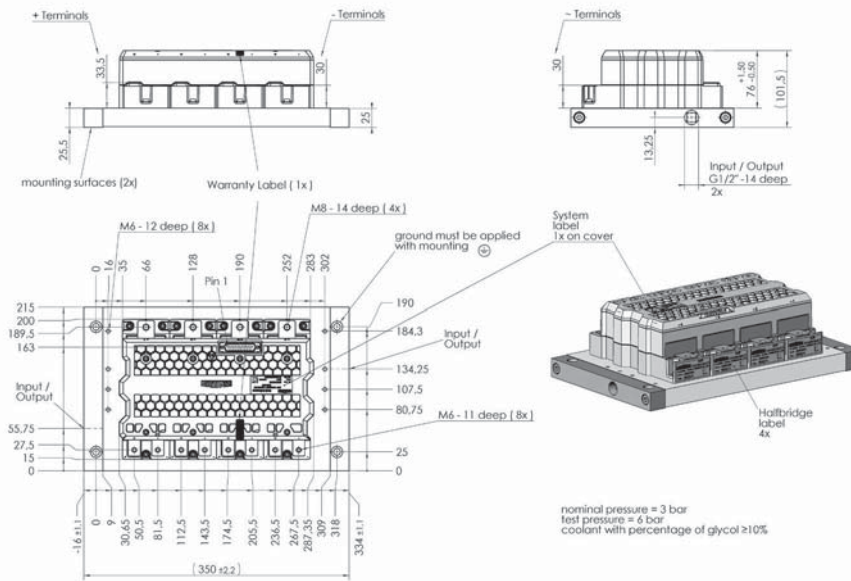
SKiP 4

Case S 44 mounted on P4016 heat sink



Weight without heat sink: 3,22 kg
 P4016: 7,55 kg

Case S 44 mounted on liquid cooled heat sink NHC



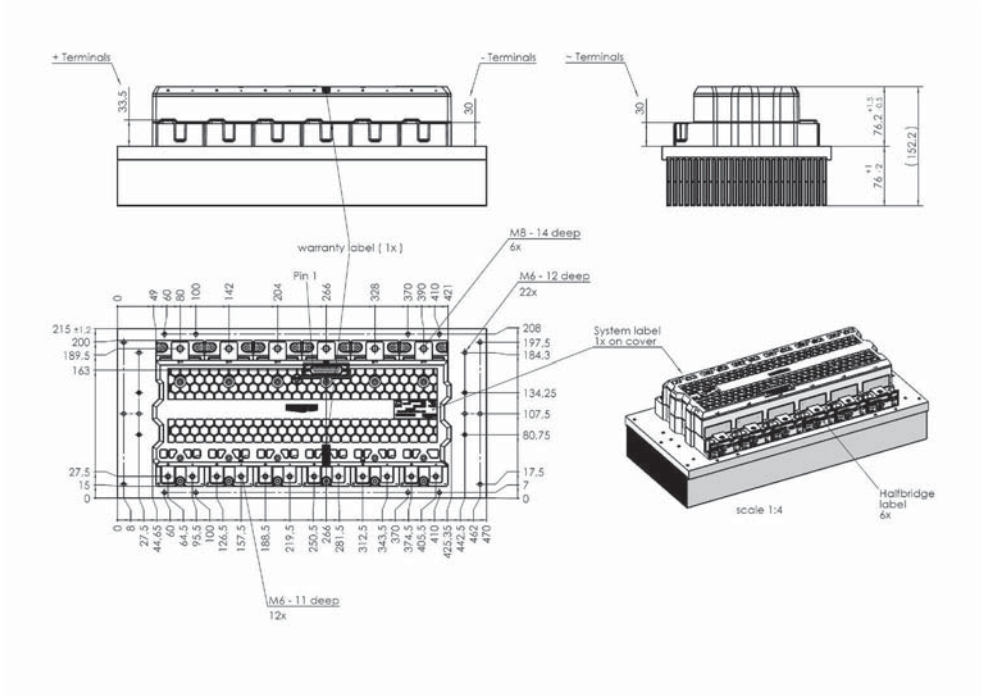
NHC: 4,25 kg

Dimensions in mm

IPM / SKiP

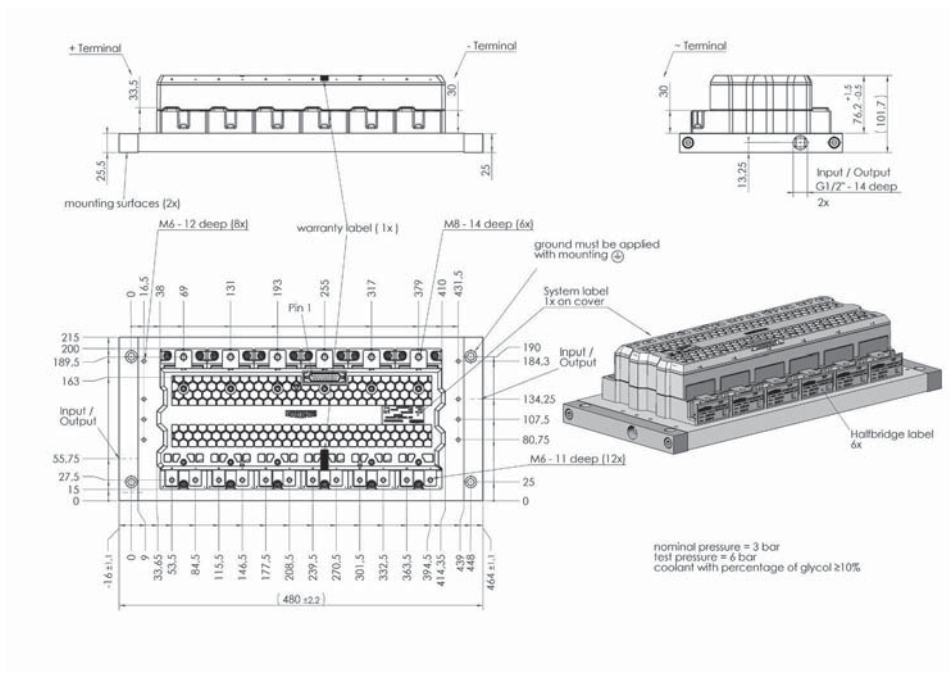
SKiP 4

Case S 64 mounted on P4016 heat sink



Weight without heat sink: 4,84 kg
 P4016: 9,9 kg

Case S 64 mounted on liquid cooled heat sink NHC



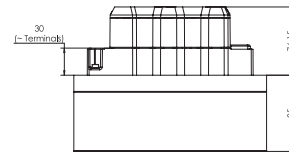
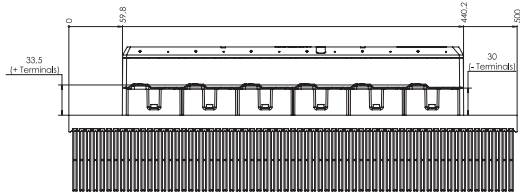
NHC: 5,77 kg

Dimensions in mm

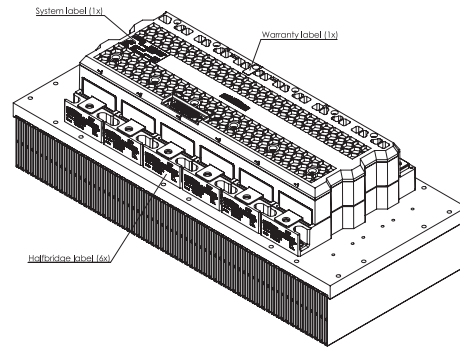
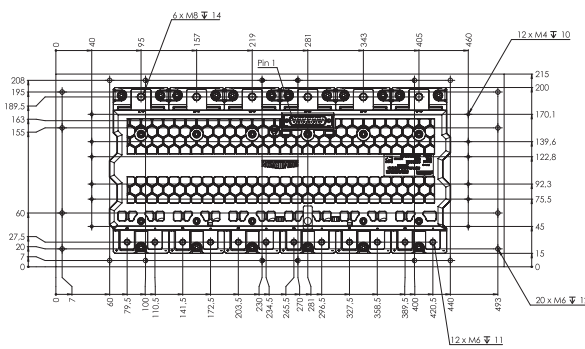
IPM / SKiiP

SKiiP 4

Case S 64 mounted on P4016 heat sink with 90° rotated fins



All dimensions in mm!



Weight without heat sink:

4,84 kg

P4016:

9,9 kg

Dimensions in mm

IPM / SKiiP Accessories

Type

F-Option SKiiP4

SKiiP4 F-Option	Fiber optic control board for SKiiP4
SKiiP4 F-Option with D-Sub connector	Fiber optic control board for SKiiP4

SKiiP3 Parallel Board

SKiiP3 Parallel Board 4-fold	Board for paralleling of 4 SKiiP3, F-Option usage possible
SKiiP3 Parallel Board 3-fold	Board for paralleling of 3 SKiiP3, F-Option usage possible
SKiiP3 Parallel Board 2-fold	Board for paralleling of 2 SKiiP3, F-Option usage possible

SKiiP 4 Parallel Board

SKiiP4 Parallel Board 4-fold without F-Option	Board for paralleling of 4 SKiiP4, F-Option usage not possible
SKiiP4 Parallel Board 4-fold F-Option	Board for paralleling of 4 SKiiP4, F-Option usage possible
SKiiP4 Parallel Board 3-fold without F-Option	Board for paralleling of 3 SKiiP4, F-Option usage not possible
SKiiP4 Parallel Board 3-fold F-Option	Board for paralleling of 3 SKiiP4, F-Option usage possible
SKiiP4 Parallel Board 2-fold without F-Option	Board for paralleling of 2 SKiiP4, F-Option usage not possible
SKiiP4 Parallel Board 2-fold F-Option	Board for paralleling of 2 SKiiP4, F-Option usage possible

SKiFace Adapter Board

SKiiP4 SKiFace Adapter UZK	Adapter board to connect SKiiP4 to SKiiP3 controller with DC-Link voltage measurement function
SKiiP4 SKiFace Adapter Temp	Adapter board to connect SKiiP4 to SKiiP3 controller with temperatur measurement function

SKiiP Accessories

SKiiP3 F-Option	Fiber optic control board for SKiiP3
------------------------	--------------------------------------

IGBT Driver

SEMIKRON IGBT Driver Family

SEMIKRON offers two different IGBT driver families for each application. Driver cores of the SKHI and SKYPER family can be optimized by using adapterboards to each module type. Driver like the SKYPER Prime offer a fully qualified Plug & Play solution saving time and costs in the application. The SKYPER family with 1W to 10W output power per channel, cover the whole range between 30kW and 2MW inverters. The high integration of SEMIKRON's new ASIC chipset provide for safe IGBT gate control over the whole lifecycle. Short circuits are managed very fast by separate error channels.

SoftOff and over voltage feedback avoid dangerous over voltages. The mixed signal ASICs guarantee lowest tolerances over the full temperature range. MLI or paralleled IGBT topologies are managed by the adjustable error handling. With an optimized interface and the adjustable filter setting the SKYPER family operates safely in noisy environments. The SEMIKRON's adapter boards allow to build up fast a broad range of inverter platforms based on various different types of IGBT modules.

Product	Page
SKYPER & SKHI	132

▶ For detailed information please refer data sheets.

Further information:
www.semikron.com/driver

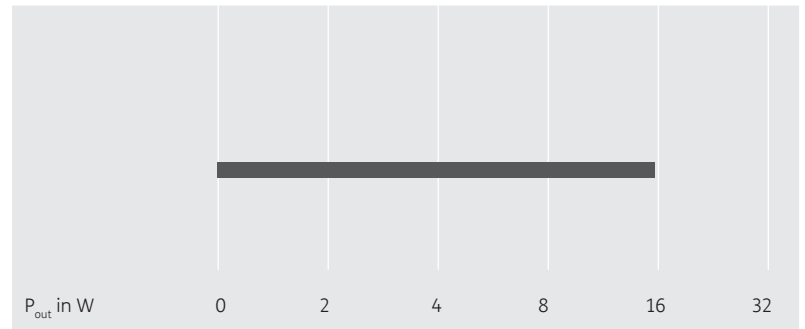
IGBT Driver

SKYPER®

Driver



600V up to 1700V

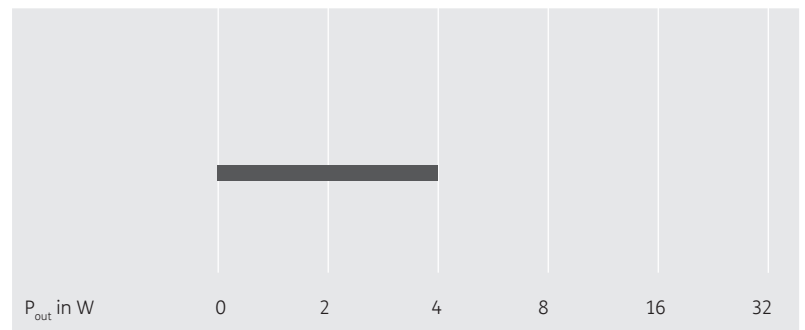


SKYPER® & SKHI

Driver Cores

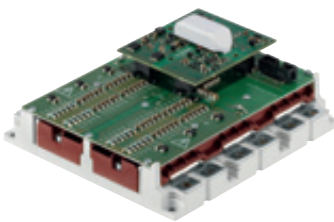


900V up to 1700V

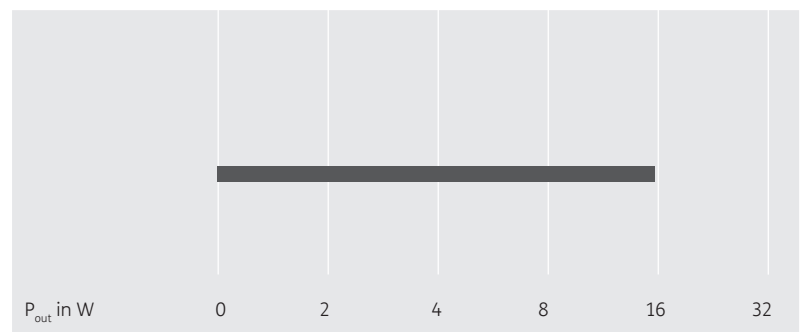


SKYPER® & SKHI

Adapterboards



1200V up to 1700V



IGBT Driver

Type

	Channels	V_{CE} V	$V_{G(on)}$ V	$V_{G(off)}$ V	$I_{outPEAK}$ A	$Q_{out/pulse}$ μC	f_{max} kHz	V_{sollO} kV	dv/dt kV/ μs
Driver									
SKHI 10/12 R	1	1200	15	-8	8	9.6	100	2500	75
SKHI 10/17 R	1	1700	15	-8	8	9.6	100	4000	75
SKHI 23/12 R	2	1200	15	-8	8	4.8	100	2500	75
SKHI 23/17 R	2	1700	15	-8	8	4.8	100	4000	75
SKHIT 01 R ⁵⁾	3	528	-	-	-	-	10	2500	-
SKYPER 12 press-fit 300 A	2	1700	15	-9	14	6	20	4000	50
SKYPER 12 press-fit 450A	2	1700	15	-9	14	6	13	4000	50
SKYPER 12 press-fit 600A	2	1700	15	-9	14	6	10	4000	50
SKYPER 12 press-fit C 300 A	2	1700	15	-9	14	6	20	4000	50
SKYPER 12 press-fit C 450A	2	1700	15	-9	14	6	13	4000	50
SKYPER 12 press-fit C 600A	2	1700	15	-9	14	6	10	4000	50
SKYPER PRIME 1000A	2	1700	15	-9	14	17	10	4000	50
Driver Core									
SKHI 21A R ⁶⁾	2	1200	15	0	8	4	50	2500	50
SKHI 22 A/B H4 R	2	1700	15	-7	8	4	50	4000	50
SKHI 22 A/B R	2	1200	15	-7	8	4	50	2500	50
SKHI 24 R	2	1700	15	-8	15	5	50	4000	50
SKYPER 32 R	2	1700	15	-7	15	2.5	50	4000	50
SKYPER 32 PRO R	2	1700	15	-7	15	6.3	50	4000	50
SKYPER 42 R	2	1700	15	-8	30	50	100	4000	100
SKYPER 42 LJ R	2	1700	14.8	-8	20	20	100	4000	100
SKHI 61 R	6	900	14.9	-6.5	2	1	50	2500	15
SKHI 71 R	7	900	14.9	-6.5	2	1	50	2500	15
Adapter Board									
Board 1 SKYPER 32 R	2	1700	15	-7	15	2.5	50	4000	50
Board 1 SKYPER 32PRO R	2	1700	15	-7	15	6.3	50	4000	50
Board 2 // 4S SKYPER 42 R	2	1200	15	-8	30	50	100	4000	100
Board 2 generic SKYPER 42 R	2	1700	15	-8	30	50	100	4000	100
Board 2//3S SKYPER 42 R	2	1700	15	-8	30	50	100	4000	100
Board 2S SKYPER 32 PRO R Gold	2	1700	15	-7	15	6.3	50	4000	50
Board 2S SKYPER 32 R Gold	2	1700	15	-7	15	2.5	50	4000	50
Board 3S SKYPER 32 PRO R Gold	2	1700	15	-7	15	6.3	50	4000	50
Board 3S SKYPER 32 R Gold	2	1700	15	-7	15	2.5	50	4000	50
Board 4S SKYPER 32 PRO R Gold	2	1700	15	-7	15	6.3	50	4000	50
Board 4S SKYPER 32 R Gold	2	1700	15	-7	15	2.5	50	4000	50
Board 63 GB SKYPER 42 R	2	1700	15	-8	30	50	100	4000	100
Board 93 GB SKYPER 42 R	2	1700	15	-8	30	50	100	4000	100

Footnotes: 5) Thyristor Driver / 6) MOSFET Driver

Stacks

Fully Qualified Inverter Assemblies Tailored to Your Specific Needs

In addition to standard semiconductor components, SEMIKRON has developed a full range of power converter assemblies.

Solution center application engineers are available to offer specific power solutions by adapting present platforms or by designing fully customized converters.

Product	Page
Water cooled	
SEMISTACK RE	136
SKiiPRACK	138
Air cooled	
SEMIKUBE	139
SEMIKUBE SlimLine	140
SEMISTACK CLASSICS	141

▶ For detailed information
please refer data sheets.

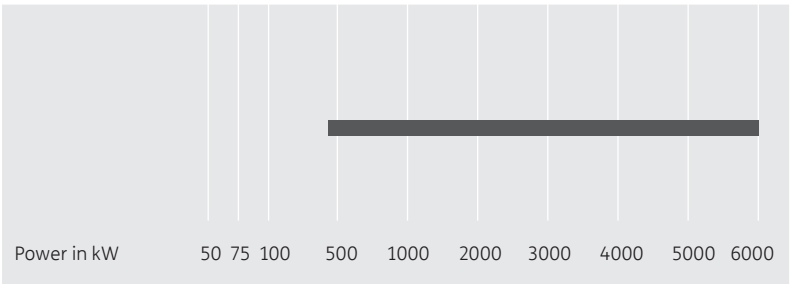
Further information:
www.semikron.com/stacks

Stacks

Water cooled

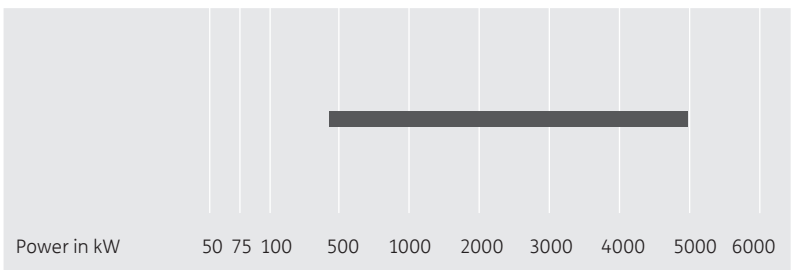
SEMISTACK®RE

Synchronous wind generators
Double-fed wind generators
Solar inverters



SKiiPRACK®

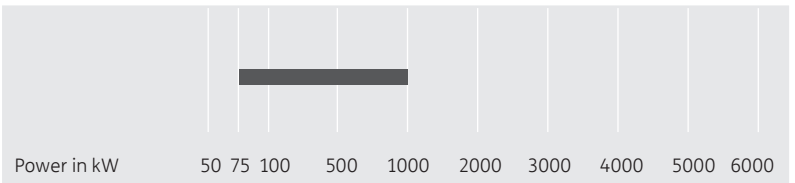
Synchronous wind generators
Double-fed wind generators
High power AC drives



Air cooled

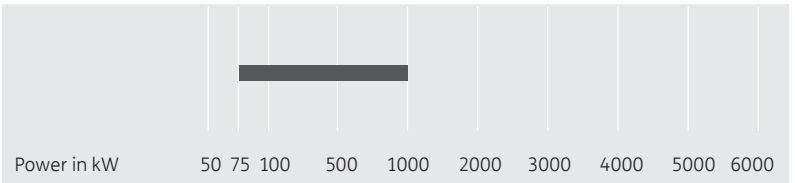
SEMIKUBE®

Solar inverters
Pump and compressor drives



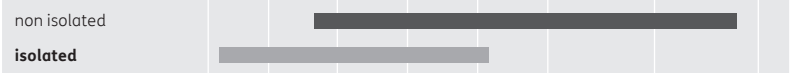
SEMIKUBE® SlimLine

Solar inverters
AC drives and servos

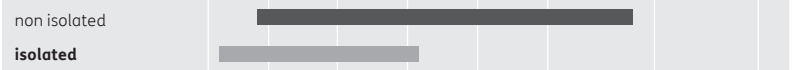


SEMISTACK®CLASSICS

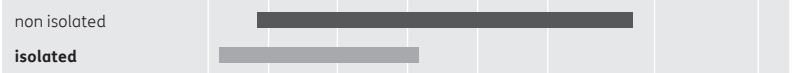
B6U
3-phase uncontrolled rectifier



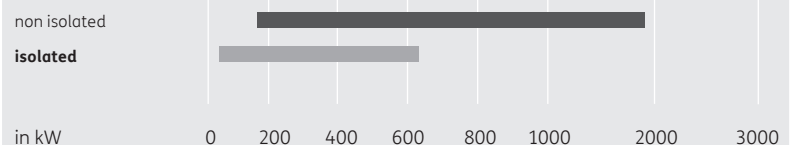
B6HK
3-phase half controlled rectifier



B6C
3-phase fully controlled rectifier

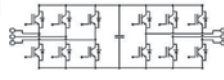
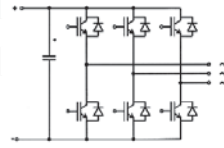


W3C
3-phase reverse parallel thyristor converter



Stacks / SEMISTACK RE

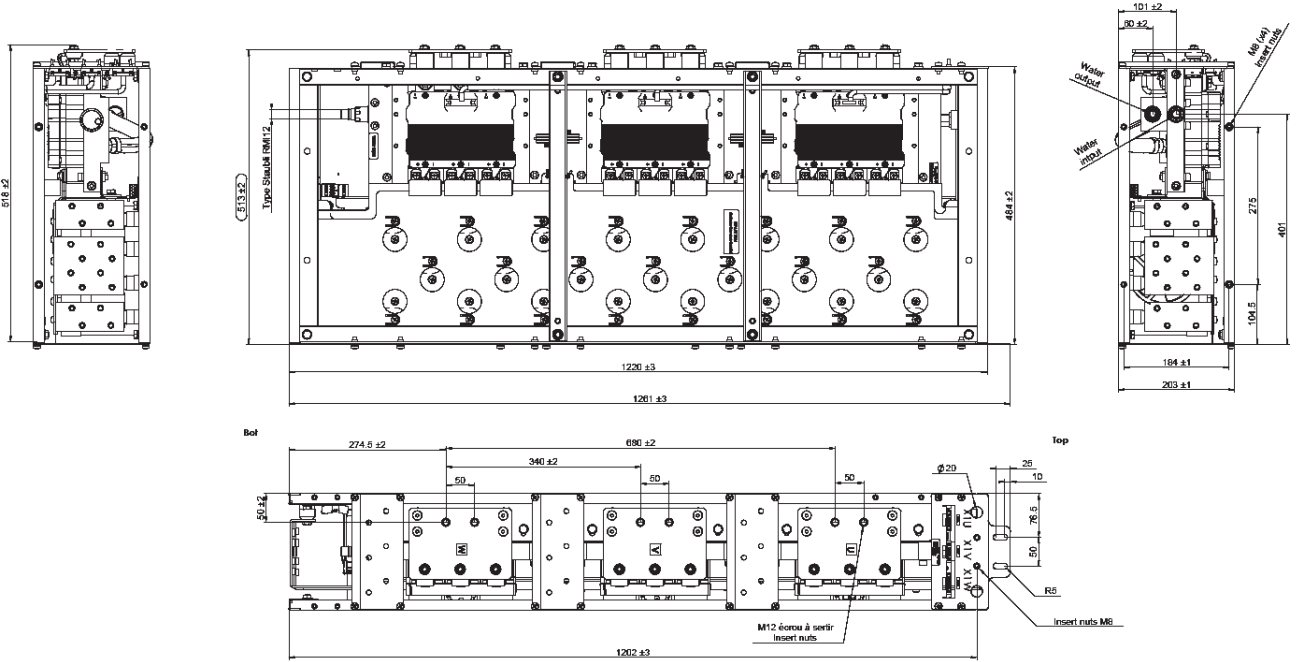
Type

	V _{Ac} V	V _{Dc} V	Current A	Component Family	Cooling	Heatsink profile	Isolated	Circuit
4-Quadrant converter								
SKS B2 120 GDD 69/11 - A11 MA PB	690	1100	1200	SKiiP 3	Water/Glycol	-	yes	
SKS B2 140 GDD 69/12 U - A11 MA PB	690	1250	1400	SKiiP 4	Water/Glycol	-	yes	
3-phase inverter								
SKS B1 090 GD 69/11 - MA PB	690	1100	900	SKiiP 3	Water/Glycol	-	yes	
SKS B2 100 GD 69/11 - MA PB	690	1100	1000	SKiiP 3	Water/Glycol	-	yes	
SKS B2 120 GD 69/11 - MA PB	690	1100	1200	SKiiP 3	Water/Glycol	-	yes	
SKS B2 140 GD 69/12 U - MA PB	690	1250	1400	SKiiP 4	Water/Glycol	-	yes	

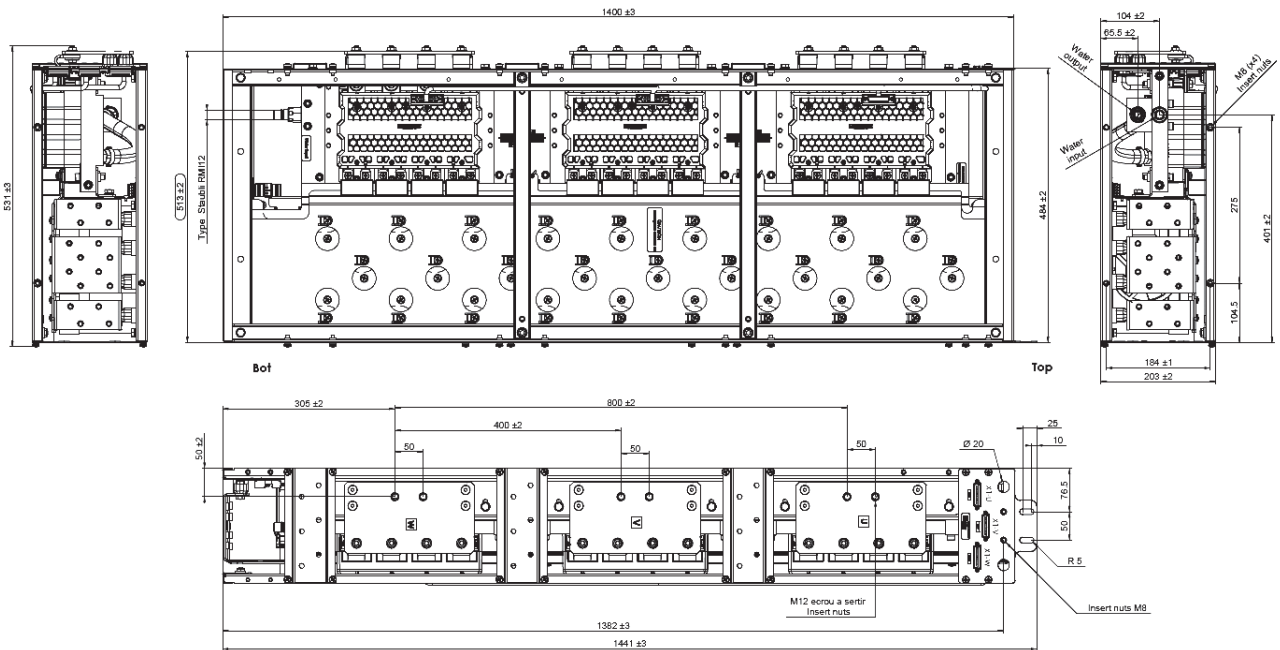
Stacks / SEMISTACK RE

Cases

SKS B1 090 GD 69/11 - MA PB



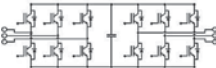
SKS B2 100 GD 69/11 - MA PB, SKS B2 120 GD 69/11 - MA PB, and SKS B2 140 GD 69/12 - MA PB



Dimensions in mm

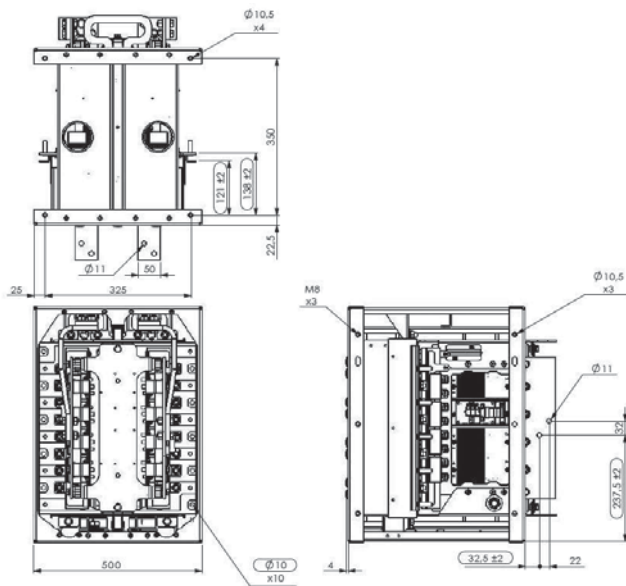
Stacks / SKiiPRACK

Type

	V _{Ac} V	V _{Dc} V	Current A	Component Family	Cooling	Heatsink profile	Isolated	Circuit
4-Quadrant converter								
SKS C 120 GDD 69/11 - A3A WA B1B	690	1100	1200	SKiiP 3	Water/Glycol	-	yes	
SKS C 240 GDD 69/11 - A6A MA B1C	690	1100	2400	SKiiP 3	Water/Glycol	-	yes	

Cases

SKiiPRACK basic stack element, the CELL



3-Cell vertical integration



8

Dimensions in mm

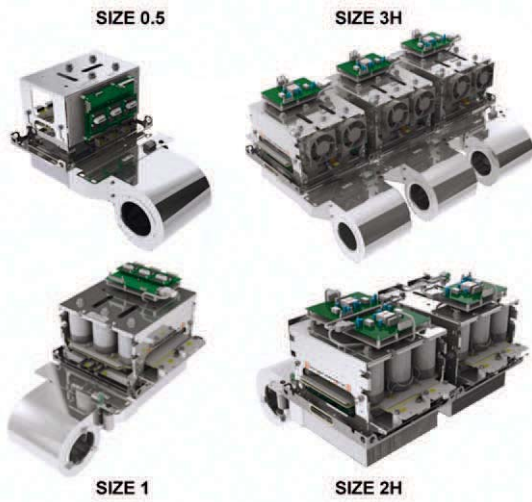
Stacks / SEMIKUBE

Type

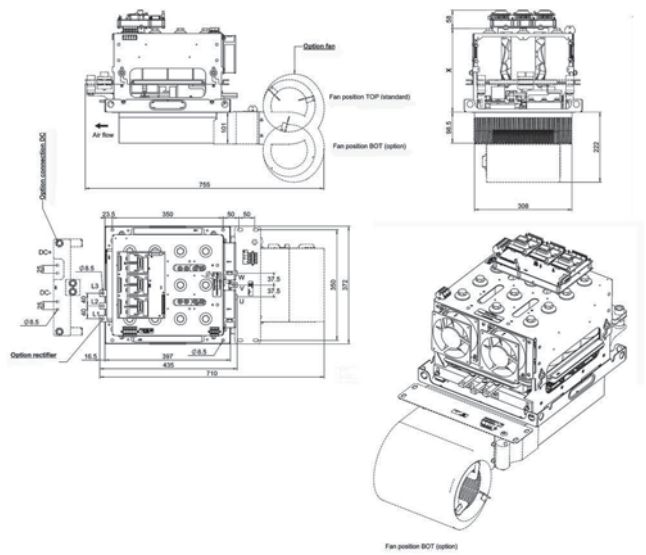
	V _{Ac} V	V _{Dc} V	Current A	Component Family	Cooling	Heatsink profile	Isolated	Circuit
3-phase inverter								
IGD-1-424-P1N4-DL-FA	460	750	200	SEMITRANS	Forced-air cooled	PX 308	yes	
IGD-2-424-P1N6-DH-FA	460	750	350	SEMITRANS	Forced-air cooled	PX 308	yes	
IGD-4-424-P1F7-BL-FA	460	750	750	SEMITRANS	Forced-air cooled	PX 308	yes	
IGD-8-326-E1F12-BH-FA	460	750	1230	SEMITRANS	Forced-air cooled	PX 308	yes	
IGD-8-426-E1F12-BH-FA	460	750	1470	SEMITRANS	Forced-air cooled	PX 308	yes	
IGD-8-424-P1F9-BH-FA	460	750	1470	SEMITRANS	Forced-air cooled	PX 308	yes	
3-phase rectifier and inverter								
IGDD6-1-326-D1616-E1N6-DL-FA	460	750	150	SEMITRANS/SEMIPACK	Forced-air cooled	PX 308	yes	
IGDD6-1-426-D1616-E1N6-DL-FA	460	750	180	SEMITRANS/SEMIPACK	Forced-air cooled	PX 308	yes	
IGDD6-2-326-D1616-E1F12-DH-FA	460	750	280	SEMITRANS/SEMIPACK	Forced-air cooled	PX 308	yes	
IGDD6-2-426-D1616-E1F12-DH-FA	460	750	330	SEMITRANS/SEMIPACK	Forced-air cooled	PX 308	yes	
IGDD6-4-326-D3816-E1F12-BL-FA	460	750	570	SEMITRANS/SEMIPACK	Forced-air cooled	PX 308	yes	
IGDD6-4-426-D3816-E1F12-BL-FA	460	750	680	SEMITRANS/SEMIPACK	Forced-air cooled	PX 308	yes	

Cases

Frames



Size 1



Dimensions in mm

Stacks / SEMIKUBE SlimLine

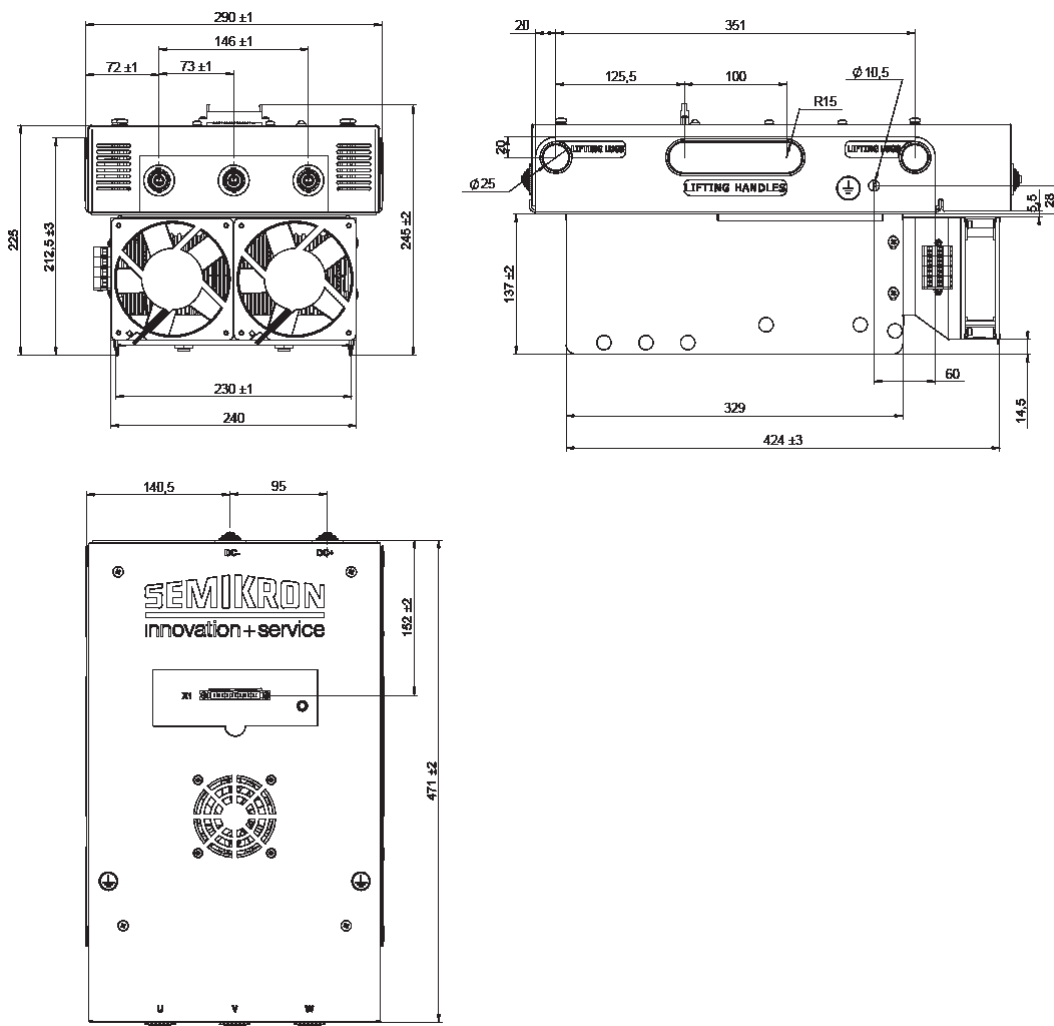
Type

	V _{AC} V	V _{DC} V	Current A	Component Family	Cooling	Frame	Isolated	Circuit
3-phase inverter								
SKS SL 20 GD 50/10 - C E4 P1 AF ¹⁾	500	1000	230	SEMITRANS	Forced-air cooled	SL20	yes	
SKS SL 40 GD 50/10 - C E4 P1 AF ¹⁾	500	1000	440	SEMITRANS	Forced-air cooled	SL40	yes	
SKS SL 80 GD 50/10 - C E4 P1 AF ¹⁾	500	1000	750	SEMITRANS	Forced-air cooled	SL80	yes	
SKS SL 150 GD 50/10 - C E4 P1 AF ¹⁾	500	1000	1500	SEMITRANS	Forced-air cooled	SL150	yes	

Footnotes: 1) New product

Cases

Frame SL20



Dimensions in mm

Stacks / SEMISTACK CLASSICS

Type

	V _{Ac} V	V _{Dc} V	DC Current A	Component Family	Cooling	Heatsink profile	Isolated	Circuit
3-phase fully-controlled thyristor bridge rectifier								
SKS 88N B6C 60 V16	500	670	88	SEMIPACK 1	Natural cooled	P3/180	yes	
SKS 88N B6C 60 V16 SU	500	670	88	SEMIPACK 1	Natural cooled	P3/180	yes	
SKS 180F B6C 120 V16	500	670	180	SEMIPACK 1	Forced-air cooled	P3/180	yes	
SKS 180F B6C 120 V16 SU	500	670	180	SEMIPACK 1	Forced-air cooled	P3/180	yes	
SKS 215N B6C 145 V16	500	670	215	Stud devices	Natural cooled	P1/150	no	
SKS 215N B6C 145 V16 SU	500	670	215	Stud devices	Natural cooled	P1/150	no	
SKS 250F B6C 170 V16	500	670	250	SEMIPACK 2	Forced-air cooled	P3/265	yes	
SKS 250F B6C 170 V16 SU	500	670	250	SEMIPACK 2	Forced-air cooled	P3/265	yes	
SKS 355N B6C 240 V16	500	670	355	Stud devices	Natural cooled	P1/200	no	
SKS 355N B6C 240 V16 SU	500	670	355	Stud devices	Natural cooled	P1/200	no	
SKS 365F B6C 245 V16	500	670	365	SEMIPACK 2	Forced-air cooled	P16/200	yes	
SKS 365F B6C 245 V16 SU	500	670	365	SEMIPACK 2	Forced-air cooled	P16/200	yes	
SKS 570F B6C 380 V16	500	670	570	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 570F B6C 380 V16 SU	500	670	570	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 640F B6C 430 V16	500	670	640	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 640F B6C 430 V16 SU	500	670	640	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 700N B6C 470 V16	500	670	700	Capsules	Natural cooled	P11/415	no	
SKS 700N B6C 470 V16 SU	500	670	700	Capsules	Natural cooled	P11/415	no	
SKS 845N B6C 570 V16	500	670	845	Capsules	Natural cooled	U3/515	no	
SKS 845N B6C 570 V16 SU	500	670	845	Capsules	Natural cooled	U3/515	no	
SKS 970F B6C 650 V16	500	670	970	SEMIPACK 5	Forced-air cooled	P16/300	yes	
SKS 970F B6C 650 V16 SU	500	670	970	SEMIPACK 5	Forced-air cooled	P16/300	yes	
SKS 1000N B6C 670 V16	500	670	1000	Capsules	Natural cooled	U3/515	no	
SKS 1000N B6C 670 V16 SU	500	670	1000	Capsules	Natural cooled	U3/515	no	
SKS 1200F B6C 800 V16	500	670	1200	Capsules	Forced-air cooled	P17/130	no	
SKS 1200F B6C 800 V16 SU	500	670	1200	Capsules	Forced-air cooled	P17/130	no	
SKS 1500F B6C 1010 V16	500	670	1500	Capsules	Forced-air cooled	P17/130	no	
SKS 1500F B6C 1010 V16 SU	500	670	1500	Capsules	Forced-air cooled	P17/130	no	
SKS 1890F B6C 1270 V16	500	670	1890	Capsules	Forced-air cooled	P18/180	no	
SKS 1890F B6C 1270 V16 ZU	500	670	1890	Capsules	Forced-air cooled	P18/180	no	
SKS 2580F B6C 1730 V16	500	670	2580	Capsules	Forced-air cooled	N4/250	no	
SKS 2580F B6C 1730 V16 ZU	500	670	2580	Capsules	Forced-air cooled	N4/250	no	
3-phase half-controlled bridge rectifier								
SKS 88N B6HK 60 V16	500	670	88	SEMIPACK 1	Natural cooled	P3/180	yes	
SKS 88N B6HK 60 V16 SU	500	670	88	SEMIPACK 1	Natural cooled	P3/180	yes	
SKS 180F B6HK 120 V16	500	670	180	SEMIPACK 1	Forced-air cooled	P3/180	yes	
SKS 180F B6HK 120 V16 SU	500	670	180	SEMIPACK 1	Forced-air cooled	P3/180	yes	
SKS 215N B6HK 145 V16	500	670	215	Stud devices	Natural cooled	P1/150	no	
SKS 215N B6HK 145 V16 SU	500	670	215	Stud devices	Natural cooled	P1/150	no	
SKS 250F B6HK 170 V16	500	670	250	SEMIPACK 2	Forced-air cooled	P3/265	yes	
SKS 250F B6HK 170 V16 SU	500	670	250	SEMIPACK 2	Forced-air cooled	P3/265	yes	
SKS 355N B6HK 240 V16	500	670	355	Stud devices	Natural cooled	P1/200	no	
SKS 355N B6HK 240 V16 SU	500	670	355	Stud devices	Natural cooled	P1/200	no	
SKS 365F B6HK 245 V16	500	670	365	SEMIPACK 2	Forced-air cooled	P16/200	yes	
SKS 365F B6HK 245 V16 SU	500	670	365	SEMIPACK 2	Forced-air cooled	P16/200	yes	
SKS 570F B6HK 380 V16	500	670	570	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 570F B6HK 380 V16 SU	500	670	570	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 640F B6HK 430 V16	500	670	640	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 640F B6HK 430 V16 SU	500	670	640	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 700N B6HK 470 V16	500	670	700	Capsules	Natural cooled	P11/415	no	
SKS 700N B6HK 470 V16 SU	500	670	700	Capsules	Natural cooled	P11/415	no	
SKS 845N B6HK 570 V16	500	670	845	Capsules	Natural cooled	U3/515	no	
SKS 845N B6HK 570 V16 SU	500	670	845	Capsules	Natural cooled	U3/515	no	
SKS 970F B6HK 650 V16	500	670	970	SEMIPACK 5	Forced-air cooled	P16/300	yes	
SKS 970F B6HK 650 V16 SU	500	670	970	SEMIPACK 5	Forced-air cooled	P16/300	yes	
SKS 1000N B6HK 670 V16	500	670	1000	Capsules	Natural cooled	U3/515	no	

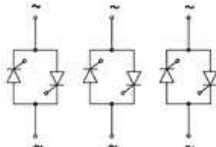
Stacks / SEMISTACK CLASSICS

Type

	V _{Ac} V	V _{Dc} V	DC Current A	Component Family	Cooling	Heatsink profile	Isolated	Circuit
3-phase half-controlled bridge rectifier								
SKS 1000N B6HK 670 V16 SU	500	670	1000	Capsules	Natural cooled	U3/515	no	
SKS 1200F B6HK 800 V16	500	670	1200	Capsules	Forced-air cooled	P17/130	no	
SKS 1200F B6HK 800 V16 SU	500	670	1200	Capsules	Forced-air cooled	P17/130	no	
SKS 1500F B6HK 1010 V16	500	670	1500	Capsules	Forced-air cooled	P17/130	no	
SKS 1500F B6HK 1010 V16 SU	500	670	1500	Capsules	Forced-air cooled	P17/130	no	
SKS 1890F B6HK 1270 V16	500	670	1890	Capsules	Forced-air cooled	P18/180	no	
SKS 1890F B6HK 1270 V16 ZU	500	670	1890	Capsules	Forced-air cooled	P18/180	no	
SKS 2580F B6HK 1730 V16	500	670	2580	Capsules	Forced-air cooled	N4/250	no	
SKS 2580F B6HK 1730 V16 ZU	500	670	2580	Capsules	Forced-air cooled	N4/250	no	
3-phase uncontrolled bridge rectifier								
SKS 91N B6U 60 V16	500	670	91	SEMIPACK 1	Natural cooled	P3/180	yes	
SKS 91N B6U 60 V16 SU	500	670	91	SEMIPACK 1	Natural cooled	P3/180	yes	
SKS 185F B6U 125 V16	500	670	185	SEMIPACK 1	Forced-air cooled	P3/180	yes	
SKS 185F B6U 125 V16 SU	500	670	185	SEMIPACK 1	Forced-air cooled	P3/180	yes	
SKS 290F B6U 195 V16	500	670	290	SEMIPACK 2	Forced-air cooled	P3/265	yes	
SKS 290F B6U 195 V16 SU	500	670	290	SEMIPACK 2	Forced-air cooled	P3/265	yes	
SKS 425N B6U 285 V16	500	670	425	Stud devices	Natural cooled	P1/150	no	
SKS 425N B6U 285 V16 SU	500	670	425	Stud devices	Natural cooled	P1/150	no	
SKS 430F B6U 290 V16	500	670	430	SEMIPACK 2	Forced-air cooled	P16/200	yes	
SKS 430F B6U 290 V16 SU	500	670	430	SEMIPACK 2	Forced-air cooled	P16/200	yes	
SKS 535N B6U 360 V16	500	670	535	Stud devices	Natural cooled	P1/200	no	
SKS 535N B6U 360 V16 SU	500	670	535	Stud devices	Natural cooled	P1/200	no	
SKS 660F B6U 440 V16	500	670	660	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 660F B6U 440 V16 SU	500	670	660	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 850F B6U 570 V16	500	670	850	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 850F B6U 570 V16 SU	500	670	850	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 1185N B6U 795 V16	500	670	1185	Capsules	Natural cooled	P11/415	no	
SKS 1185N B6U 795 V16 SU	500	670	1185	Capsules	Natural cooled	P11/415	no	
SKS 1220F B6U 820 V16	500	670	1220	SEMIPACK 5	Forced-air cooled	P16/300	yes	
SKS 1220F B6U 820 V16 SU	500	670	1220	SEMIPACK 5	Forced-air cooled	P16/300	yes	
SKS 1630N B6U 1090 V16	500	670	1630	Capsules	Natural cooled	U3/515	no	
SKS 1630N B6U 1090 V16 ZU	500	670	1630	Capsules	Natural cooled	U3/515	no	
SKS 1910N B6U 1280 V16	500	670	1910	Capsules	Natural cooled	U3/515	no	
SKS 1910N B6U 1280 V16 ZU	500	670	1910	Capsules	Natural cooled	U3/515	no	
SKS 1950F B6U 1305 V16	500	670	1950	Capsules	Forced-air cooled	P17/130	no	
SKS 1950F B6U 1305 V16 ZU	500	670	1950	Capsules	Forced-air cooled	P17/130	no	
SKS 2300F B6U 1540 V16	500	670	2300	Capsules	Forced-air cooled	P18/180	no	
SKS 2300F B6U 1540 V16 ZU	500	670	2300	Capsules	Forced-air cooled	P18/180	no	
SKS 4015F B6U 2690 V16	500	670	4015	Capsules	Forced-air cooled	N4/250	no	

Stacks / SEMISTACK CLASSICS

Type

	V _{Ac} V	V _{Dc} V	DC Current A	Component Family	Cooling	Heatsink profile	Isolated	Circuit
3-phase reverse parallel thyristor converter								
SKS 67N W3C 60 V16	500	-	67	SEMIPACK 1	Natural cooled	P3/180	yes	
SKS 67N W3C 60 V16 SU	500	-	67	SEMIPACK 1	Natural cooled	P3/180	yes	
SKS 140F W3C 120 V16	500	-	140	SEMIPACK 1	Forced-air cooled	P3/180	yes	
SKS 140F W3C 120 V16 SU	500	-	140	SEMIPACK 1	Forced-air cooled	P3/180	yes	
SKS 170N W3C 150 V16	500	-	170	Stud devices	Natural cooled	P1/150	no	
SKS 170N W3C 150 V16 SU	500	-	170	Stud devices	Natural cooled	P1/150	no	
SKS 195F W3C 170 V16	500	-	195	SEMIPACK 2	Forced-air cooled	P3/265	yes	
SKS 195F W3C 170 V16 SU	500	-	195	SEMIPACK 2	Forced-air cooled	P3/265	yes	
SKS 275N W3C 240 V16	500	-	275	Stud devices	Natural cooled	P1/200	no	
SKS 275N W3C 240 V16 SU	500	-	275	Stud devices	Natural cooled	P1/200	no	
SKS 290F W3C 250 V16	500	-	290	SEMIPACK 2	Forced-air cooled	P16/200	yes	
SKS 290F W3C 250 V16 SU	500	-	290	SEMIPACK 2	Forced-air cooled	P16/200	yes	
SKS 450F W3C 390 V16	500	-	450	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 450F W3C 390 V16 SU	500	-	450	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 520F W3C 450 V16	500	-	520	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 520F W3C 450 V16 SU	500	-	520	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 545N W3C 470 V16	500	-	545	Capsules	Natural cooled	P11/415	no	
SKS 545N W3C 470 V16 SU	500	-	545	Capsules	Natural cooled	P11/415	no	
SKS 650N W3C 560 V16	500	-	650	Capsules	Natural cooled	U3/515	no	
SKS 650N W3C 560 V16 SU	500	-	650	Capsules	Natural cooled	U3/515	no	
SKS 760F W3C 660 V16	500	-	760	SEMIPACK 5	Forced-air cooled	P16/300	yes	
SKS 760F W3C 660 V16 SU	500	-	760	SEMIPACK 5	Forced-air cooled	P16/300	yes	
SKS 780N W3C 675 V16	500	-	780	Capsules	Natural cooled	U3/515	no	
SKS 780N W3C 675 V16 SU	500	-	780	Capsules	Natural cooled	U3/515	no	
SKS 950F W3C 825 V16	500	-	950	Capsules	Forced-air cooled	P17/130	no	
SKS 950F W3C 825 V16 SU	500	-	950	Capsules	Forced-air cooled	P17/130	no	
SKS 1180F W3C 1020 V16	500	-	1180	Capsules	Forced-air cooled	P17/130	no	
SKS 1180F W3C 1020 V16 SU	500	-	1180	Capsules	Forced-air cooled	P17/130	no	
SKS 1540F W3C 1335 V16	500	-	1540	Capsules	Forced-air cooled	P18/180	no	
SKS 1540F W3C 1335 V16 SU	500	-	1540	Capsules	Forced-air cooled	P18/180	no	
SKS 2150F W3C 1860 V16	500	-	2150	Capsules	Forced-air cooled	N4/250	no	
SKS 2150F W3C 1860 V16 ZU	500	-	2150	Capsules	Forced-air cooled	N4/250	no	

Systems

Most Compact Power Electronics System for Utility Vehicles

SEMIKRON's inverter systems are already fully equipped with current sensors, IGBT drivers, DC link capacitors and a fast processor (DSP).

The systems are designed to operate with supply voltages of 24V up to 800V and with output power ratings of up to 250 kVA.

Product	Page
SKAI 2	146

▶ For detailed information please refer data sheets.

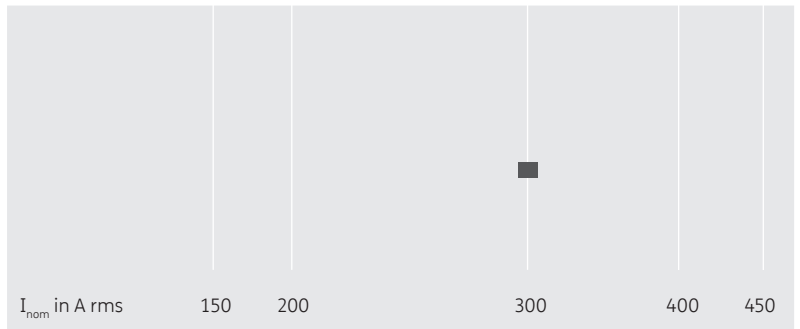
Further information:
www.semikron.com/systems

Systems

SKAI® 2 IGBT Inverter



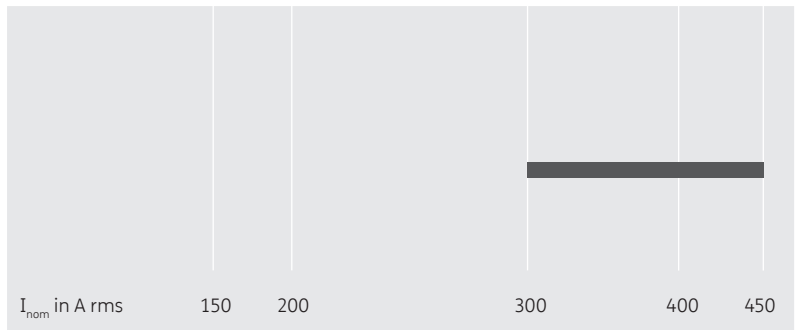
600V up to 1200V



SKAI® 2 MOSFET Single Inverter



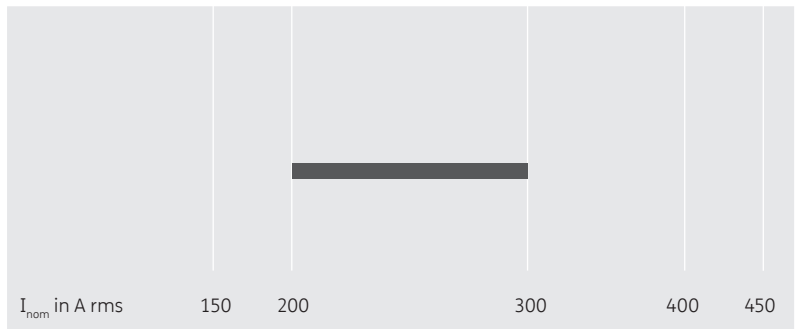
24V up to 160V



SKAI® 2 MOSFET Dual Inverter



24V up to 160V



Systems / SKAI2

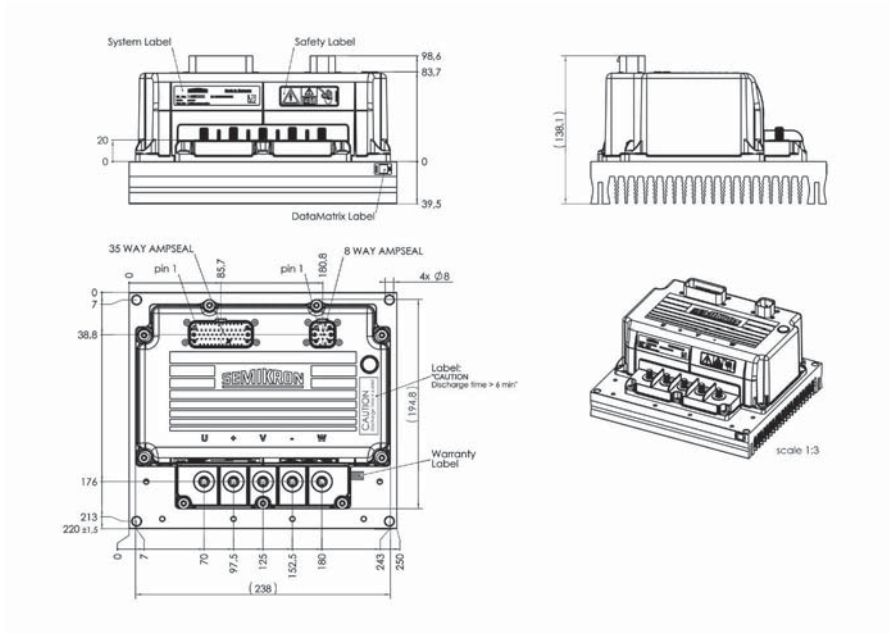
Type

	$V_{\text{battery (max)}}$ V	I_{nom} A_{rms}	Topology	Cooling	DSP	Case	Circuit
MOSFET - Three-phase inverter							
SKAI 60 A2 MD10-P	72	365	3-Phase	Baseplate	Yes	3	
SKAI 70 A2 MD15-W	115	450	3-Phase	Liquid	Yes	2	
SKAI 50 A2 MD20-L	160	300	3-Phase	Forced Air	Yes	1	
SKAI 50 A2 MD20-W	160	350	3-Phase	Liquid	Yes	2	
IGBT - Three-phase inverter							
SKAI 70 A2 MM15-L	115	250	Dual 3-Phase	Forced Air	Yes	4	
SKAI 70 A2 MM15-P	115	250	Dual 3-Phase	Baseplate	Yes	6	
SKAI 70 A2 MM15-W	115	300	Dual 3-Phase	Liquid	Yes	5	
SKAI 50 A2 MM20-L	160	200	Dual 3-Phase	Forced Air	Yes	4	
SKAI 50 A2 MM20-W	160	250	Dual 3-Phase	Liquid	Yes	5	
SKAI 90 A2 GD06-WCI	450	300	3-Phase	Liquid	Yes	7	
SKAI 45 A2 GD12-WCI	800	300	3-Phase	Liquid	Yes	7	
SKAI 90 A2 GD06-WDI	450	300	3-Phase	Liquid	No	7	
SKAI 45 A2 GD12-WDI	800	300	3-Phase	Liquid	No	7	

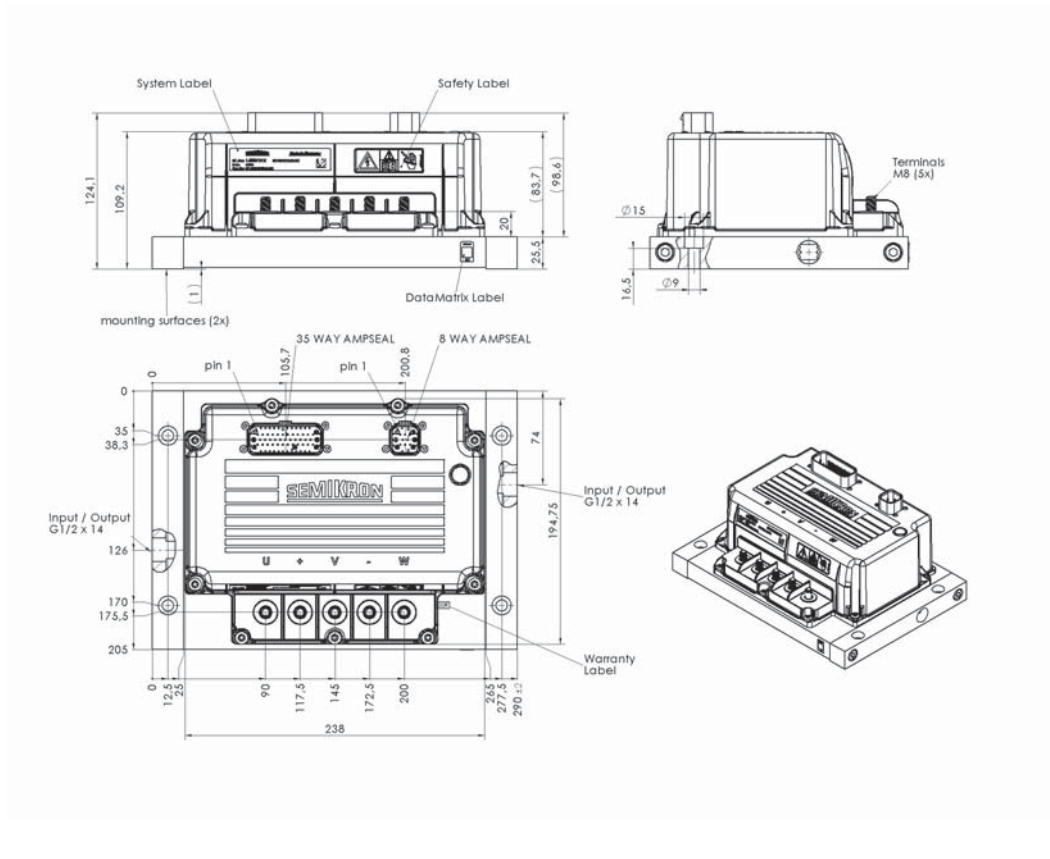
Systems / SKAI2

Cases

Case 1



Case 2

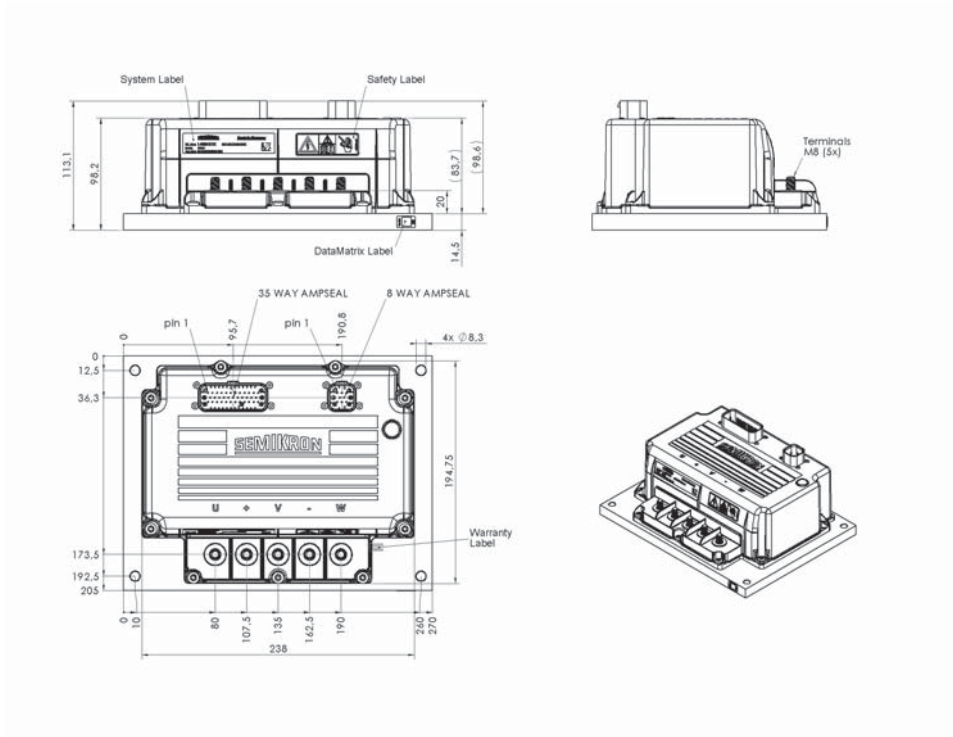


Dimensions in mm

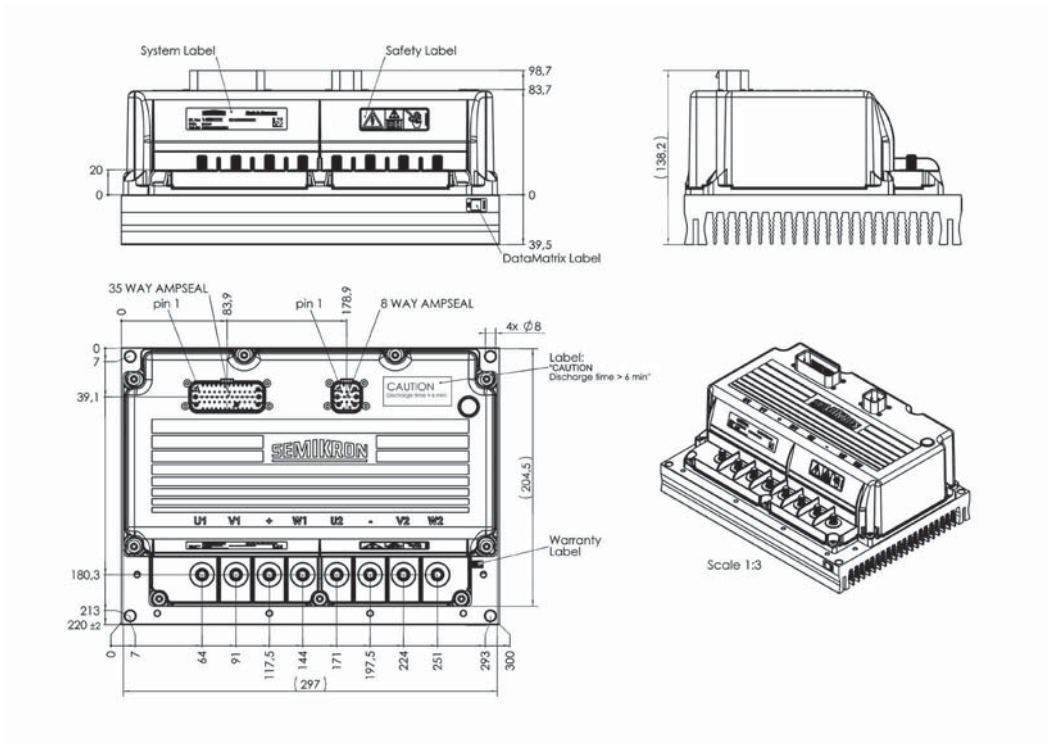
Systems / SKAI2

Cases

Case 3



Case 4

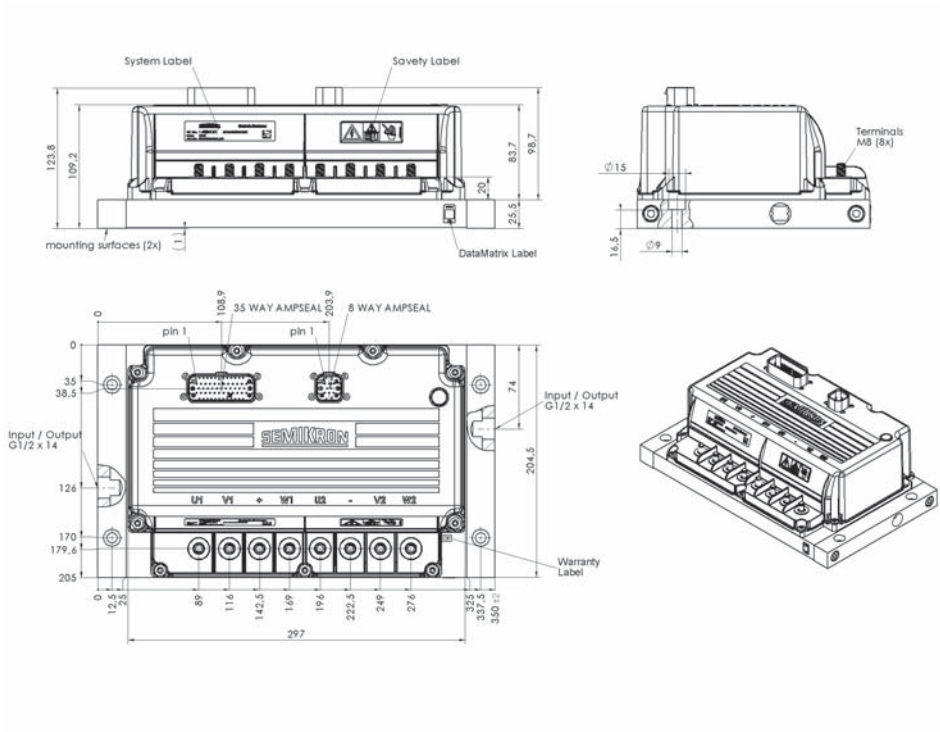


Dimensions in mm

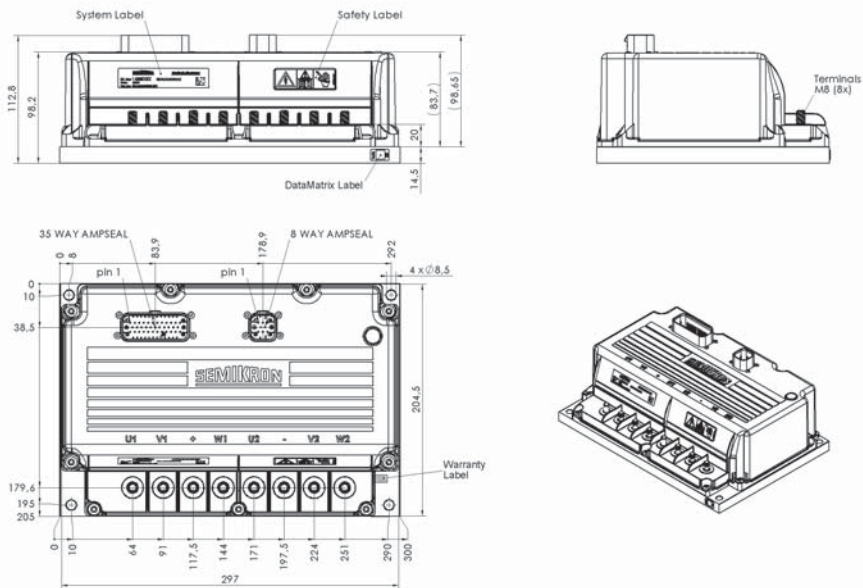
Systems / SKAI2

Cases

Case 5



Case 6

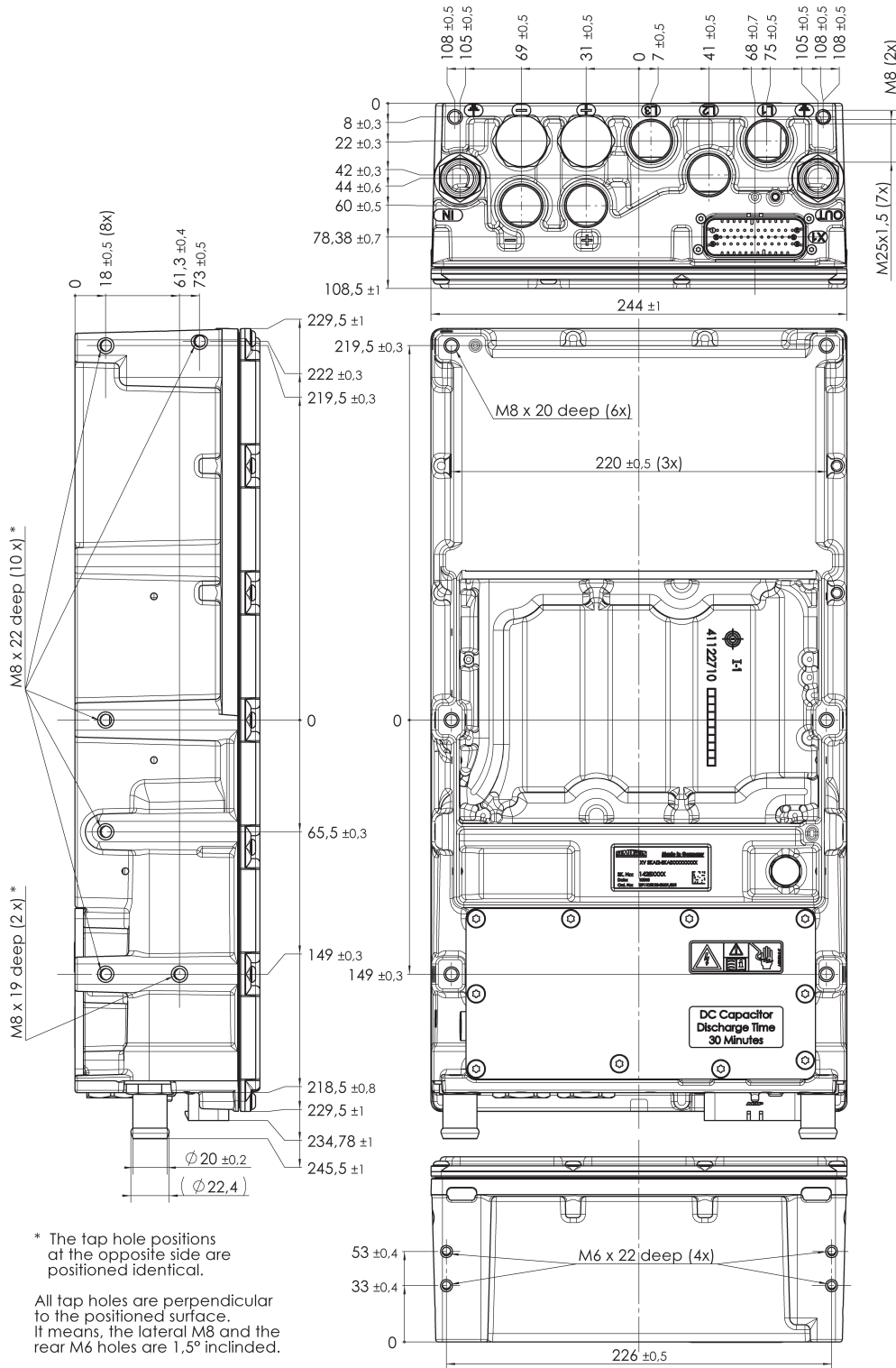


Dimensions in mm

Systems / SKAI2

Cases

Case 7



Dimensions in mm

Chips / Discretes

Chips – CAL (Controlled Axial Lifetime) freewheeling diodes are available in 600V / 650V, 1200V, and 1700V voltage classes with current ratings up to 200A. Depending on the target application's frequency, variants with custom designed switching properties are available.

Rectifier diodes and thyristors are designed for the 1600V voltage class, covering a wide range of current ratings up to 770A, equivalent to a die size of more than 500 mm². Variable configurations of the thyristor gate (corner vs. center gate) enable an optimized bond layout in the respective target design on the customer side. All chips are used throughout SEMIKRON's module and system range which means a proven history of outstanding performance and reliability. They are compatible to various joint and assembly techniques. Customers may benefit from the vast application knowledge of the SEMIKRON engineering team.

Discretes – the discrete components of SEMIKRON offer a wide variety of packaging technologies, including axial epoxy diodes, stud screw fit diodes, stud screw fit thyristors, capsule diodes and thyristors. The line offers standard rectifiers with current ratings up to 6000A, fast rectifiers up to 140A, avalanche rectifiers and high voltage rectification up to 5000V.

Product	Page
Chips SEMICELL	
Freewheeling Diode CAL	154
Rectifier Diode	157
Thyristor	157
Discrete Diode	
Leaded	158
Stud screw fit	159
Capsule	161
Discrete Thyristor	
Stud screw fit	162
Capsule	163

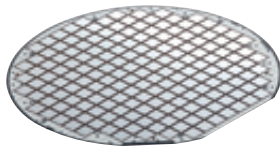
▶ For detailed information please refer data sheets.

Further information:
www.semikron.com/chips
www.semikron.com/discretes

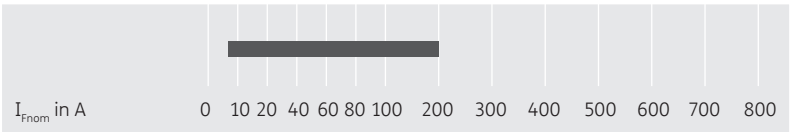
Chips / Discretes

Chips SEMICELL

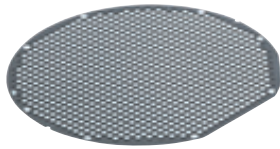
Freewheeling Diode CAL



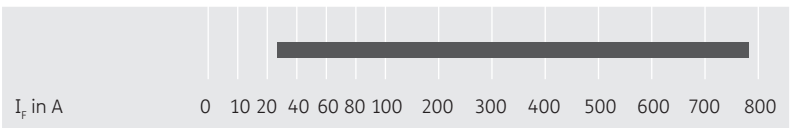
600V up to 1700V



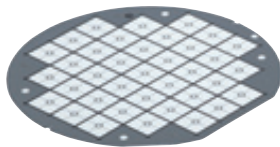
Rectifier Diode



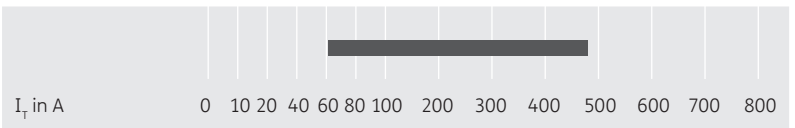
1600V



Thyristor



1600V

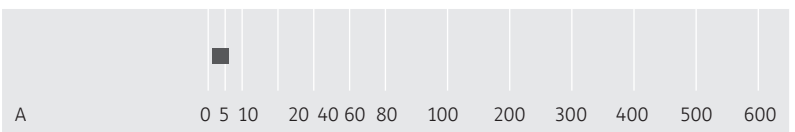


Discrete Diodes

Leaded



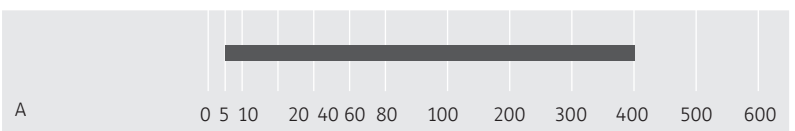
100V up to 2000V



Stud screw fit



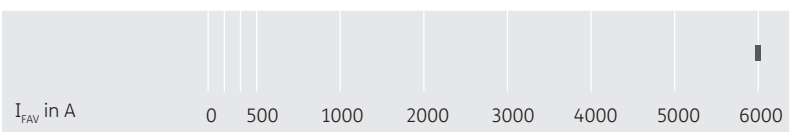
400V up to 5000V



Capsule



200V up to 600V



Discrete Thyristors

Stud screw fit



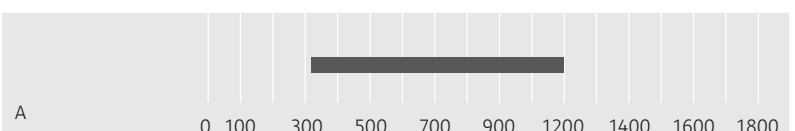
400V up to 1800V



Capsule



400V up to 1800V



Discretes / Chips / SEMICELL

Type

	V_{RRM} V	$I_F @ T_J = 150^\circ C$ A	$I_{FSM} @ T_J = 150^\circ C$ 10ms A	$V_F @ T_J = 25^\circ C$ V	$I_F @ V_F T_J = 25^\circ C$ A	$Q_r @ T_J = 125^\circ C$ μC
--	----------------	--------------------------------	---	-------------------------------	-----------------------------------	--------------------------------------

600V - Freewheeling Diodes CAL I3 Fast

SKCD 06 C 060 I3	600	15	80	1.35	8	1
SKCD 09 C 060 I3	600	20	100	1.35	13	1.46
SKCD 18 C 060 I3	600	30	200	1.35	25	1.98
SKCD 31 C 060 I3	600	50	440	1.35	50	3.3
SKCD 47 C 060 I3	600	80	720	1.35	85	6.2
SKCD 61 C 060 I3	600	100	1000	1.35	110	8.7
SKCD 81 C 060 I3	600	150	1260	1.35	155	11.5
SKCD 121 C 060 I3	600	210	2100	1.35	245	18

Type

	V_{RRM} V	$I_F @ T_J = 175^\circ C$ A	$I_{FSM} @ T_J = 150^\circ C$ 10ms A	$V_F @ T_J = 25^\circ C$ V	$I_F @ V_F T_J = 25^\circ C$ A	$Q_r @ T_J = 150^\circ C$ μC
--	----------------	--------------------------------	---	-------------------------------	-----------------------------------	--------------------------------------

600V - Freewheeling Diodes CAL High Density

SKCD 04 C 060 I HD	600	10	65	1.23	4.7	1.3
SKCD 06 C 060 I HD	600	20	95	1.23	8	1.42
SKCD 09 C 060 I HD	600	30	160	1.23	13	2.4
SKCD 16 C 060 I HD	600	50	320	1.23	25	3.87
SKCD 24 C 060 I HD	600	75	395	1.23	41	6
SKCD 42 C 060 I HD	600	100	810	1.23	75	11.1
SKCD 61 C 060 I HD	600	150	1080	1.23	112	15.75
SKCD 81 C 060 I HD	600	200	1310	1.23	152	19.69

Type

	V_{RRM} V	$I_F @ T_J = 175^\circ C$ A	$I_{FSM} @ T_J = 150^\circ C$ 10ms A	$V_F @ T_J = 25^\circ C$ V	$I_F @ V_F T_J = 25^\circ C$ A	$E_r @ T_J = 150^\circ C$ mJ
--	----------------	--------------------------------	---	-------------------------------	-----------------------------------	---------------------------------

650V - Freewheeling Diodes CAL I4 Fast

SKCD 24 C 065 I4F	650	50	460	1.30	39	1.1
SKCD 42 C 065 I4F	650	100	680	1.30	73	2.2
SKCD 61 C 065 I4F	650	150	1100	1.30	109	3.8
SKCD 81 C 065 I4F	650	200	1290	1.30	148	5.8

Discretes / Chips / SEMICELL

Type

Type	V_{RRM} V	$I_F @ T_J = 150^\circ C$ A	$I_{FSM} @ T_J = 150^\circ C$ 10ms A	$V_F @ T_J = 25^\circ C$ V	$I_F @ V_F, T_J = 25^\circ C$ A	$Q_{rr} @ T_J = 125^\circ C$ μC
1200V - Freewheeling Diodes CAL I3 Fast						
SKCD 11 C 120 I3	1200	15	130	2.00	10	1.6
SKCD 18 C 120 I3	1200	25	200	2.00	15	3
SKCD 23 C 120 I3R	1200	30	270	2.00	25	3.8
SKCD 31 C 120 I3	1200	40	370	2.00	35	5.3
SKCD 47 C 120 I3	1200	55	600	2.00	55	7.5
SKCD 61 C 120 I3	1200	75	800	2.00	70	11
SKCD 81 C 120 I3	1200	100	1100	2.00	100	16.5
SKCD 121 C 120 I3	1200	150	1600	2.00	155	24

1200V - Freewheeling Diodes CAL High Density

SKCD 06 C 120 I HD	1200	6	60	1.50	5	1.24
SKCD 11 C 120 I HD	1200	15	140	1.50	12	2.9
SKCD 14 C 120 I HD	1200	20	170	1.50	15	4
SKCD 18 C 120 I HD	1200	25	200	1.50	20	5
SKCD 31 C 120 I HD	1200	55	480	1.50	45	11
SKCD 47 C 120 I HD	1200	85	700	1.50	70	17.4
SKCD 61 C 120 I HD	1200	115	900	1.50	90	24.5
SKCD 81 C 120 I HD	1200	160	1150	1.50	130	34.4

Type

Type	V_{RRM} V	$I_F @ T_J = 175^\circ C$ A	$I_{FSM} @ T_J = 150^\circ C$ 10ms A	$V_F @ T_J = 25^\circ C$ V	$I_F @ V_F, T_J = 25^\circ C$ A	$E_{rr} @ T_J = 150^\circ C$ mJ
1200V - Freewheeling Diodes CAL I4 Fast						
SKCD 08 C 120 I4F	1200	8	36	2.33	8	0.4
SKCD 11 C 120 I4F	1200	15	65	2.38	15	0.6
SKCD 16 C 120 I4F	1200	25	100	2.41	25	1
SKCD 22 C 120 I4F	1200	35	170	2.30	35	1.6
SKCD 31 C 120 I4F	1200	50	270	2.22	50	2.6
SKCD 46 C 120 I4F	1200	75	430	2.17	75	4.2
SKCD 46 C 120 I4F R	1200	75	430	2.17	75	4.2
SKCD 53 C 120 I4F	1200	100	550	2.20	100	5.4
SKCD 81 C 120 I4F	1200	150	900	2.14	150	8.7

Discretes / Chips / SEMICELL

Type

Type	V_{RRM} V	$I_F @ T_J = 150^\circ C$ A	$I_{FSM} @ T_J = 150^\circ C$ 10ms A	$V_F @ T_J = 25^\circ C$ V	$I_F @ V_F, T_J = 25^\circ C$ A	$Q_{rr} @ T_J = 125^\circ C$ µC
------	----------------	--------------------------------	---	-------------------------------	------------------------------------	------------------------------------

1700V - Freewheeling Diodes CAL Fast

SKCD 47 C 170 I	1700	55	550	2.05	55	15
SKCD 61 C 170 I	1700	75	720	2.05	75	24

1700V - Freewheeling Diodes CAL High Density

SKCD 47 C 170 I HD	1700	75	650	1.73	75	25
SKCD 61 C 170 I HD	1700	100	710	1.73	100	35
SKCD 81 C 170 I HD	1700	150	1070	1.73	150	53.5

Type

Type	V_{RRM} V	$I_F @ T_J = 175^\circ C$ A	$I_{FSM} @ T_J = 150^\circ C$ 10ms A	$V_F @ T_J = 25^\circ C$ V	$I_F @ V_F, T_J = 25^\circ C$ A	$E_{rr} @ T_J = 150^\circ C$ mJ
------	----------------	--------------------------------	---	-------------------------------	------------------------------------	------------------------------------

1700V - Freewheeling Diodes CAL I4 Fast

SKCD 28 C 170 I4F	1700	40	280	1.71	23	12
SKCD 46 C 170 I4F	1700	75	450	1.71	43	17
SKCD 56 C 170 I4F	1700	100	580	1.71	57	22.2
SKCD 81 C 170 I4F	1700	150	860	1.71	89	31.5

Discretes / Chips / SEMICELL

Type

	V_{RRM} V	$I_{FDCI} @ T_J = 150^\circ C$ A	$I_{FSM} @ T_J = 150^\circ C, 10ms$ A	$V_F @ T_J = 25^\circ C$ V	$I_F @ V_F, T_J = 25^\circ C$ A	$t_{rr} @ T_J = 25^\circ C$ μs
1600V - Rectifier						
SKR 3,5 Qu bond ⁽⁴⁾	1600	25	200	1.00	8	20
SKR 4,2 Qu bond ⁽⁴⁾	1600	35	270	1.00	13	20
SKR 4,8 Qu bond ⁽⁴⁾	1600	45	350	1.00	18	21
SKR 5,6 Qu bond ⁽⁴⁾	1600	50	490	1.00	25	22
SKR 6,2 Qu bond ⁽⁴⁾	1600	65	600	1.00	33	22
SKR 7,0 Qu bond ⁽⁴⁾	1600	75	890	1.00	45	23
SKR 8,9 Qu bond ⁽⁴⁾	1600	140	1380	1.00	77	26
SKR 10,3 Qu bond ⁽⁴⁾	1600	170	1650	1.00	106	29
SKR 12,4 Qu bond ⁽⁴⁾	1600	235	2300	1.00	160	34
SKR 15,2 Qu bond ⁽⁴⁾	1600	330	3800	1.00	245	42
SKR 16,3 x 18,2 Qu bond ⁽⁴⁾	1600	365	5100	1.00	320	49
SKN 18,2 Qu bond ⁽⁴⁾	1600	380	5500	1.00	360	53
SKN 22,4 Qu bond ⁽⁴⁾	1600	770	9450	1.00	550	72

Footnotes: 4) solderable top metallization on request

Type

	V_{RRM}, V_{DRM} V	$I_{TDO} @ T_J = 130^\circ C$ A	$I_{TSM} @ T_J = 130^\circ C, 10ms$ A	$V_{GT} @ T_J = 25^\circ C$ V	$I_{GT} @ T_J = 25^\circ C$ A	$t_q @ T_J = 130^\circ C$ μs
1600V - Thyristor Central Gate						
SKT 8,9 Qu ZG bond ⁽⁴⁾	1600	105	1000	1.98	100	150
SKT 10,3 Qu ZG bond ⁽⁴⁾	1600	125	1250	1.98	100	150
SKT 12,4 Qu ZG bond ⁽⁴⁾	1600	165	1800	1.98	100	150
SKT 13,5 Qu ZG bond ⁽⁴⁾	1600	185	2300	1.98	100	135
SKT 15,2 Qu ZG bond ⁽⁴⁾	1600	215	3200	1.98	100	150
SKT 18,2 Qu ZG bond ⁽⁴⁾	1600	250	5000	1.98	100	150
SKT 24,3 Qu ZG bond SG ⁽⁴⁾	1600	480	8200	1.98	150	150
1600V - Thyristor Corner Gate						
SKT 5,6 Qu RG bond ⁽⁴⁾	1600	60	280	1.98	100	150
SKT 7,0 Qu RG bond ⁽⁴⁾	1600	75	450	1.98	100	150
SKT 8,9 Qu RG bond ⁽⁴⁾	1600	105	1000	1.98	100	150
SKT 10,3 Qu RG bond ⁽⁴⁾	1600	125	1250	1.98	100	150
SKT 12,4 Qu RG bond ⁽⁴⁾	1600	165	1800	1.98	100	150

Footnotes: 4) solderable top metallization on request

Discretes / Diodes / Leaded

Type

	Voltage (V)	Current (A)	T_c	$I_{SM}@T_j=25^\circ\text{C}$	V_F	$R_{th(j-c)}$ per chip	T_j	Case	Topology Picture
	V	A	$^\circ\text{C}$	A	V	K/W	$^\circ\text{C}$		

Standard recovery

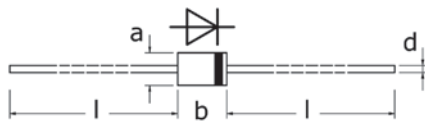
SK 1	1000-1600	1.45	60	60	1.50	85	-40 ... +150	E33	
SKN 2,5	400-1600	2.5	45	180	1.20	55	-40 ... +180	E5	
SK 3	1000-1600	3.3	85	180	1.20	60	-40 ... +150	E34	
SKN 5	200-1600	5	45	190	1.25	25	-40 ... +180	E6	

Avalanche

SKa1	1300-1700	1.45	60	60	1.50	85	-40 ... +150	E33	
SKNa2	1300-1700	2	45	180	1.20	55	-40 ... +150	E5	
SKa3	1300-1700	3.3	90	180	1.20	60	-40 ... +150	E34	
SKNa4	1300-1700	3.7	35	190	1.20	25	-40 ... +150	E6	

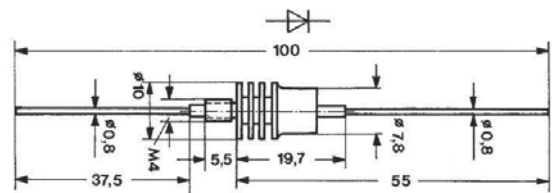
Cases

E33 / E34

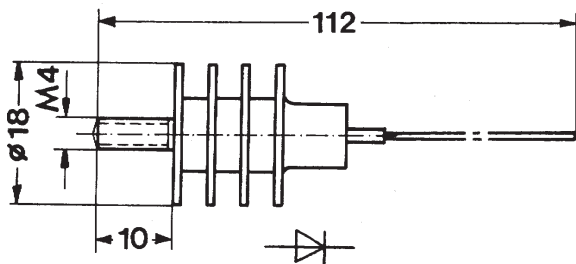


Cases	a	b	l	d
E 33	4,5	7	28	0,75
E 34	6	9	27	1,18

E5



E6



Dimensions in mm

Discretes / Diodes / Stud Screw Fit

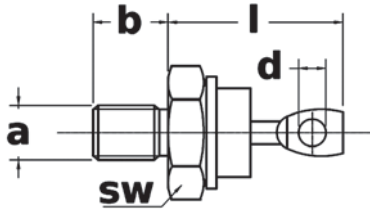
Type

	Voltage (V)	Current (A)	T _C	I _{FSM} @T _J =25°C	V _F	R _{th(j-c)} per chip	T _J	Case	Topology Picture	
	V	A	°C	A	V	K/W	°C			
Standard recovery										
SKN 20	400-1600	20	125	375	1.55	2	-40 ... +180	E9		
SKN 26	400-1600	25	100	375	1.55	2	-40 ... +180	E8		
SKN 45	400-1600	45	125	700	1.60	0.85	-40 ... +180	E12		
SKN 70	400-1600	70	125	1150	1.50	0.55	-40 ... +180	E12		
SKN 71	400-1600	70	125	1150	1.50	0.55	-40 ... +180	E11		
SKN 100	400-1800	100	120	1750	1.55	0.45	-40 ... +180	E13		
SKN 130	400-1800	130	125	2500	1.50	0.35	-40 ... +180	E14		
SKN 240	400-1800	240	125	6000	1.40	0.2	-40 ... +180	E15		
SKN 320	400-1600	320	125	9000	1.35	0.16	-40 ... +180	E16		
SKN 400	1800-3000	400	100	9000	1.45	0.11	-40 ... +160	E17		
SKR 20	400-1600	20	125	375	1.55	2	-40 ... +180	E9		
SKR 26	400-1600	25	100	375	1.55	2	-40 ... +180	E8		
SKR 45	400-1600	45	125	700	1.60	0.85	-40 ... +180	E12		
SKR 70	400-1600	70	125	1150	1.50	0.55	-40 ... +180	E12		
SKR 71	400-1600	70	125	1150	1.50	0.55	-40 ... +180	E11		
SKR 100	400-1800	100	120	1750	1.55	0.45	-40 ... +180	E13		
SKR 130	400-1800	130	125	2500	1.50	0.35	-40 ... +180	E14		
SKR 240	400-1800	240	125	6000	1.40	0.2	-40 ... +180	E15		
SKR 320	400-1600	320	125	9000	1.35	0.16	-40 ... +180	E16		
Fast recovery										
SKN 2F17	400-1000	17	113	450	2.15	1.2	-40 ... +150	E7		
SKN 3F20	800-1200	20	104	375	2.15	1.2	-40 ... +150	E7		
SKN 2F50	400-1000	50	105	1100	1.80	0.5	-40 ... +150	E10		
SKN 60F	1200-1700	60	100	1400	1.75	0.5	-40 ... +150	E10		
SKN 135F	800-1200	135	100	2500	1.95	0.2	-40 ... +150	E14		
SKN 136F	800-1200	135	100	2500	1.95	0.2	-40 ... +150	E31		
SKN 140F	1200-1700	140	100	2500	1.80	0.2	-40 ... +150	E14		
SKN 141F	1200-1700	140	100	2500	1.80	0.2	-40 ... +150	E31		
SKR 2F17	400-1000	17	113	450	2.15	1.2	-40 ... +150	E7		
SKR 3F20	800-1200	20	104	375	2.15	1.2	-40 ... +150	E7		
SKR 2F50	400-1000	50	95	800	1.80	0.65	-40 ... +150	E10		
SKR 60F	1200-1700	60	100	1400	1.75	0.5	-40 ... +150	E10		
SKR 135F	800-1200	135	100	2500	1.95	0.2	-40 ... +150	E14		
SKR 136F	800-1200	135	100	2500	1.95	0.2	-40 ... +150	E31		
SKR 140F	1200-1700	140	100	2500	1.80	0.2	-40 ... +150	E14		
SKR 141F	1200-1700	140	100	2500	1.80	0.2	-40 ... +150	E31		
Avalanche										
SKNa 20	1300-1700	20	93	375	1.55	2	-40 ... +150	E9		
SKNa 22	3600-5000	25	104	450	1.95	1	-40 ... +160	E42		
SKNa 47	3600-5000	45	106	700	1.80	0.6	-40 ... +160	E43		
SKNa 102	3600-5000	125	80	1900	1.90	0.3	-40 ... +160	E44		
SKNa 202	3600-5000	200	80	3800	1.95	0.2	-40 ... +160	E45		
SKNa 402	3600-5000	400	88	7800	1.85	0.1	-40 ... +160	E46		

Discretes / Diodes / Stud Screw Fit

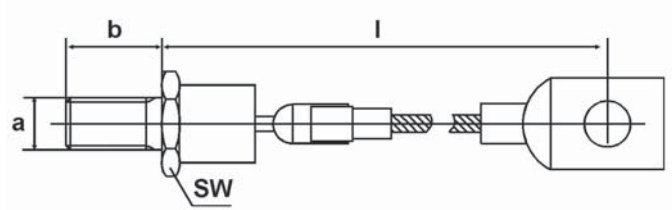
Cases

E7 / E8 / E10 / E11 / E31



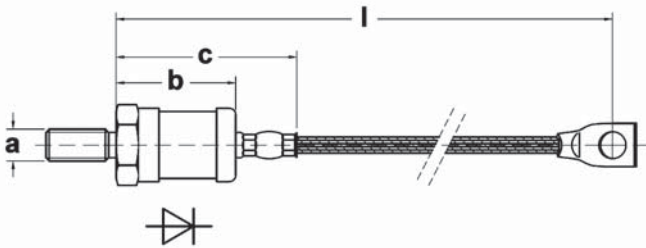
Cases	a	b	d	l	sw
E 7	M 5	11	2,7	22	11
E 8	M 6	11	2,7	21,5	11
E 10	M 6	11	4	25	17
E 11	M 8	11	4	25,5	17
E 31	M 12	18	8,4	55	24

E9 / E12 ... E17



Cases	a	b	l	SW
E 9	M 6	11	130	11
E 12	M 8	11	135	17
E 13	M 12	18	165	24
E 14	M 12	18	165	24
E 15	M 16 x 1,5	20	190	32
E 16, E 17	M 24 x 1,5	20	230	41

E 42 / E 43 / E 44 / E 45 / E 46




Cases	a	b	c	l
E 42	M 6	28.5	45	150
E 43	M 8	32	54	160
E 44	M 12	38	57	185
E 45	M 16 x 1,5	48	70	205
E 46	M 24 x 1,5	54	82	250

Dimensions in mm

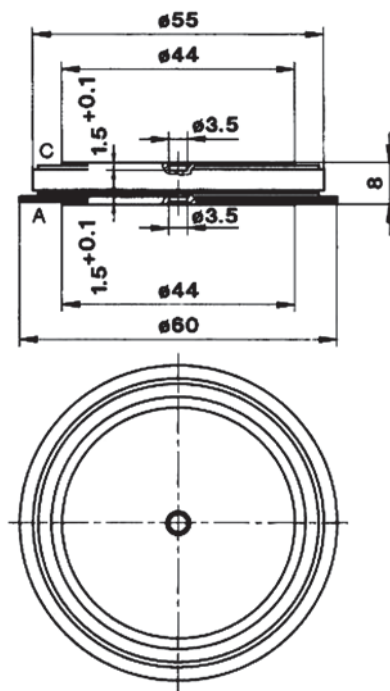
Discretes / Diodes / Capsules

Type

	Voltage (V) V	Current (A) A	T_c °C	$I_{FSM}@T_j=25^\circ\text{C}$ A	V_F V	$R_{th(j-c)}$ per chip K/W	T_j °C	Case	Topology Picture
SKN 6000	200-600	6000	85	60000	1.30	0.012	-40 ... +180	E35	

Cases

E35



Dimensions in mm

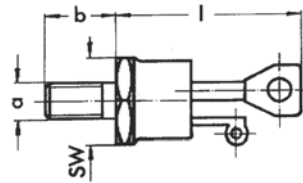
Discretes / Thyristors / Stud Screw Fit

Type

	Voltage (V)	Current (A)	T_c	$I_{TSM}@T_j=25^\circ C$	$V_T@I_T, T_j=25^\circ C$	$I_T@V_T$	$R_{th(j-c)}$ per chip	T_j	Case	Topology Picture
	V	A	$^\circ C$	A	V	A	K/W	$^\circ C$		
SKT 10	600-1200	10	111	250	1.6	30	1.3	-40 ... +130	B1	
SKT 16	400-1800	16	104	370	2.4	75	0.9	-40 ... +130	B2	
SKT 24	400-1800	24	95	450	1.9	75	0.9	-40 ... +130	B2	
SKT 40	400-1800	40	80	700	1.95	120	0.66	-40 ... +130	B3	
SKT 50	600-1800	50	78	1050	1.8	120	0.6	-40 ... +130	B3	
SKT 55	400-1800	55	92	1300	1.8	200	0.47	-40 ... +130	B5	
SKT 80	600-1800	80	85	1700	2.25	300	0.28	-40 ... +130	B5	
SKT 100	400-1800	100	85	2000	1.75	300	0.28	-40 ... +130	B5	
SKT 130	400-1600	130	85	3500	2.25	500	0.18	-40 ... +130	B6	
SKT 160	400-1600	160	84	4300	1.75	500	0.18	-40 ... +130	B6	
SKT 250	400-1600	250	85	7000	1.65	800	0.123	-40 ... +130	B7	
SKT 300	400-1600	300	93	11000	1.45	800	0.096	-40 ... +130	B7	

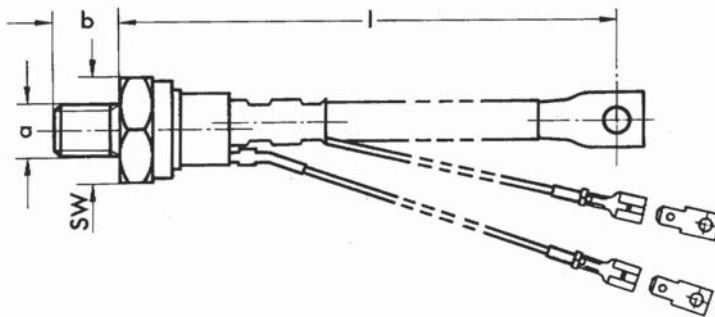
Cases

B1 ... B3



Cases	a	b	l	SW
B 1	M 5	11	20,3	11
B 2	M 6	11	30	14
B 3	M 8	11	33,5	17

B5 ... B7



Cases	a	b	l	SW
B 5	M 12	18	160	24
B 6	M 16 x 1,5	20	190	32
B 7	M 24 x 1,5	20	230	41

Dimensions in mm

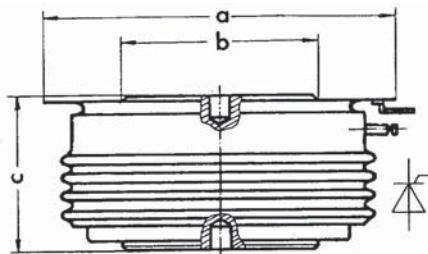
Discretes / Thyristors / Capsules

Type

	Voltage (V)	Current (A)	T_c	$I_{TSM}@T_J=25^\circ C$	$V_T@I_T, T_J=25^\circ C$	$I_T@V_T$	$R_{th(j-c)}$ per chip	T_J	Case	Topology Picture
	V	A	$^\circ C$	A	V	A	K/W	$^\circ C$		
SKT 340	1200-1800	340	82	5700	1.9	1000	0.072	-40 ... +125	B8	
SKT 493	400-1800	490	80	8000	2.1	1500	0.047	-40 ... +125	B11a	
SKT 551	1200-1800	550	85	9000	1.65	1500	0.047	-40 ... +125	B11	
SKT 553	400-1800	550	85	9000	1.65	1500	0.047	-40 ... +125	B11a	
SKT 760	1200-1800	760	80	15000	1.65	2400	0.04	-40 ... +125	B10	
SKT 1200	1200-1800	1200	85	30000	1.65	3600	0.021	-40 ... +125	B14	

Cases

B8 ... B14



Cases	a	b	c
B 8	41	19	14
B 10	57,3	34	26
B 11	41	25	14
B 11a	41	25	14
B 14	73	47	26

Dimensions in mm

Accessories

Heatsinks / Fans / Thermal Interface Materials

Heatsinks – SEMIKRON offers a broad range of different heat sinks including forced and natural air cooling. The heatsinks are available for capsules, insulated base modules or IPMs.

Fans – SEMIKRON offers a broad range of axial, centrifugal and radial fans for different inverter designs.

Thermal interface materials – According to customer demands SEMIKRON offers thermal interface solutions with silicone based or silicone free materials as well as phase change materials

Product	Page
Heatsinks	166
Fans	168
Thermal interface materials	169

▶ For detailed information please refer data sheets.

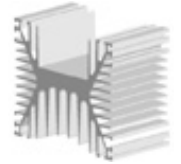
Further information:
www.semikron.com/heatsinks
www.semikron.com/fans
www.semikron.com/thermal-interface-materials

Heatsinks

Forced air cooled



Natural cooled



Fans

Axial



Centrifugal

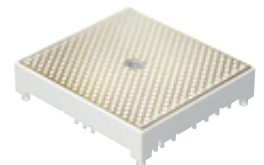


Radial



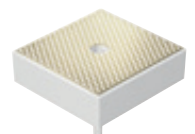
Thermal Interface Materials

Silicone-based grease



e.g. SEMITOP

Silicone-free grease



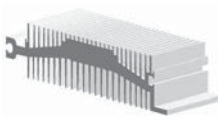
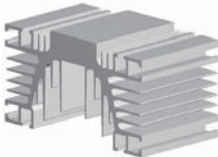
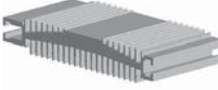
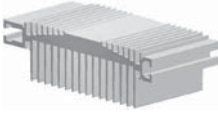
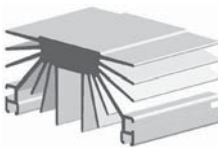
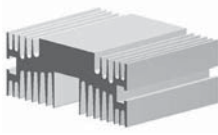
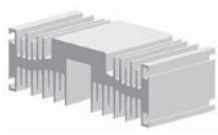
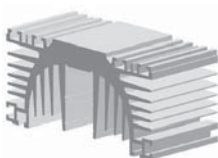
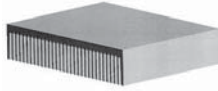
e.g. MiniSKiiP

Phase Change Material



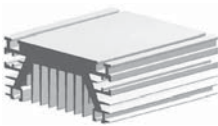
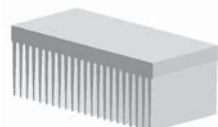


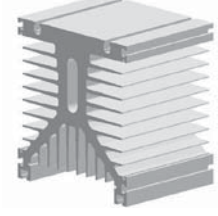
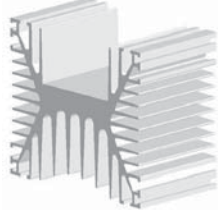
e.g. SEMiX Press-Fit

Accessories / Heatsinks

Type	Suitable for	R_{thsa} natural cooling K/W	R_{thsa} forced air cooling K/W	Weight kg	Weight kg/m	Produkt Picture
Forced-air cooled						
N 4	Capsules	-	0.04	6.3	25.1	
P 11	Capsules	0.2	0.05	3.8	15	
P 17	Capsules	0.45	0.12	1.5	10.6	
P 18	Capsules	0.37	0.08	1.6	12.2	
P 8 ⁷⁾	Capsules	0.35	0.07	1.7	9.6	
P 8,5 ⁷⁾	Capsules	0.3	0.08	1.5	9.5	
P 9 ⁷⁾	Capsules	0.21	0.06	4.1	17.8	
U 3	Capsules	0.14	0.06	7.1	23.7	
P 21 ⁷⁾	Isolated base modules	-	0.02	4.1	40.8	

Footnotes: 7) Non standard item, available on request only, typical minimum batch quantities of 60 pieces will apply

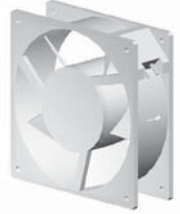

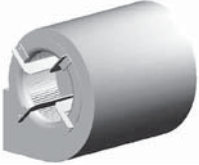


Accessories / Heatsinks

Type	Suitable for	R_{thsa} natural cooling K/W	R_{thsa} forced air cooling K/W	Weight kg	Weight kg/m	Produkt Picture
Forced-air cooled						
R 4A	Isolated base modules	1.4	0.38	0.6	-	
P 16	SKiiP or modules	-	0.06	1.3	23.5	
Px 308 ⁷⁾	SKiiP or modules	-	0.013	2	12.2	
P 1	Studs or modules	0.7	0.4	0.8	11.3	
P 3	Isolated base modules	0.45	0.14	0.7	17.6	
Natural cooled						
P 4 ⁷⁾	Stud device	0.27	-	4.1	20.6	

Footnotes: 7) Non standard item, available on request only, typical minimum batch quantities of 60 pieces will apply

Accessories / Fans

Type

	V_{in} V	f Hz	V_{air}/t m ³ /h	P_{max} W	T_{Amax} °C	Weight kg	Noise dB	Produkt Picture
Axial Fans								
SKF 3-230-01	230	50 / 60	150 / 174	15 / 14	70	0.55	37 / 41	
SKF RE-024-01	24	-	500	90	75	0.43	76	
SKF SR-024-01	24	-	56	3.6	70	0.085	43	
SKF 9-230-01	230	50 / 60	375 / 440	24 / 26	70	1	54 / 60	
SKF 8-230-01	230	50 / 60	325 / 380	45 / 39	50 / 70	1.1	49 / 53	
Centrifugal Fans								
SKF 17A-230-11	230	50 / 60	850 / 930	110 / 120	70	2	74	
SKF 17B-230-12	230	50 / 60	1175 / 1300	230	70	6.1	73 / 76	
Radial Fans								
SKF 16A-230-01	230	50 / 60	630 / 590	130 / 140	60 / 50	3.3	59	
SKF 16P-230-01	230	50 / 60	1125	165	60	3.9	-	
SKF 16B-230-01	230	50 / 60	640 / 580	167 / 191	70 / 50	3.75	58 / 57	
SKF 16A-230-11	230	50 / 60	630 / 590	130 / 140	60 / 50	3.3	59	
								

Accessories / Thermal Interface Materials

Type	Case	Thermal paste	Tolerances (+/-) μm	Thickness (after assembly) μm	Thermal conductance W/m*K
Silicone-based grease					
MiniSKiiP	0 II	Wacker P12	10	33	0.8
MiniSKiiP	1 II	Wacker P12	10	30	0.8
MiniSKiiP	2 I	Wacker P12	10	50	0.8
MiniSKiiP	2 II	Wacker P12	10	55	0.8
MiniSKiiP	3 I	Wacker P12	10	45	0.8
MiniSKiiP	3 II	Wacker P12	10	40	0.8
MiniSKiiP ¹⁾	2 II	Wacker P12	6	35	0.8
MiniSKiiP ¹⁾	3 II	Wacker P12	6	35	0.8
MiniSKiiP	8 I AC	Wacker P12	10	61	0.8
MiniSKiiP	8 I AB	Wacker P12	10	60	0.8
SKiM 4/5	4	Wacker P12	6	44	0.8
SKiM 63/93	93	Wacker P12	6	21	0.8
SKiM 63/93	63	Wacker P12	6	21	0.8
SEMITOP	2	Wacker P12	7	29	0.8
SEMITOP	3	Wacker P12	7	47	0.8
SEMITOP	4	Wacker P12	6	31	0.8
Silicone-free grease					
MiniSKiiP	2 II	Electrolube HTC	10	75	0.9
MiniSKiiP	3 II	Electrolube HTC	10	60	0.9
Phase Change Materials					
SEMiX ¹⁾	3p	HALA TPC-Z-PC-P8	3	19	3.4

Footnotes: 1) New product